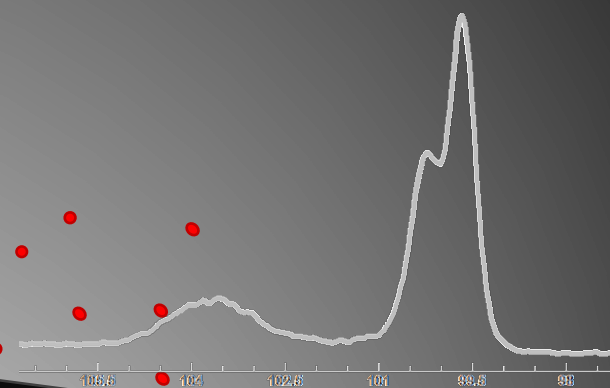
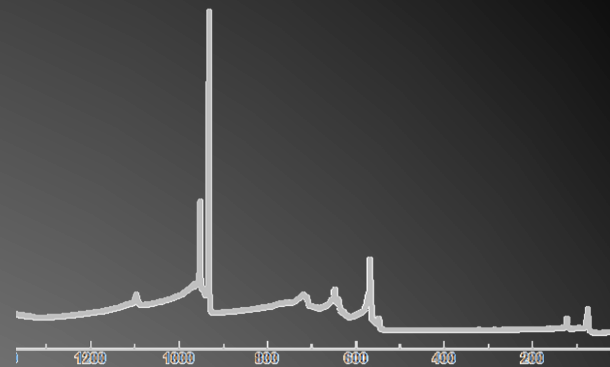


Monochromatic XPS Spectra



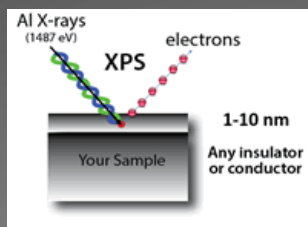
The Elements
and Native Oxides

B. Vincent Crist

XPS International, LLC
<https://xpslibrary.com>

Monochromatic XPS Spectra

The Elements and Native Oxides



1 H 1s																				2 He 1s	
H ₂ ⁺	LiH																			He ⁺ /Be	He ⁺ /C

Handbooks of Monochromatic XPS Spectra

Volume 1 - *The Elements and Native Oxides*

by

B. Vincent Crist, Ph.D.

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B. Vincent Crist

Published by XPS International LLC

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Handbook of Monochromatic XPS Spectra

Volume 1 – The Elements

C (1s) BE = 285.0 eV
Charge Referencing

*Select an Element to see its
Atom % Table and Spectra.*

1																	18
1																	2
H																	He
3	4											13	14	15	16	17	10
Li	Be											B	C	N	O	F	Ne
11	12											13	14	15	16	17	18
Na	Mg											Al	Si	P	S	Cl	Ar
19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34	35	36
K	Ca	Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn	Ga	Ge	As	Se	Br	Kr
37	38	39	40	41	42	43	44	45	46	47	48	49	50	51	52	53	54
Rb	Sr	Y	Zr	Nb	Mo	Tc	Ru	Rh	Pd	Ag	Cd	In	Sn	Sb	Te	I	Xe
55	56	57	72	73	74	75	76	77	78	79	80	81	82	83	84	85	86
Cs	Ba	La	Hf	Ta	W	Re	Os	Ir	Pt	Au	Hg	Tl	Pb	Bi	Po	At	Rn
87	88	89															
Fr	Ra	Ac															
			58	59	60	61	62	63	64	65	66	67	68	69	70	71	
			Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu	
			90	91	92	93	94	95	96	97	98	99	100	101	102	103	
			Th	Pa	U	Np	Pu	Am	Cm	Bk	Cf	Es	Fm	Md	No	Lr	

Handbook of Monochromatic XPS Spectra

Volume 2 – Native Oxides

Charge
Neutralizer OFF

*Select an Element to see its
Atom % Table and Spectra.*

1																	18
1																	2
H																	He
3	4											13	14	15	16	17	10
Li	Be											B	C	N	O	F	Ne
11	12											13	14	15	16	17	18
Na	Mg											Al	Si	P	S	Cl	Ar
19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34	35	36
K	Ca	Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn	Ga	Ge	As	Se	Br	Kr
37	38	39	40	41	42	43	44	45	46	47	48	49	50	51	52	53	54
Rb	Sr	Y	Zr	Nb	Mo	Tc	Ru	Rh	Pd	Ag	Cd	In	Sn	Sb	Te	I	Xe
55	56	57	72	73	74	75	76	77	78	79	80	81	82	83	84	85	86
Cs	Ba	La	Hf	Ta	W	Re	Os	Ir	Pt	Au	Hg	Tl	Pb	Bi	Po	At	Rn
87	88	89															
Fr	Ra	Ac															
			58	59	60	61	62	63	64	65	66	67	68	69	70	71	
			Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu	
			90	91	92	93	94	95	96	97	98	99	100	101	102	103	
			Th	Pa	U	Np	Pu	Am	Cm	Bk	Cf	Es	Fm	Md	No	Lr	

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Monochromatic XPS Spectra of The Elements and Native Oxides

THE ELEMENTS

Ag ⁰	(Silver metal, Z=47)	47
Al ⁰	(Aluminium metal, Z=13).	51
Ar (+)	(Argon implanted in carbon, Z=18)..	55
As ⁰	(Arsenic metal, Z=33).	59
Au ⁰	(Gold metal, Z=79)	64
B ⁰	(Boron, Z=5)	69
Ba (2+)	(Barium Carbonate, Z=56)	73
Be ⁰	(Beryllium metal, Z=4)	79
Bi ⁰	(Bismuth metal, Z=83)	83
Br (-)	(Bromine in potassium bromide, Z=35)	87
C ⁰	(Carbon, Z=6)	93
Ca ⁰	(Calcium metal, Z=20)	99
Cd ⁰	(Cadmium metal, Z=48)	106
Ce (4+)	(Cerium in cerium oxide, Z=58).....	110
Cl (-)	(Chlorine in sodium chloride, Z=17).....	116
Co ⁰	(Cobalt metal, Z=27)	122
Cr ⁰	(Chromium metal, Z=24).....	126
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Pt ⁰	(Platinum metal, Z=78).....	286
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Re ⁰	(Rhenium metal, Z=75)	295
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BO _x	naturally formed, native oxide of Boron	328
BeO _x	naturally formed, native oxide of Beryllium	333
BiO _x	naturally formed, native oxide of Bismuth.....	338
CdO _x	naturally formed, native oxide of Cadmium.....	343
CoO _x	naturally formed, native oxide of Cobalt.....	348
CrO _x	naturally formed, native oxide of Chromium	353
CuO _x	naturally formed, native oxide of Copper	358
FeO _x	naturally formed, native oxide of Iron.....	363
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YO _x	<i>freshly formed</i> , native oxide of Yttrium	501
ZnO _x	naturally formed, native oxide of Zinc	506
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INTRODUCTION

This handbook contains wide scan spectra and narrow scan spectra from the elements and native oxides of the elements. The elements have been analyzed under conditions that have maximized the accuracy of the binding energies. The binding energies for the pure elements are referenced to the reference energies recommended by the National Physical Laboratory in the UK. Please refer to section "F" (Energy Scale Reference Energies and Calibration Details) for more details about calibration.

“The Elements” Section:

Includes wide scan survey spectra, high energy resolution spectra, and valence band spectra for the elements Ag, Al, Ar(+), As, Au, B, Ba(+), Be, Bi, Br(-), C, Ca(2+), Cd, Ce(4+), Cl(-), Co, Cr, Cs (+), Cu, Dy, Er, Eu, F(-), Fe, Ga, Gd, Ge, Hf, Hg, Ho, I(-), In, Ir, K(+), La(3+), Li(+), Lu, Mg, Mn, Mo, N(3-), Na(+), Nb, Nd, Ni, O(2-), P, Pb, Pd, Pr, Pt, Rb(+), Re, Rh, Ru, S, Sb, Sc, Se, Si, Sm, Sn, Sr(2+), Ta, Tb, Te, Ti, Tl, Tm, V, W, Y, Yb, Zn, and Zr.

If the element is part of insulating chemical compound, then a C (1s) spectrum is also provided to allow the user to correct for sample charging. All narrow scan spectra are peak-fitted to reveal FWHM, peak asymmetry, and peak separation for spin-orbit pairs. The strong signals observed in the wide scan survey spectra are labeled and tabulated together with rough BE values of those strong signals. The details of the experimental protocol used to produce each of these spectra are provided in the "Instrument and Analysis Details" section. All pure elements, except for Silicon and Selenium, were ion etched prior to analysis.

The “Native Oxides” Section:

Includes wide scan survey spectra, high energy resolution spectra for principal signals of each element, carbon (1s) high energy resolution spectra, and oxygen (1s) high energy resolution spectra found in/on naturally formed native oxides of the elements Ag, Al, As, B, Be, Bi, Cd, Co, Cu, Fe, Ga, Ge, Hf, In, Ir, Mg, Mn, Mo, Nb, Ni, Pb, Pd, Pt, Re, Rh, Ru, Sb, Sc, Se, Sn, Ta, Te, Ti, Tl, V, W, Y, Zn, and Zr. Atomic percentage based tables of surface composition, which reveal the natural oxidative tendencies of the elements and the tendencies of these elements to capture various gases from the air and/or various contaminants introduced to the surface from handling by the original chemical producers. To enhance traceability and to try to determine chemical shifts it was deemed essential to observe the pure metal signal for a set of spectra to be included in this Native Oxide section. The samples used for these measurements were, in general, naturally formed native oxides that were analyzed as received without any treatment of any kind. All of these samples had been stored in a set of drawers which were not air-tight and so the samples were exposed to the normal atmosphere of a laboratory for many months or years.

Note: Most of the native oxides are naturally formed native oxides, but a few of the native oxides are actually “freshly formed” native oxides that were produced by scraping the surface of the oxidized metal with a clean knife and exposing the freshly cleaned surface to the normal atmosphere of the laboratory for a time period between 5 minutes and several days. This scraping was done because the naturally formed native oxide or carbonate film was thick enough to hide the pure metal signal when the samples were analyzed by XPS. This method produces freshly formed native oxides which have probably not reached a thermodynamically stable state.

ORGANIZATION AND DETAILS OF SPECTRAL SETS

Organization of Spectra

A set of spectra for a particular chemical is located by looking for the chemical formula abbreviation written in the upper right hand corner of each page. For the element called "aluminium (Al)" the user will find its chemical abbreviation "Al" in the upper right corner of the pages that belong to that set of data and spectra. The spectra are organized by using the chemical abbreviation. This means that spectra for "antimony (Sb)" can be found by looking for the chemical formula: "Sb".

Contents of Each Set of Spectra

The spectra are presented exactly as printed by the Spectral Data Processor software which is provided in each XI SpecMaster Data-Base system. The first page of a set includes the "Detailed Surface Composition Table" which reports the peak assignments, binding energies, relative sensitivity factors, and Atom % abundance of each major signal contained in the wide scan survey spectrum for that chemical. In the title line of this first page the user will find the full chemical name along with other basic information about the chemical, such as Formula Weight, Chemical Abstract Services number, common name, and the Latin language name of the element if available.

The second page of each set is the wide scan survey spectrum with peak labels for each of the strong signals.

Detailed information about the operating capabilities of the SSI systems and the instrument and analysis conditions used to collect these data are presented in the "Instrument and Analysis Details" section of this book.

The remaining pages of each set are the high energy resolution narrow scan spectra which were obtained by measuring the strongest signals found in the wide scan survey spectrum. These spectra include detailed peak-fit results in a table and display the actual peak-fit results for each spectrum. The binding energies of insulating materials are reported in both raw and corrected form. Based on our research we have used a 285.0 eV value for the C (1s) signal of hydrocarbons for charge referencing spectra. The FWHM values for each peak of a high energy resolution spectrum is adjacent to the binding energy for that peak. The percentage numbers given for each peak is a relative percentage that is based on the intensity of that signal only (It is not an atom % value).

Philosophy of Data Collection Methods

Our philosophy is to collect spectra under analysis conditions that are practical, readily reproduced, and typically used in laboratories that use monochromatic X-ray sources and work under real world practical analysis conditions. We have assumed that the most XPS laboratories need practical reference spectra and will not spend the time or money to produce and to analyze pure, clean surfaces under ultimate energy resolution conditions.

However, we did spend extra time to collect data with above average signal to noise (S/N) ratios which reveal the presence of minor components that might otherwise be missed. In the production of these spectra we did not attempt to clean the surfaces of the native oxides or the insulators which would make charge referencing a difficult task. For practical reasons we used the C (1s) spectra from the naturally formed layer of adventitious hydrocarbons because that signal is the “de facto” standard for charge referencing insulating materials.

The spectral data contained within these handbooks are designed to assist engineers, scientists, analysts, theoreticians, and teachers who use XPS on an everyday basis under practical working conditions. We believe that these spectra will help XPS users to analyze industrial problems, gather reference data, perform basic research, test theories, and teach others. These spectra are designed to be practical tools for everyday use and were obtained under practical working conditions. No attempt was made to produce research grade spectra, but many of the spectra are actually research grade spectra because of the self-consistent methods used.

In the production of some spectra no attempt to produce a pure, clean surface, but some effort was made to produce surfaces with a minimum amount of natural surface contamination if needed. When ion etching was used to clean a material that contained more than one element, then ion etching was done with conditions that should minimize preferential sputtering. For the spectra of pure elements, the surface was strongly ion etched.

Peak-Fitting (Curve-Fitting) of High Energy Resolution Spectra

Peak-fitting was performed by using the software provided with the Surface Science Instruments XPS system. That software allows the user to control the full width at half maxima (FWHM) value of any peak, the binding energy (BE) of any peak, peak areas, the ratio of two peak areas, the energy difference between two peak maxima, the shape of a peak as a sum-function of Gaussian and Lorentzian peak shapes in any peak, and the percentage of asymmetry in any peak.

By empirically peak-fitting the spectra from large sets of closely related materials in a trial and error method and analyzing the trends, it was possible to recognize several fundamental peak-shape and peak-fitting parameters for pure elements, binary oxides, polymers, and semiconductors. We used those empirical results to guide our efforts to peak-fit many of the spectra which had complicated peak shapes. In some cases we used the theoretical ratio of spin-orbit coupled signals to assist the peak-fitting of some spectra and also the energy interval between spin-orbit coupled signals that were derived from pure element spectra. No attempt was made to fit the spectra in accordance with theoretical expectations or calculations.

A reduced “chi-squared” value, which indicates the goodness of a peak-fit, was used to determine if a peak-fit was reasonable or not. Based on practical experience a “chi-squared” value between 1 and 2 implies a relatively good peak-fit. A “chi-squared” value between 2 and 4 implies that the fit has not yet been optimized. A “chi-squared” value larger than 4 implies that one or more signals may be missing from the peak-fit effort.

A Shirley-type baseline was used for all peak-fits. Peak shapes for the main XPS signals obtained from chemical compounds (e.g. oxides, halides, etc.) were typically optimized by using a Gaussian:Lorentzian ratio between 80:20 and 90:10. For pure metals, the Gaussian:Lorentzian ratio for the main XPS signals was normally between

50:50 and 70:30. The main XPS signals for semi-conductor materials usually required a Gaussian:Lorentzian peakshape between 70:30 and 80:20.

From the peak-fitting of the binary oxides, we have observed that FWHM for the C (1s), O (1s) and the main metal signal from the binary oxide are usually in range 1.0-1.4 eV. This trend helped us to decide if we had good charge compensation.

Charge Compensation of Insulating Materials

Charge compensation of insulating materials was normally handled by using the patented SSI mesh-screen together with a low voltage flood gun of electrons which used an acceleration voltage that was adjusted to 3-4 eV for optimum results. The mesh-screen device uses a 90% transmission electro-formed mesh made of nickel metal that is supported above the surface of the sample by mounting the mesh on a conductive metal frame that is grounded to the sample mount. To achieve good charge compensation the mesh-screen is positioned so that the distance between the mesh and the surface of the sample is between 0.5 - 1.0 mm. When the distance between the mesh-screen and the surface of the sample is greater than 1.2 mm, the usefulness of the mesh screen flood gun system was normally null.

The mesh-screen is understood to function as an electron cut-off lense with some tendency to allow incoming flood gun electrons to focus onto the area being irradiated with monochromatic X-ray beam. This occurs because the X-ray beam does not have a uniform flux density over the area of the beam. In effect, the mesh-screen produces a nearly uniform electric potential at the surface of the sample and allows incoming flood-gun electrons to pass through whenever they are needed (on demand).

The mesh-screen was used on every insulating material except for a few materials that were analyzed before the flood gun mesh-screen method was developed.

Abbreviations Used

Due to the limited space provided to describe each sample in each electronic data-file, it was necessary to use various abbreviations. The abbreviations are:

scr = screen used for charge compensation

scrn = screen used for charge compensation

TOA = take-off-angle for the electrons

Aldr = Aldrich Chemical Co.

RMC = Rare Metalics Co.

SPP = Scientific Polymer Products Co. MS

Co. = Metal Samples Company

FG = flood gun,

mesh = mesh-screen used for charge control,

1mm=1 mm height used for the mesh-screen,

semi-con = semi-conductive behavior

conduc, = conductive behavior

Tech = technical grade purity,

pellet = sample pressed into pellet form by pellet press used to make Infrared KBr pellets,

plt = pellet

pel = pellet

INSTRUMENT AND ANALYSIS DETAILS USED TO MAKE XPS SPECTRA

A. Instrument Details (ref 1)

Manufacturer:	Surface Science Instruments (SSI)
Model:	X-Probe S-Probe (upgraded from M-Probe model 2703)
Software Version;	1.36.05 (Compiled in MS-DOS "C" version 6.0)
Analyzer Type:	Fixed Analyzer Transmission (FAT) Fixed Pass Energy = Constant Analyser Energy (CAE) 180° Hemi-spherical (truncated)
Input Lens Field of View:	30° for sample normal to lens axis (1" diameter port) (always larger than X-ray beam; retarding potential scanned)
X-ray Type:	Al ^o monochromatic (one 2 " diameter thin natural SiO ₂ crystal wafer glued onto Zerodur substrate heated to 65° C)
X-ray kV and mA Emission:	10 KV, 1.5-22.0 mA (depending on spot size used)
X-ray Energy Defined as:	1486.7 eV (8.3393 Å), Bragg Angle=78.5°
Excitation Source Window:	0.6 μ aluminum in S-Probe (10μ mylar i n X-Probe)
Angle of X-ray Incidence:	$\alpha = 71^\circ$ (relative to sample normal)
Electron Emission Angle:	$\beta = 0^\circ$ (relative to sample normal)
Angle Between X-ray Axis and Electron Analyzer Axis:	$\phi = 71^\circ$ (fixed, non-variable)

Pass Energy of Analyzer:	150 V for Resolution 4 setting 100 V for Resolution 3 setting 50 V for Resolution 2 setting 25 V for Resolution 1 setting
Type & Size of Input Slit:	Fixed (2 mm X 35 mm); magnetic compression
Type & Size of Output Slit:	None (dispersion limited by hemisphere voltages)
Electron Collection Lens	
Field of View:	$\sim 1 \text{ mm}^2$ for a take off angle = 0° at 1000 eV KE
Electron Collection Lens Efficiency:	7% over 2π steradians
Sample Surface to Tip of Electron	
Collection Lens Distance:	$\sim 33 \text{ mm}$
Crystal to Sample Surface Distance:	$\sim 190 \text{ mm}$
Crystal to X-ray Anode Distance:	$\sim 190 \text{ mm}$
True Background Count of Noise:	< 10 electrons/second at -50 eV (shot noise limited)
Detector Type:	SSI Position Sensitive Detector (PSD), resistive anode, 40 mm X 40 mm, electronically defined as 128 active channels with a maximum electron count rate of 1,000,000
Dead Time:	zero (unless ion etching pure element while collecting data)
Base Pressure:	4.0×10^{-10} torr
Normal Operating Pressure:	1.6×10^{-9} torr
FWHM Diffracted by Natural SiO ₂ :	$\sim 0.25 \text{ eV}$

Power Settings:	200 Watts in a 250 x 1100 μ X-ray beam
	100 Watts in a 150 x 800 μ X-ray beam
	45 Watts in a 80 x 350 μ X-ray beam
	15 Watts in a 40 x 250 μ X-ray Beam
X-ray Induced Current:	1.1×10^{-9} amps for a 600 μ spot in X-Probe
Approximate True X-ray Power :	$\sim 6 \times 10^{-6}$ W in a 600 μ spot
Approximate True X-ray Irradiance:	~ 8 W/m ²
Approximate True X-ray Photon Flux:	$\sim 7 \times 10^9$ photons/sec

B. Experimental Details

Electron Take-Off-Angle:	90° relative to sample surface (unless otherwise reported)
Pass Energies Used:	Wide scans were done at PE = 150 eV Narrow scans were normally done at PE = 50 eV Valence band scans were done at PE=150 eV
X-ray Beam Size Used: (for S-Probe)	Wide scans: 250 x 1500 μ ellipse (at 90° TOA) 250 x 1100 μ ellipse (at 35° TOA) Narrow Scans: 250 x 1500 μ ellipse (at 90° TOA) 150 x 1000 μ ellipse (at 90° TOA)
SSI Mesh-Screen:	A 85% transmission (20 μ diameter wire with 200 μ spacing) nickel metal mesh screen was adhered to a small 25 mm x 25 mm x 1.5 mm (W x L x H) aluminum plate over a 20 mm x 20 mm aperture.

The mesh-screen was placed over all oxide samples so that the distance between the sample surface and the mesh-screen was <1.0 mm but >0.3 mm.

Dwell Time (counting time):	200 milliseconds/channel (usual setting)
Data Transfer Time:	4 milliseconds
Max. Number of Channels:	5000 (channels = data points)
Scan Time for One Wide Scan:	~ 3.5 minutes (using 1024 data points)
Scan Time for One Narrow Scan:	~100 seconds (using 256 data points)
Energy Range:	-100 to +1400 eV (BE range)
Typical Step Size:	0.1 eV/step (i.e. 0.1 eV/data point)

C. Data Processing Details

Baseline Subtraction:	None, unless S/BG gave a small display. When the baseline was removed, the intensity of the lowest point was subtracted from all points.
Data Smoothing:	None
Energy Shifting:	None

D. Sample Details (for Volumes 1-5)

The "Description" given on each XPS spectrum reports the empirical elemental formula for the oxide, purity, source, production lot number, a note, if appropriate, about being conductive or semi-conductive, the abbreviation "scrn" which means that the SSI mesh-screen was used, and a number, and "90": which means that a 90° electron take-off-angle used to collect the data for that sample.

Abbreviations used in the description and their full meaning include: Aldr = Aldrich Chemical Co., RMC = Rare Metallics Co., semi-con = semi-conductive behavior, scrn = SSI mesh-screen used, TOA = electron Take-Off-Angle, Tech = technical grade purity, pellet = sample pressed into pellet form, plt = pellet, pel = pellet, MS Co. = Metal Samples Company in Munford, Alabama USA (Tel 205-358- 4202), SPP = Scientific Polymer Products Inc. in Ontario, New York state, USA (Tel 716-265-0413)

Sources of Elements and Chemical Compounds (for Volume 1)

The pure element samples were obtained from various sources without any specific information about sample purity so pure element samples must be assumed to be pure at the 99%+ level. The "halide" salts used to produce spectra from gaseous or highly reactive elements were also obtained from various sources. These halide samples were obtained as crystalline "windows" which are normally used in Infrared spectroscopy and have purities at the 99% level. The Boron Nitride (BN) sample was a white ceramic electrical standoff which was fractured in air. The copper foil material, which was always used to determine reference energies, were obtained as 99% pure foil which was designed as a multiple purpose foil for use around the home. The gold ingot material, which was also used to determine reference energies was obtained as a 99.999% pure sample from Aldrich Chem. Co..

Source of Polymer Materials (for Volume 4)

A special kit (#205) of the 100 polymer materials was obtained from Scientific Polymer Products, Inc. which is located at 6265 Dean Parkway, Ontario, New York, USA 13519 (Tel 716-265-0413).

Source of Alloys (for Volume 6)

A special kit of 54 metallic alloys was obtained from the Metal Samples Co., which is located at Route #1, Box 152, Munford, Alabama, USA, 36268 (Tel 205-358-4202). This kit includes a materials analysis report on each alloy in weight percents. The National Research Institute for Metals (NRIM) in Tsukuba, Japan has provided a series of various binary alloys made of AuCu and CoNi alloys.

Sources of Semi-Conductor Materials (for Volume 3)

Over the course of many years, many people in the Japanese semi-conductor business have given samples of various semi-conductor materials in crystalline wafer form. Various samples were donated by the Oki Electric Company, Mitsubishi Materials, Canon, and various universities. The source of each material is included with the individual sample descriptions whenever that information was provided.

Sources of Commercially Pure Binary Oxide Samples (for Volume 2)

Most of the commercially pure binary oxides were purchased from the Aldrich Chem. Co.. The packages from the Aldrich Chemical Co. included an "Analytical Information" sheet which described an ICP or AA analysis summary, a production lot number, the Aldrich product number, sample purity number (e.g. 99+%), sample appearance (color and physical form), date of chemical analysis, formula weight and a label on the bottle that reports the melting point, toxicity, Chemical Abstracts registry number and density. The samples from Aldrich were generally quite pure at the surface. Other oxide samples were obtained from either Cerac Inc. (USA) or Rare Metallics Co., Ltd. (Japan). The packages from Cerac Inc. included a "Certificate of Analysis" with an ICP or AA analysis summary, a production lot number, a product number, purity (e.g. 99+%), and mesh size. The packages from Rare Metallics Co. did not include analytical data reports, but instead had stock numbers and a purity statement. Two samples (i.e. SiO₂ natural crystal and Al₂O₃ fused plate) were obtained from in-house sources and do not have any purity reports.

Powdered Samples Pressed into 3mm Diameter Pellet

Until analyzed, all finely powdered samples were kept stored in their original glass or plastic containers, which were packaged inside of plastic-lined aluminum bags. Just prior to XPS analysis, each bottle was opened in the normal air of the room where the XPS system was kept, and a small 50- 100 mg portion of the sample was removed via a clean nichrome spatula and placed in the compression chamber of a hand-operated, stainless steel pellet press. All finely powdered samples were compressed without any chemical treatments, which, if done, may have introduced unusual contamination or produced some change in the samples. The resulting pellets varied in thickness from 0.3 - 0.8 mm.

To avoid iron and /or chromium contamination from the anvil, a thin sheet of paper was placed over the sample in the compression chamber. Any powders, which were clumped together, were very gently pressed into a powder just prior to compression. To avoid unnecessary heat-induced oxidation, those samples which were hard and granular were very gently ground into a fine powder in a agate marble mortar and pestle. As soon as each sample was removed from the compression chamber, it was mounted onto silver (Ag°) paint inside of a 5mm wide round brass boat which was 1.3 mm in height.

Silver paint was used so that conductive oxides could behave as true conductors thereby providing true electron binding energies for those oxides that were indeed conductive. In general, each oxide was exposed to room air for <15 min..

Benefits of Pressing Powders into Pellets (increased counts and simple charge control)

A comparison of the electron counts obtained from powdered samples pressed onto double-sided adhesive tape and positioned at a 35° electron take-off-angle with the electron counts obtained from hand-pressed glossy or semi-glossy pellets positioned at a 90° electron take-off-angle (TOA) revealed that a pellet at a 90° electron TOA produces 3-5 times higher electron counts than a powdered sample pressed onto double-sided tape at a 35° electron TOA.

By pressing the finely powdered oxides into pellets, it was also found the surface charging behavior of these glossy or semi-glossy samples was very easy to control by using the mesh-screen electron flood-gun combination with the flood gun set to 4-6 eV acceleration energy and approximately 0.5 mA filament current.

Problems Caused by Pressing Samples into Pellets

By pressing the finely powdered oxides into pellets, the surface of the resulting samples were usually smooth enough to appear glossy or semi-glossy, but some samples had iron or chromium contamination which indicated that the oxide had undergone a pressure induced reaction with the stainless steel anvil. Very strong hand pressure caused some oxides to react with the stainless steel anvil, but medium hand pressure usually did not produce undesired iron and chromium contamination. All analyses that showed any unexpected contamination were repeated. Other forms of accidental contamination (chlorine or previously analyzed oxides) were caused by insufficient cleaning of the stainless steel anvil, which was normally cleaned with a metal polishing solution (Pikal) and rinsed with distilled water and isopropanol. All analyses that showed any unexpected contamination were repeated.

Solution to Pressure Induced Contamination of Pellets

Experiments on ways to avoid the pressure-induced iron or chromium contamination, produced pellets with semi-smooth non-glossy surfaces which required more effort to produce good charge control.

These non-glossy surfaces also gave electron count rates that were about 10-50% lower than the glossy or semi-glossy surfaces. As a result, it appears that very smooth surfaces, which appear glossy or semi-glossy, greatly simplify efforts to control surface charging under the charge-control mesh-screen and also enhance the electron count rate by 10-50% more than a pellet that has a semi-rough non-glossy appearance.

Extensive experiments on different methods to avoid contamination of the pellets revealed that contamination is minimized or avoided by using freshly cleaned aluminum foil as a "buffer" between the oxide powders and the metals in the steel anvil components. The aluminum foil, which is sold as a kitchen wrap material, is cleaned with 100% isopropanol (isopropyl alcohol) just prior to use. The foil is cut to a size that is readily useful with the pellet press device after it is cleaned. Alternately, we have also used a type of "glycine" paper which is commonly used to as a paper to hold powders when weighing a powdered sample. This "weighing" paper is common in many chemical laboratories and can be substituted for the aluminum foil whenever the pressing results with the aluminum foil produce undesired binding results. The glycine paper method sometimes introduces very small amounts of contaminants which produce a N (1s) and C (1s) signals. The amount of these contaminants is much smaller than the amount of contaminants that occur by simply pressing the powder without any sort of paper or aluminum foil buffers.

Source of Pellet Press Equipment

"Qwik Handi-Press" from Barnes Analytical Division, Spectra-Tech, Inc. 652 Glenbrook Road, Stamford, Connecticut, 06906 (FAX 203-357-0609) Kit: Part # 0016-111 to 0016-121 contains 1,3, and 7 mm die sets. Originally purchased through Aldrich Chem. Co. in 1989.

E. Energy Resolution Details

Table 1: Experimentally Observed Relation Between Energy Resolution

Element (XPS signal)	Resulting FWHM	Resolution Setting	Pass Energy	X-ray Spot Size
Si (2p _{3/2}) crystal - fractured edge	0.38 eV	5	10 eV	40 x 250μ
Si (2p _{3/2}) crystal - fractured edge	0.43 eV	1	25 eV	80 x 350μ
Au (4f _{7/2}) foil - ion etched clean	0.64 eV	5	10 eV	250 x 1000μ
Au (4f _{7/2}) foil - ion etched clean	0.79 eV	1	25 eV	250 x 1000μ
Au (4f _{7/2}) foil - ion etched clean	0.86 eV	2	50 eV	250 x 1000μ
Au (4f _{7/2}) foil - ion etched clean	1.40 eV	4	150 eV	250 x 1000μ
Ag (3d _{5/2}) foil - ion etched clean	0.42 eV	5	10 eV	40 x 250μ
Ag (3d _{5/2}) foil - ion etched clean	0.64 eV	1	25 eV	40 x 250μ
Ag (3d _{5/2}) foil - ion etched clean	0.75 eV	2	50 eV	40 x 250μ
Ag (3d _{5/2}) foil - ion etched clean	1.00 eV	3	100 eV	40 x 250μ
Ag (3d _{5/2}) foil - ion etched clean	1.30 eV	4	150 eV	40 x 250μ
Cu (2p _{3/2}) foil - ion etched clean	0.85 eV	5	10 eV	250 x 1000μ
Cu (2p _{3/2}) foil - ion etched clean	0.94 eV	1	25 eV	250 x 1000μ
Cu (2p _{3/2}) foil - ion etched clean	1.06 eV	2	50 eV	250 x 1000μ

Cu (2p _{3/2}) foil - ion etched clean	1.60 eV	4	150 eV	250 x 1000μ
Cu (2p _{3/2}) foil - ion etched clean	0.85 eV	5	10 eV	150 x 800μ
Cu (2p _{3/2}) foil - ion etched clean	0.96 eV	1	25 eV	150 x 800μ
Cu (2p _{3/2}) foil - ion etched clean	1.05 eV	2	50 eV	150 x 800μ
Cu (3s) foil - ion etched clean	2.35 eV	2	50 eV	250 x 1000μ

Table 2: Theoretical Analyzer Resolution versus Pass Energy Settings

Theoretical Analyser Resolution	Pass Energy	Effective Detector Width
0.25 eV	25.0 eV	3.5 eV
0.50	50	7.0
1.00	100	14.0
1.50	150	21.0

F. Energy Scale Reference Energies and Calibration Details (ref. 8)

From May 1986 to January 1993

Energy Scale Reference Energies: 932.47 eV for Cu (2p_{3/2}) signal
122.39 eV for Cu (3s) signal
83.96 eV for Au (4f_{7/2}) signal
Binding Energy Uncertainty: less than ± 0.08 eV
Digital-to-Analog (DAC) Conversion Setting: 163.88

After January 1993 (Based on NPL reference energies published in 1990)

Energy Scale Reference Energies: 932.67 $<\pm 0.05$ eV for Cu (2p_{3/2}) signal
122.45 $<\pm 0.05$ eV for Cu (3s) signal
83.98 $<\pm 0.05$ eV for Au (4f_{7/2}) signal
Observed Reference Energy: 75.01 $<\pm 0.05$ eV for Cu (3p₃) signal
Binding Energy Uncertainty: less than ± 0.08 eV
Digital-to-Analog (DAC) Conversion Setting: 163.87

Note: NPL has recently revised reference energies to be 932.62 eV for Cu (2p₃) and 83.96 eV for Au (4f₇) for monochromatic systems using an electron take-off-angles of 45°

Reference Energies of Adventitious Hydrocarbon Contaminants

From May 1986 to January 1993 the electron binding energy of adventitious hydrocarbons was assumed to occur at 284.6 eV based on SSI and C. D. Wagner's research and recommendations.

Publications by P. Swift (Surface and Interface Analysis **4**, 47 (1982), S. Kohiki and K. Oki (J. Electron Spectrosc. Related Phenom. **33**, 375-380 (1984), and G. Barth, R. Linder and C. E. Bryson, III (Surface and Interface Analysis **11**, 307-311 (1988) have shown that the electron binding energy for various hydrocarbon contaminants and polymers is not necessarily a constant number. Research by this author indicates that the electron binding energy for adventitious hydrocarbons lies somewhere between 284.4 and 287.0 eV depending on the underlying (oxide) materials. By taking a simple average of all available binding energies, the author has found that 285.0 eV is preferred for hydrocarbons on ion etched metals where the hydrocarbon is many hours old. For naturally-formed native oxides the preferred binding energy is 285.2 eV. Oxide based materials at the far left of the periodic element table (columns 1-4) tend to have higher values (285.2-287.0 eV, while most of the transition metal oxides center around 285.0 eV. Near the far right of the periodic table, the binding energy seems to rise to a 285.2-286.5 eV range (columns 12-14) when the native oxides of those elements are analyzed.

In routine practice, this author prefers to use the 285.0 eV number. Some potential factors that may cause this rather large range of electron binding energies for adventitious hydrocarbon contamination includes the dipole moment at the surface of the oxide material, which is expected to be much stronger than the dipole moment of a pure metal, and also, in the case of naturally formed native oxide films, the thickness of the native oxide, any physical or chemical treatments, the thickness of the adventitious

hydrocarbon layer, and the type of instrument used to analyze the sample. The type of instrument being used may cause different shifts in the observed binding energy of the adventitious hydrocarbon contamination because the source may or may not generate different amounts of low energy secondary electrons from the window that protects the X-ray source. The heat from the source and contamination that degases from a just turned on source may also influence the observed binding energy. Electron flood guns and implanted ions may or may not influence the binding energy of semiconductive materials.

Instrument Stability and Long Term Calibration

Initially each of the two SSI systems, that we have used, was calibrated 2-3 times per week because its ability to maintain accurate voltage settings was unknown. Once it was determined that the systems could maintain reliable voltage settings for 1-3 months, it was decided that good calibration could be maintained by checking and, if necessary, correcting the pass energies of the system on a 2-4 week basis. Each of the two SSI XPS instruments, that we have used, have been calibrated on a routine basis every 2-4 weeks by using SSI's reference energies. By using this method over several years time, it was found that the maximum uncertainty (error in pass energies) was normally $<\pm 0.10$ eV, but a few times rose to ± 0.15 eV or less. In a very rare case, the uncertainty rose to 0.20 eV. Long term use of the SSI systems has shown that the DAC circuit does not change enough to be observed unless the room temperature changes by more than 10 degrees Centigrade. If the room temperature changes within a few hours time by more than 10 degrees or the temperature of the DAC chip is changed by more than 10 degrees, then a >0.1 eV shift, which is much smaller than the reliability of almost all literature BEs, can be observed. Variables, which seem to cause pass energy settings to change slightly, include building line-voltages, ion etching conditions, and the addition or removal of some electrical device.

G. Electron Counting and Instrument Response Function Details

Instrument Response Functions (for the X-Probe System only) (ref 3, 4, 5)

Instrument Response Function: $Q(E)=E^{+0.27}$ for 150 eV PE (ref.3)

Instrument Response Function: $Q(E)=E^{+1.0}$ for 50 eV PE (ref.3)

Signal/Background (S/BG) Ratios for Ion Etched Silver using a 250x1000 μ Spot*

Pass Energy	25 eV	50 eV	100 eV	150 eV
S/BG ratio**	>140	>110	>70	>50

* Using a 90° electron take-off-angle and a smooth Ag°/mylar film.

** The S/BG ratio is a simple numerical ratio of electrons counts at the peak maximum relative to the average electron counts observed at approximately 10 eV lower BE.

Lens Voltage Settings Available via Software under Instrument Calibration

Pass Energy*	29.6-29.8	54.7-54.9	105.1-105.3	155.9-156.2
Detector Widths	3.743	7.486	14.954	22.297
Sensitivity Exponent	-0.1	0.3	0.7	1.1
V1 Offset	30	55	105	155
V1 Slope	0.600	0.611	0.676	0.709

* These pass energies include corrections for instrument work function. True pass energies were set to 25, 50, 100, and 150 eV ± 0.1 eV.

H. Effects of Poorly Focussing the Distance between the Sample and the Electron Lens

If the focus distance between the sample surface and the electron collection lens is poorly adjusted, then the number of electron counts drops very quickly. A 0.5 mm error in focus produces a >300% decrease in counts, but does not produce any observable error in binding energies, which is a common problem with many XPS instruments. A 0.1 mm error in focus produces a 15% decrease in peak area counts and is easily observed as a horizontal displacement in the static (un-scanned mode) XPS signal as observed on the standard CRT display of the detector response. Such a decrease in signal intensity generally urges the operator to correct the focus error so as to maximize the electron count rate. In this

manner, the operator has avoided any chance of obtaining false BE readings and has accurately reproduced a nearly absolute focus point which greatly increases the quantitative accuracy of any unknown sample. Experiments with the Bragg angle alignment of the crystal indicated that the maximum error due to an unusual bad alignment of the crystal would be <0.1 eV. To observe an error greater than 0.1 eV, the electron counts were found to decrease by >50%.

I. Quantitation Details and Choice of "Sensitivity Exponents" (ref 2, 4, 5)

By default, the SSI software uses a 0.7 number as the sensitivity exponent factor for each pass energy setting which are used in an equation that modifies theoretically calculated atomic photo-ionization cross-sections (John H. Scofield, Ph.D.) to generate relative sensitivity factors that are valid for this XPS systems and which can be used to generate valid atomic percentages. The 0.7 value produces a $\pm 10\%$ accuracy in quantitative results for XPS signals obtained by using a 150 eV pass energy and occur within the 0-700 eV BE range. For signals that occur at higher BEs, it is generally necessary to change the sensitivity exponent factor to a 1.1 or higher value (1.4). To measure signals obtained by using other pass energies for quantitation, it is necessary to use other sensitivity exponent factors, if the user desires to maximize quantitative accuracy.

To determine useful sensitivity exponents, it is useful to use freshly ion etched poly-crystalline copper foil to test the validity of the sensitivity exponent for larger BE ranges and different pass energies. By integrating the peak areas of the Cu (2p₁), Cu (2p₃), Cu (3s), Cu (3p) and Cu (3d) signals with a modest amount of attention to baseline end points, it is possible to perform trial and error choices of the sensitivity exponents until a useful number is determined. Once a useful number has

been entered into the computer software routine, then the software can generate "fictional" atomic percentages for each of the integrated copper signals which will generate 20 atom % values with a uncertainty of $\pm 1-2$ atom %. If the exponent factor is severely wrong then the atomic percentages will generate numbers such as 10%, 11%, 26%, 24%, and 29% or perhaps 31%, 28%, 14%, 13%, and 14%.

This trial-and-error approach may require 1-2 hours time and can be done on either wide scan data or more preferably narrow scan data for each of the 4-5 pass energies. This method, in effect, assumes that all five of the relative sensitivity factors for copper are reasonably correct. If wide scan data are used, then this method requires a little extra effort to avoid the satellites of the Cu (2p) signals.

This method, in effect, pretends that the pure copper sample is a standard material that is composed of 5 components which are present in 20 atomic % concentration. The objective is to change the sensitivity exponent until the software generates a 20 atom % result for each of the five copper signals. After useful sensitivity exponents are found, they are tested by analyzing freshly exposed bulk regions of crystalline materials such as SiO₂, Al₂O₃, and NaCl. The high and low BE signals of the NaCl crystal are especially useful to test the validity of the sensitivity exponents.

As further checks, the freshly exposed bulk of common polymers (e.g. mylar or PMMA) or a thin film of high purity silicone oil can also be analyzed. Teflon has repeatedly given a slightly larger than desirable error by comparison to the other materials listed above. For that reason Teflon seems to be a less desirable material to determine useful sensitivity exponent values.

J. Crude Tests of the Reliability of Relative Sensitivity Factors

Crude testing of Scofield's numbers are included in atomic percentage composition tables that give atomic percentages for only one element. This testing used the software's automatic peak area integration software that is reasonably accurate. The results indicate that some of the relative sensitivity factors for some of the weaker signals are less reliable. If, however, all factors are taken into account, then Scofield's numbers are reliable to a 95% accuracy level for truly homogeneous materials. These results are available when using the Spectral Data Processor software.

K. Traceability Details

The definition of traceability reported by Martin P. Seah and Cedric J. Powell in the J. Vac. Soc. Technol. Vol 8, p.736 (1990) publication is: "The property of a result of a measurement whereby it can be related to appropriate standards, generally international or national standards, through an unbroken chain of comparisons." Based on this definition, the following correlations were envisioned.

Traceability of Reference Binding Energies (Calibration)

At this time, there are no international standards for binding energies or reference energies. Numbers which are considered to be standard binding energies (BE), which would lead to traceability in BEs, include (a) those provided by Martin P. Seah at the National Physical Laboratory (NPL) in the United Kingdom (England), and (b) those provided by the ASTM in the USA "Standard Practice for Checking

the Operating Characteristics of XPS Spectrometers" designated as "E 902-88". Other nations also have similar national standards, which tend to imitate those set by the USA and the UK. Recently, many people in the world have been using NPL's reference energies, which have become "de facto" standards but have not yet been accepted by the International Standards Organization (ISO).

There are still many workers and researchers using various numbers provided by the instrument makers. The author of this book was using Surface Science Instruments (SSI) Co. reference energies until December 1992 and then switched to NPL BEs in January 1993. SSI reference energies came from Hewlett-Packard (HP). SSI and HP both used high precision voltage meters from HP to calibrate their ESCA machines (i.e. X, M, and S-Probe and HP-5950 A-type and B-type, resp.). Hewlett Packard was the first company to offer a commercial ESCA system, which used reference energies developed in cooperation with Kai Siegbahn at Uppsala, who effectively developed ESCA into a useful science and received the Nobel Prize.

In a recent effort to improve the accuracy of BEs obtained from pure elements, the S-Probe pass energies were checked and corrected, if needed, almost every work-day for two months to obtain high precision and high accuracy BEs for the pure elements that are metals. This study used the NPL reference energies with Cu (2p_{3/2}) at 932.67 eV with ± 0.02 uncertainty and Au (4f_{7/2}) 83.98 eV with ± 0.02 uncertainty by using 0.02 eV/pt. steps for the calibrations. To determine the "true" BE of each of the pure elements, which were scraped clean in air and then ion etched in vacuum, a 0.05 eV/pt. step was used. A repetitive ion etching (depth profile) style was used to collect wide scan, valence (Fermi edge) band, and narrow scans of the main signals for each metal at 50, 25 and 10 eV pass energies. Each repetitive experiment run lasted about 4 hours. Therefore, if NPL's BE numbers are

accepted as "de facto" international standards, then the ultimate traceability of BEs in this data collection can be related to NPL BE numbers for Cu (2p₃) and Au (4f₇). In a different, but similar manner, the BEs used to calibrate the S-Probe are traceable to Siegbahn's work and the high precision, high voltage meters produced by the Hewlett Packard Company.

Traceability Transfer from Pure Metals to Non-conductive Binary Oxides

A question that should be posed is traceability to the oxide BEs. Traceability begins with NPL's BEs for pure copper and gold as state above. Traceability then transfers to pure element BEs which are based on NPL reference BEs. Traceability then transfers to pure element BEs based on SSI's reference BEs, and then the naturally formed native oxide data published in Volume 2 of our XPS Spectral Handbook series where BEs were measured from pure element signals and also the naturally formed native oxide signals.

Naturally formed native oxides typically have thin oxide films (10-80Å) which, in general, behave as good or true electrical conductors, which allows a direct measure of the true binding energy of many, but not all, binary oxides. To determine if traceability can indeed be transferred to true binary oxides, it was necessary to study the behavior of the naturally formed native oxides by applying various flood gun settings with the samples grounded and insulated. The results from that study can be used to transfer traceability to the experimentally observed BEs of pure binary oxides. The most difficult transfer of traceability occurs for the naturally formed native oxide systems. If the flood gun study was not done, then it is difficult to transfer traceability in a reliable manner from a conductive metal to one of its corresponding non-conductive binary oxides.

Traceability of Instrument Response Function

Copper, gold and silver data obtained from the X-Probe system were submitted to Martin P. Seah at the NPL for a round robin test on transmission function; the results of which were published in *Surface and Interface Analysis*, p.243 (1993). In that publication, X-Probe data, which we contributed, were attributed to group #35. That paper reported that instrument has a $Q(E) = E^{0.27}$ for Rex 4 pass energy (PE=150 V) and a $Q(E) = E^{1.0}$ for the Res 2 pass energy (PE=50 V). If the NPL method is accepted as a "de-facto" standard, even though it is not an internationally recognized standard, then the transmission function and quantitation results of the S-Probe system are traceable to the "metrology spectrometer" at NPL.

Traceability of Relative Sensitivity Factors (RSFs) used for Quantitation

Scofield's theoretically calculated photo-ionization cross-sections are internationally used as the "de- facto" standard theoretical numbers, except in Russia and a few other places, where Band's numbers are preferred but are almost identical to Scofield's. The SSI system uses a very simple equation that modifies Scofield's numbers to generate relative sensitivity factors that are used by the SSI software to calculate atom %s. That equation corrects for pass energy differences, transmission function differences, and inelastic mean free path versus kinetic energy dependency. The SSI system relies on Scofield numbers and that simple equation. Other instrument makers prefer to blend Scofield's numbers and experimentally determined numbers.

Traceability of Sample Purity

The purity of the commercially pure (99+%) binary oxides can be traced to Aldrich's ICP or AA analyses performed by Aldrich. Copies of their results are included in the handbook at the beginning of each group of spectra. Similar data sheets were also obtained for samples bought from Cerac. A set of gold, copper, and silver samples, i.e. "Reference Metal Samples SCAA90" set, kit #367, was obtained from the NPL and used to test the instrument response function of the M-Probe system. Binding energies obtained from those gold, copper, and silver samples were identical to binding energies obtained from our commonplace gold, copper, and silver samples within the expected uncertainty of ± 0.08 eV used for routine instrument calibration.

L. Reference Papers Describing Capabilities of X-Probe, M-Probe, and S-Probe XPS Systems

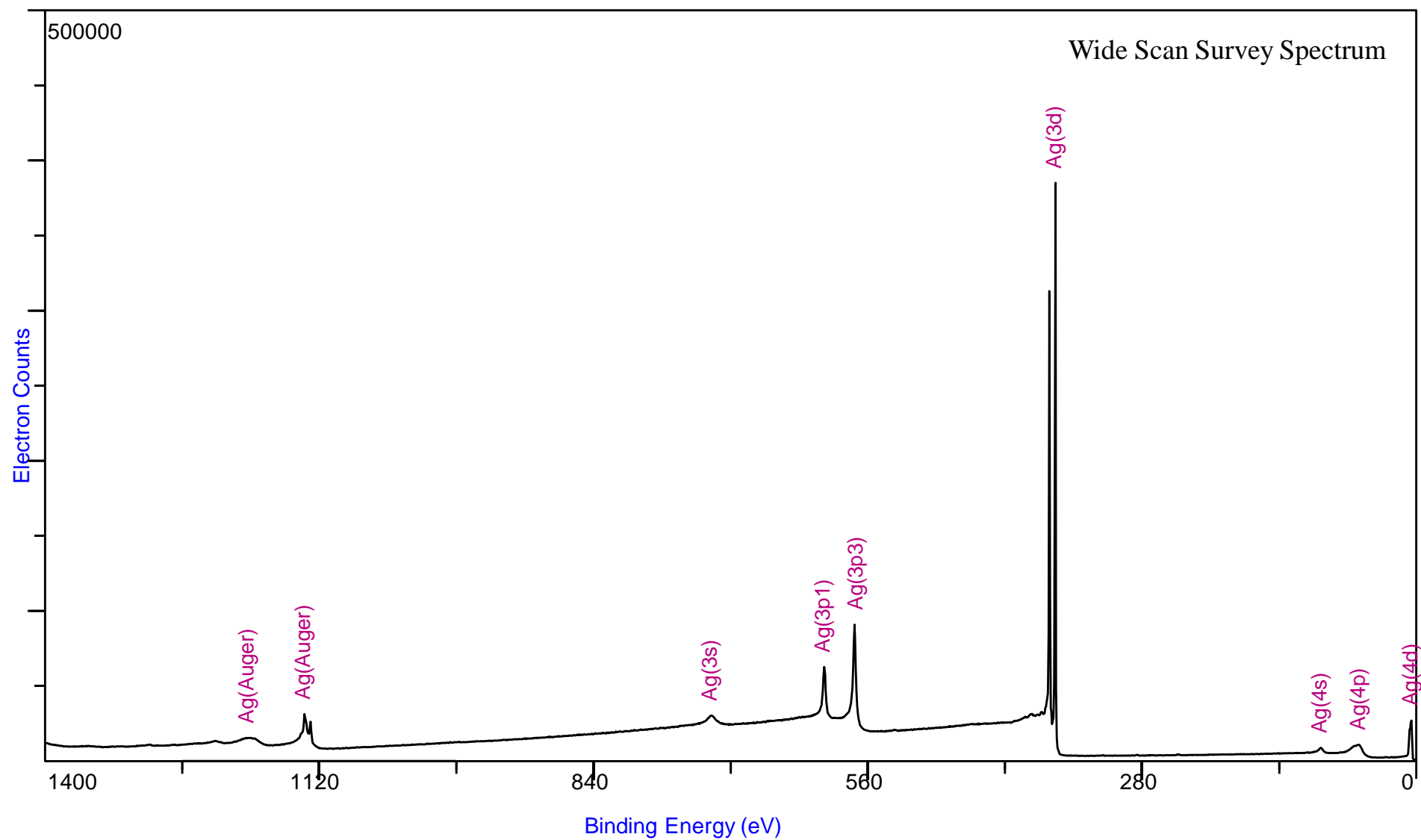
1. Robert L. Chaney, *Surface and Interface Analysis*, **10**, 36-47 (1987) [re: X-Probe]
2. Noel H. Turner, *Surface and Interface Analysis*, **18**, 47-51 (1992) [re: Quantitation]
3. M. P. Seah, *Surface and Interface Analysis*, **20**, 243-266 (1993) [re: Response Function]
4. L.T. Weng et al, *Surface and Interface Analysis*, **20**, 179-192 (1993) [re: Response Function]
5. L.T. Weng et al, *Surface and Interface Analysis*, **20**, 193-205 (1993) [re: Response Function]
6. B. Vincent Crist, *Surface Science Spectra*, **1**, 292-296 (1993) [re: KBr spectra]
7. B. Vincent Crist, *Surface Science Spectra*, **1**, 376-380 (1993) [re: Ar/C spectra]
8. M. P. Seah, I.S. Gilmore, and G. Beamson, *Surface and Interface Analysis*, **26**, 642-649 (1998)

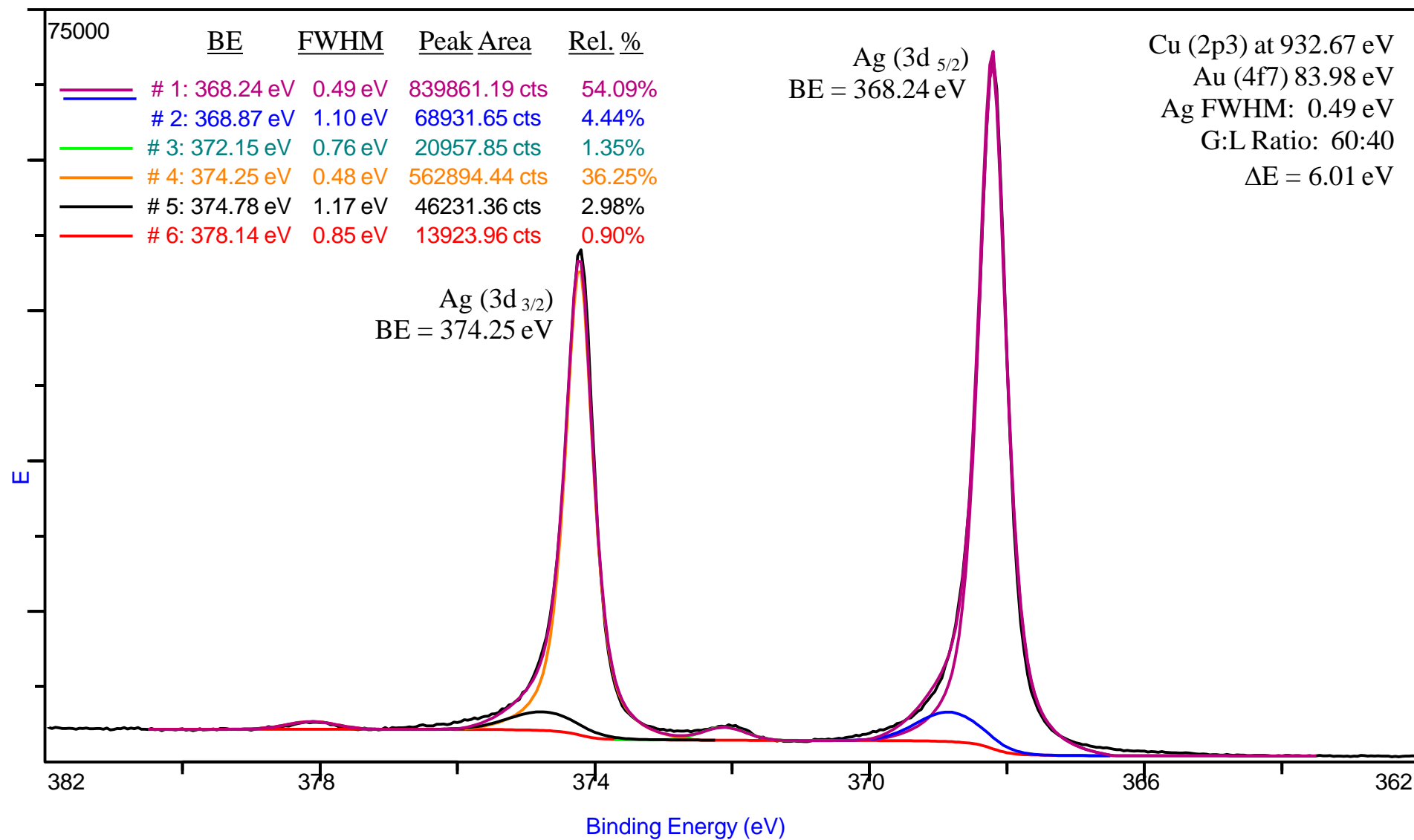
The Elements

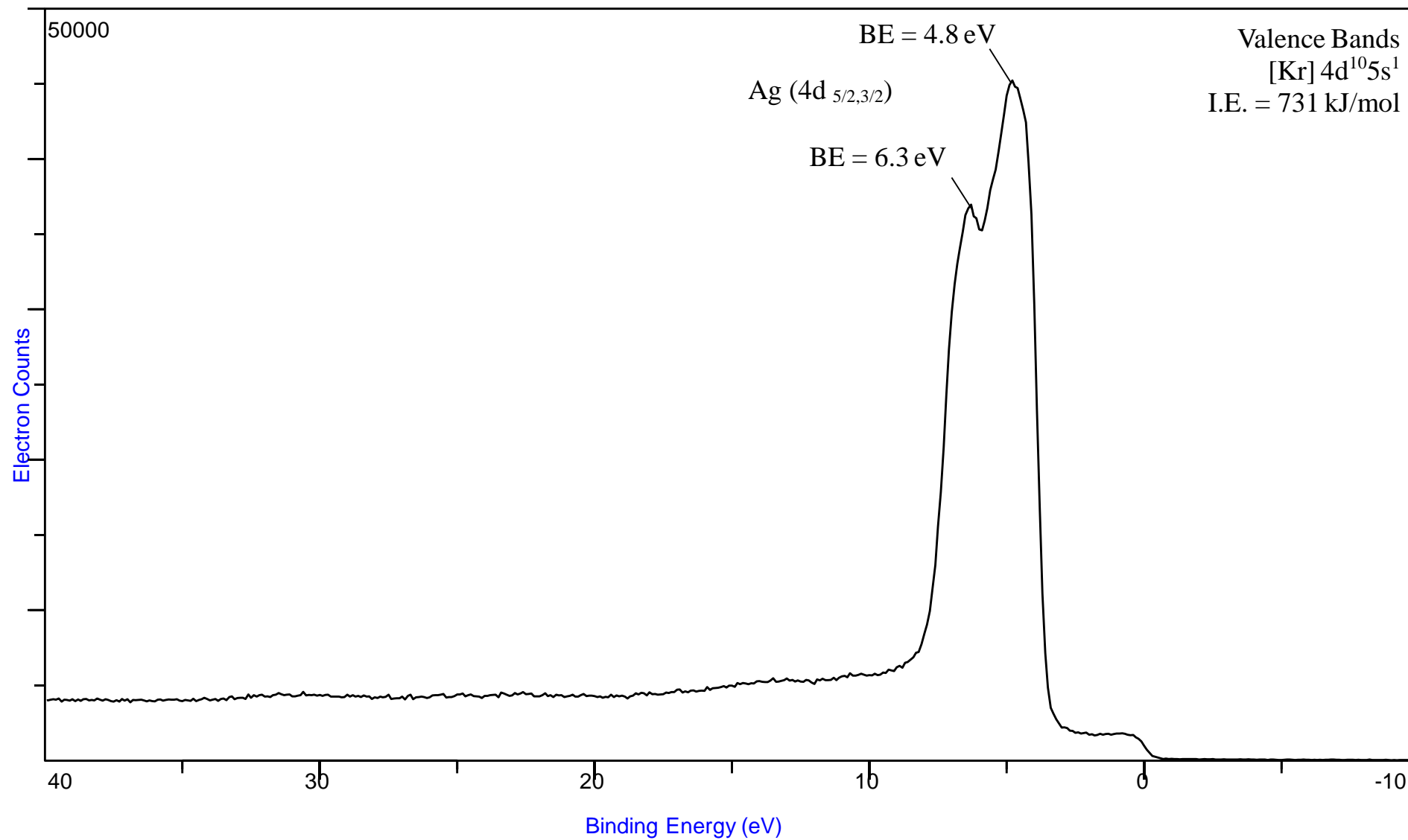
Detailed Surface Composition Table

Description: Silver (Ag) [Argentum => Ag]
 Sum of 15 individual spectra after repetitive ion etching
 Date: Tue Mar 1 1994

<u>Signal</u>	<u>Corrected</u> <u>BE</u>	<u>Exper.</u> <u>BE</u>	<u>Sens</u> <u>Factor</u>	<u>Norm</u> <u>Area</u>	<u>Relative</u> <u>Area</u>
Ag Auger	1192.7	1192.7	0.00	56994	117296
Ag Auger	1134.9	1134.9	0.00	123548	0
Ag3s	719.6	719.6	2.68	43435	16218
Ag3p1	604.0	604.0	3.79	98589	26023
Ag3p3	573.6	573.6	5.87	186287	31709
Ag3d	368.4	368.4	17.78	294202	16546
Ar2s	319.6	319.6	1.96	599	306
C 1s	284.5	284.5	1.00	910	910
Ar2p	241.7	241.7	3.06	1404	459
Ag4s	97.0	97.0	0.66	14200	21419
Ag4p	58.6	58.6	2.13	59667	27983
Ag4d	4.5	4.5	1.62	63425	39240







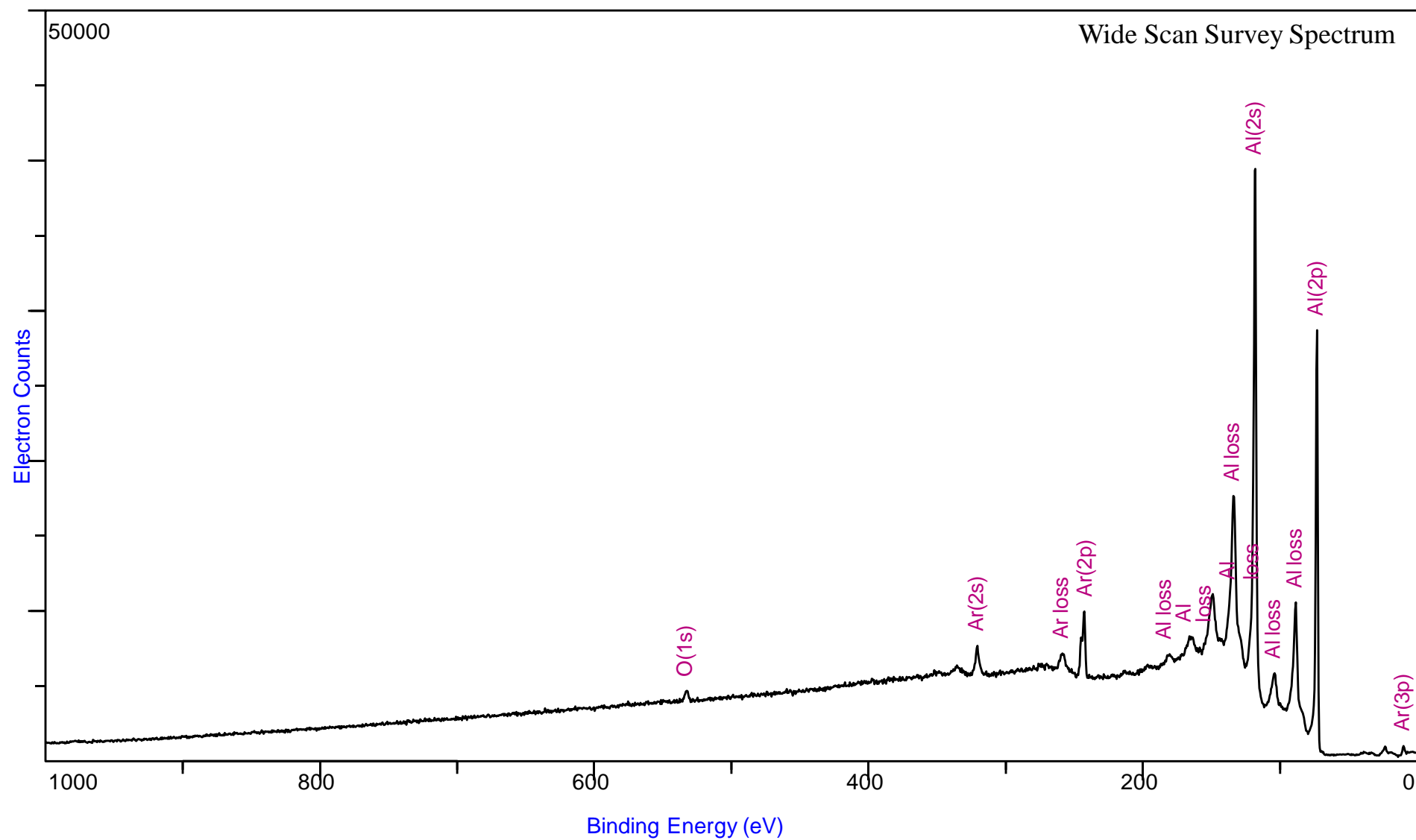
Detailed Surface Composition Table

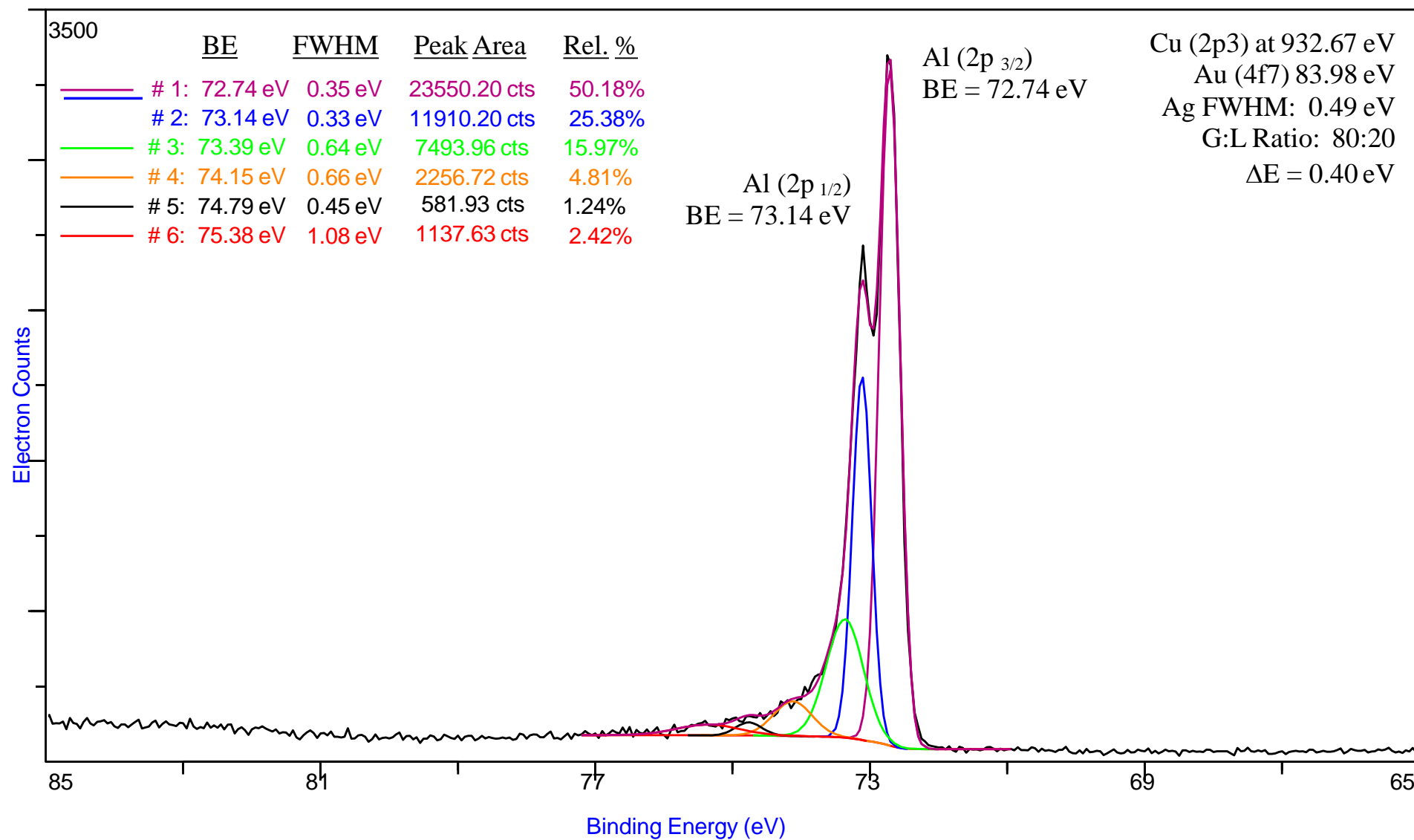
Description: Aluminium (Al) 90 deg TOA

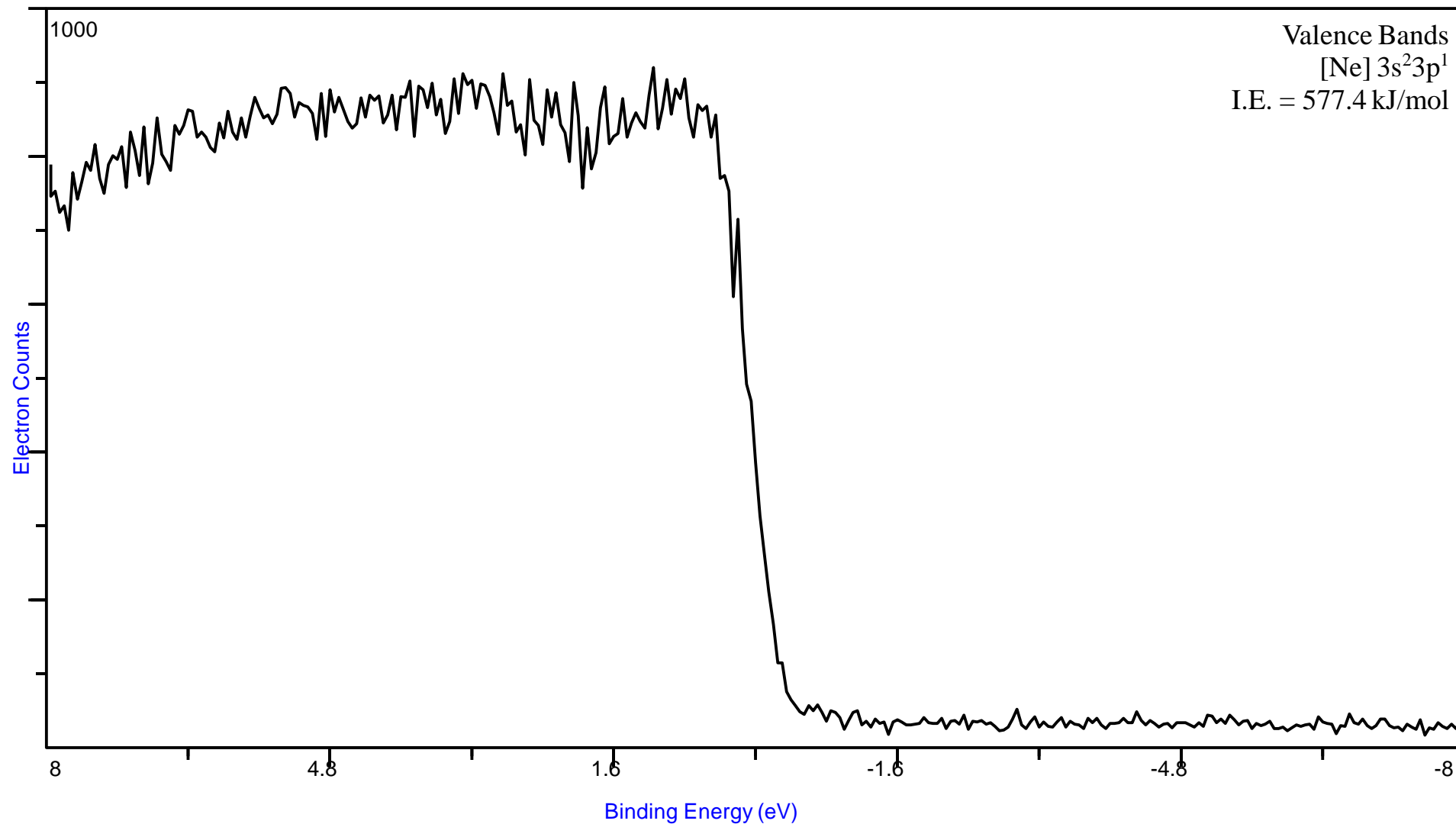
Sum of 10 spectra from repetitive etch/scans

Date: Thu Mar 3 1994

Signal	Corrected BE	Exper. BE	Sens Factor	Norm Area	Relative Area
O 1s	532.3	532.3	2.12	2859	1348
Ar2s	320.5	320.5	1.89	6880	3644
Ar loss	258.3	258.3	6.89	7355	1068
Ar2p	242.5	242.5	3.19	13927	4366
Al loss	180.1	180.1	0.00	3099	0
Al loss	165.4	165.4	0.00	8634	1021
Al loss	148.8	148.8	0.00	19410	0
Al loss	133.4	133.4	0.00	49247	0
Al2s	117.9	117.9	0.90	87391	96758
Al loss	103.7	103.7	0.00	10757	0
Al loss	88.2	88.2	0.00	31383	0
Al2p	72.7	72.7	0.67	51411	76273
Ar3p	9.5	9.5	0.32	1678	5196







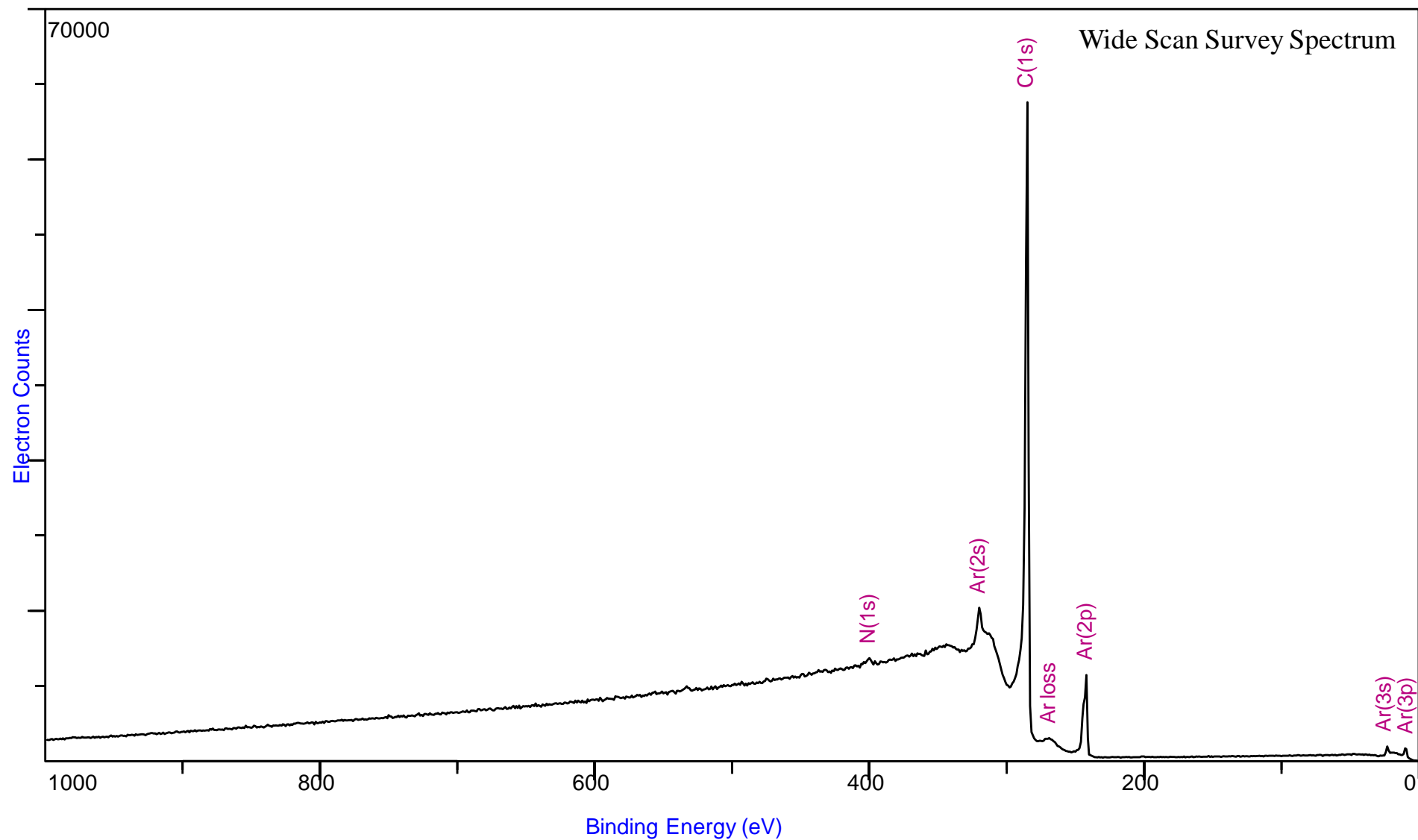
Detailed Surface Composition Table

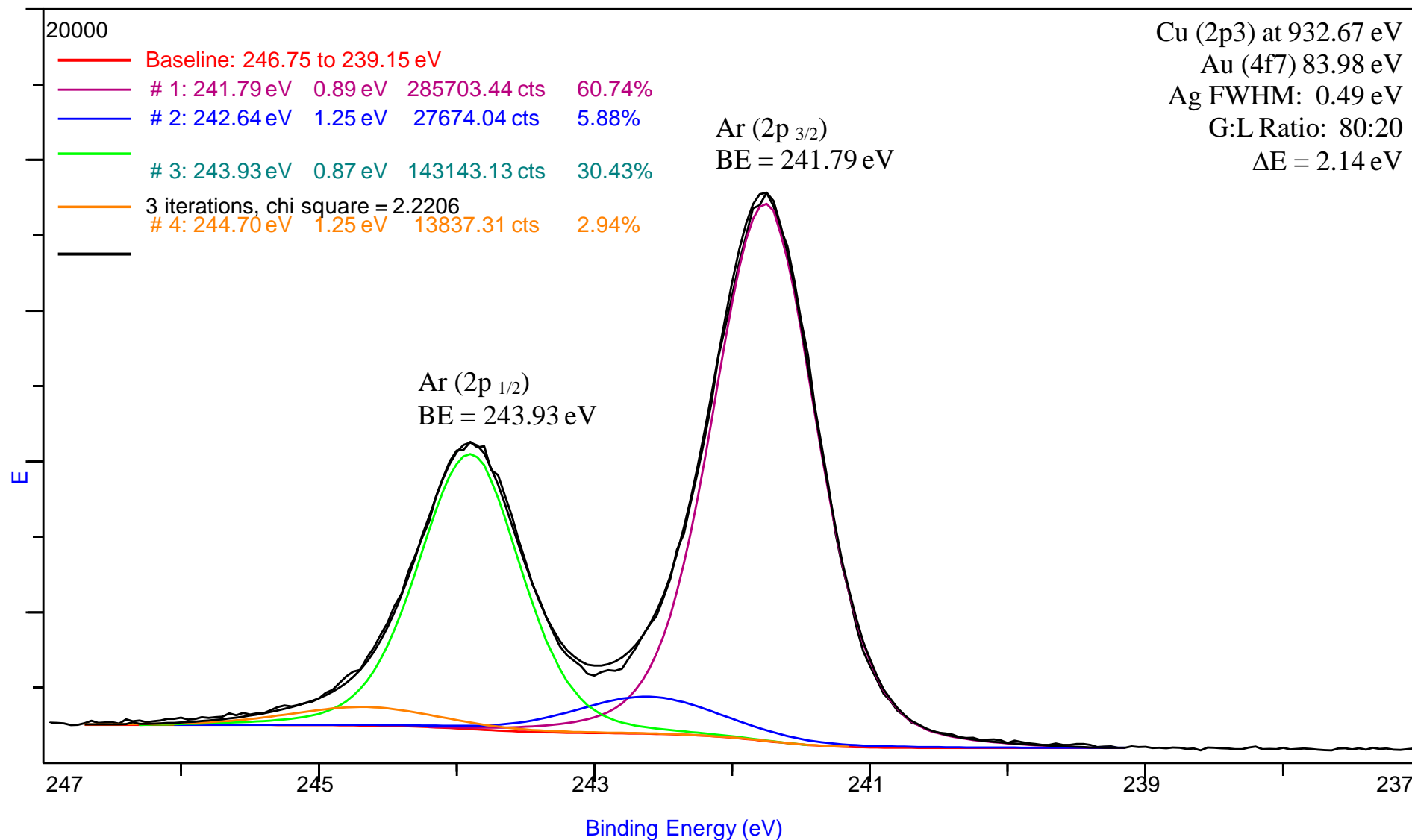
Description: Argon Ions Implanted in Natural Graphite Crystal (90 TOA)

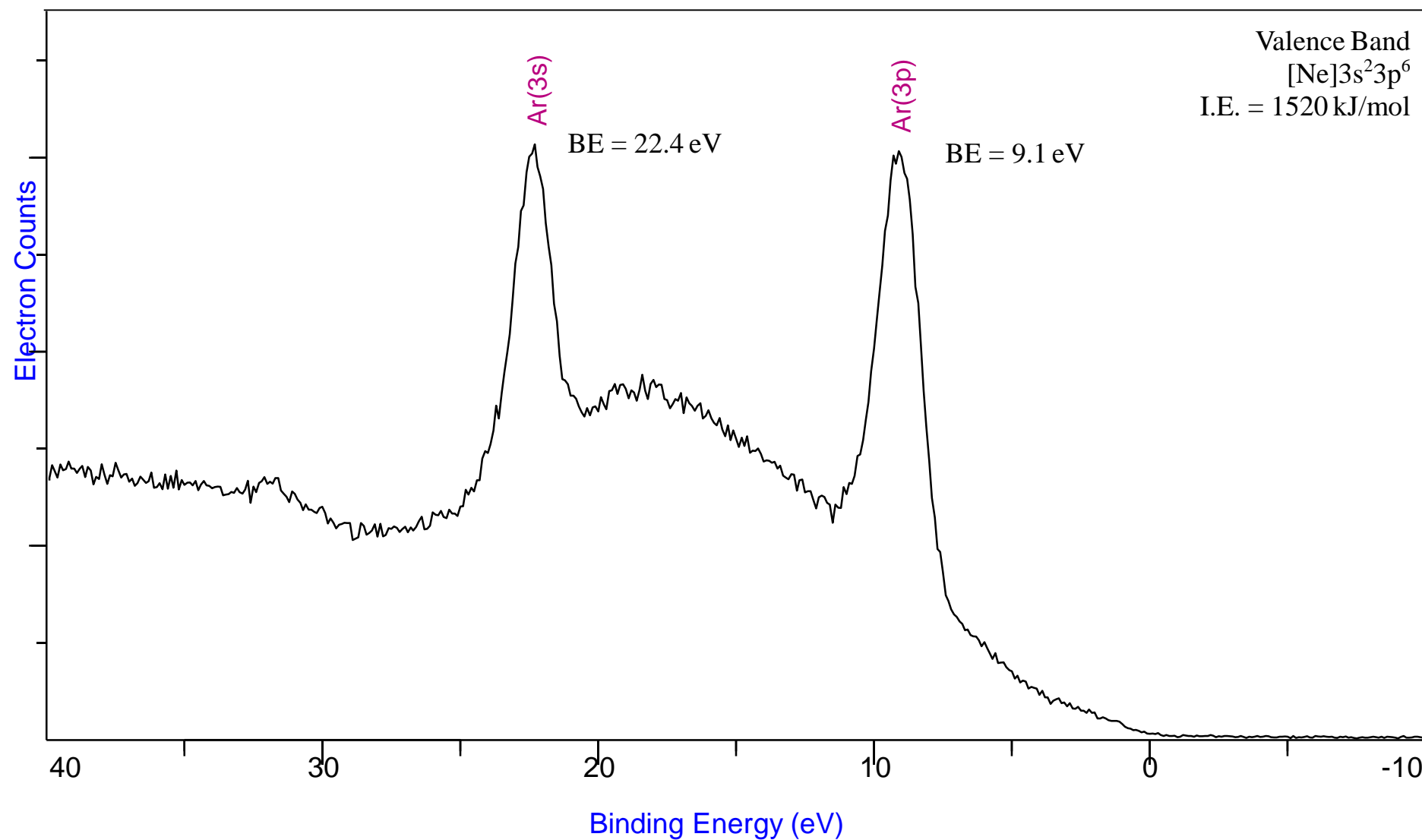
[\(Ref 7\)](#)

Date: Tue Jan 12 1993

<u>Signal</u>	<u>Corrected</u> <u>BE</u>	<u>Exper.</u> <u>BE</u>	<u>Sens</u> <u>Factor</u>	<u>Norm</u> <u>Area</u>	<u>Relative</u> <u>Area</u>	<u>Atom</u> %
Ar2s	319.5	319.2	1.90	30888	16239	
* C 1s	284.8	284.5	1.00	233917	233887	95.88
Ar loss	268.8	268.5	0.00	7032	0	
* Ar2p	241.8	241.5	3.17	31861	10046	4.12
Ar3s	22.3	21.9	0.29	3946	13713	
Ar3p	8.9	8.6	0.31	2352	7584	







Detailed Surface Composition Table

Description: Arsenic (As)

Date: Thu Mar 10 1994

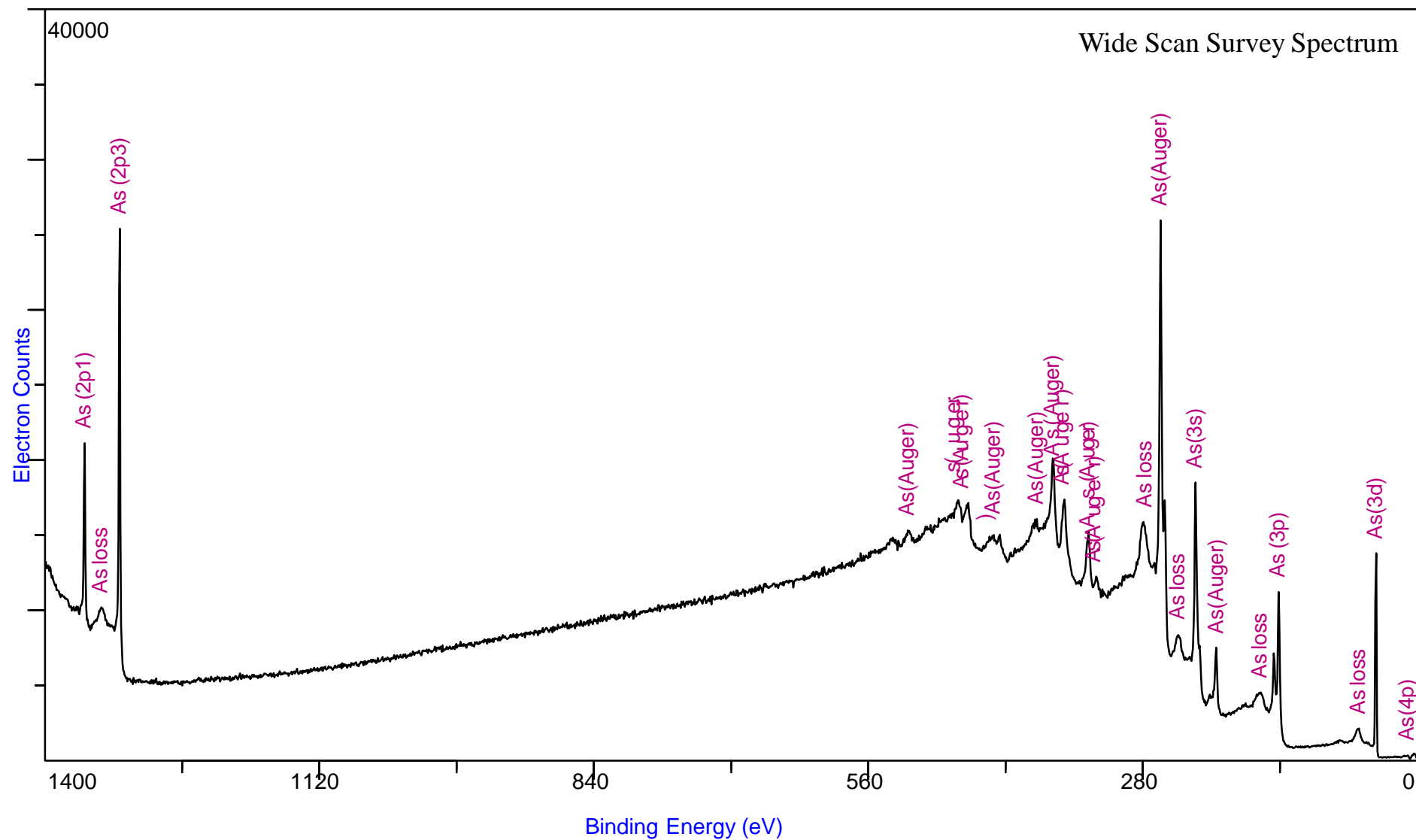
<u>Signal</u>	<u>Corrected</u> <u>BE</u>	<u>Exper.</u> <u>BE</u>	<u>Sens</u> <u>Factor</u>	<u>Norm</u> <u>Area</u>	<u>Relative</u> <u>Area</u>
As (2p1)	1359.5	1359.5	0.00	6333	0
As loss	1342.3	1342.3	0.00	2270	0
As (2p3)	1323.9	1323.9	0.00	16085	0
As Auger	519.0	519.0	0.00	1225	0
As Auger	467.8	467.8	0.00	1584	0
As Auger	457.7	457.7	0.00	2299	0
As Auger	425.5	425.5	0.00	720	0
As Auger	387.5	387.5	0.00	870	0
As Auger	371.2	371.2	0.00	7374	0
As Auger	359.6	359.6	0.00	5447	0
As Auger	335.0	335.0	0.00	4237	0
As Auger	327.0	327.0	0.00	792	0
As loss	279.1	279.1	1.00	7177	7178
As Auger	261.4	261.4	0.00	27159	0

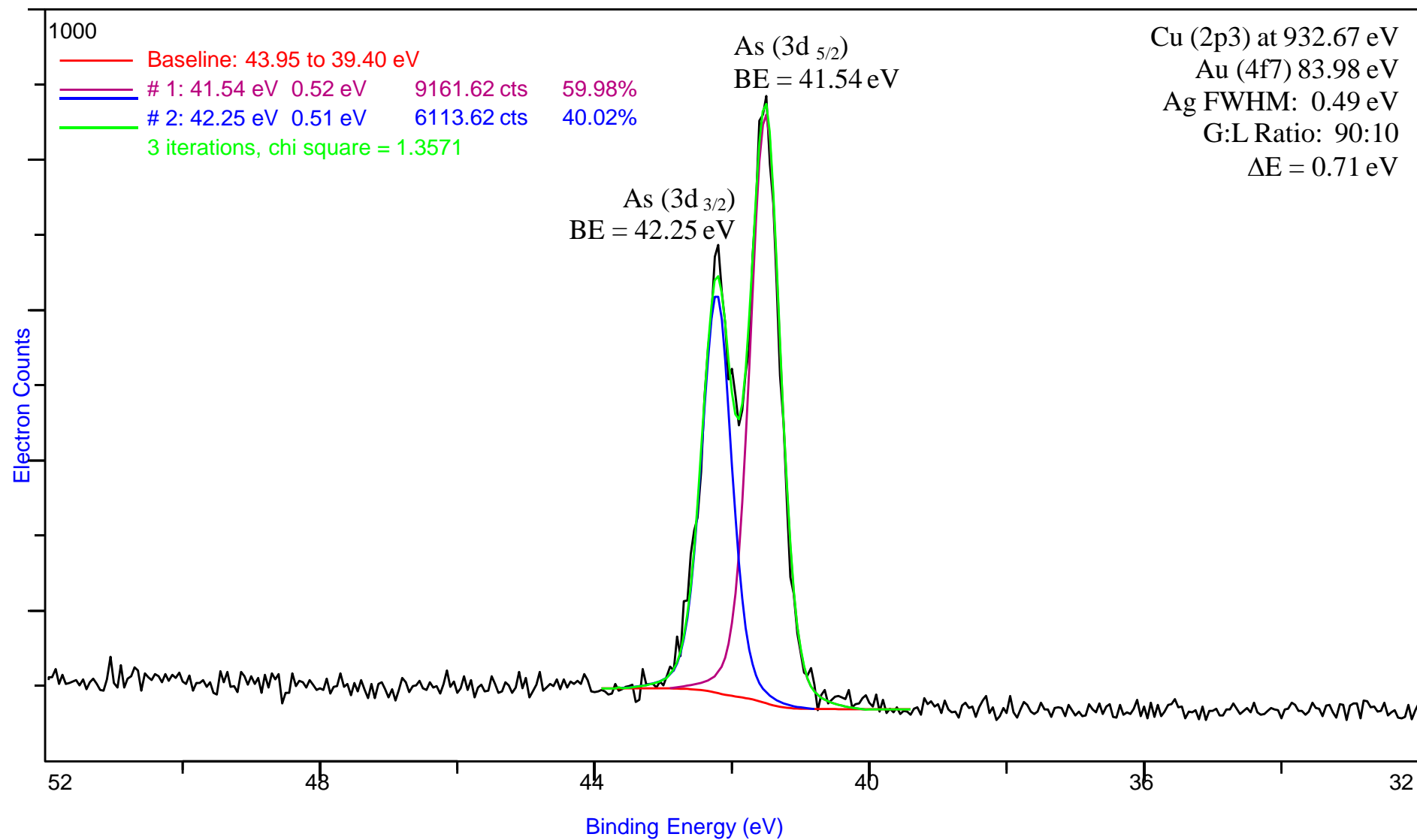
Detailed Surface Composition Table (continued)

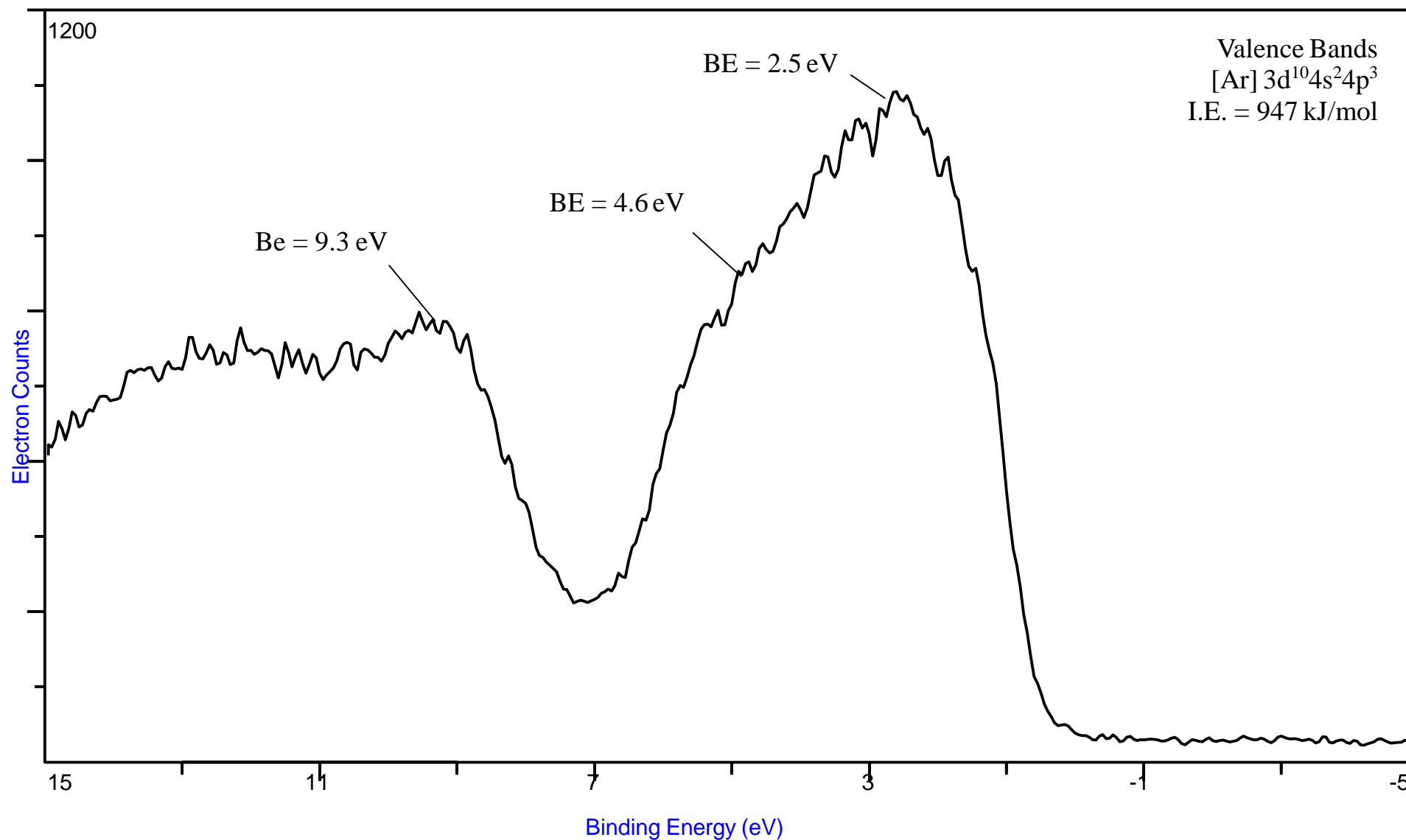
Description: Arsenic (As)

Date: Thu Mar 10 1994

<u>Signal</u>	<u>Corrected</u> <u>BE</u>	<u>Exper.</u> <u>BE</u>	<u>Sens</u> <u>Factor</u>	<u>Norm</u> <u>Area</u>	<u>Relative</u> <u>Area</u>
As loss	243.4	243.4	0.00	2653	0
As3s	225.7	225.7	0.00	13349	109271
As Auger	204.7	204.7	1.34	2677	2002
As loss	159.1	159.1	0.00	1201	0
As (3p)	140.7	140.7	1.42	10842	7637
As loss	59.2	59.2	0.00	1677	0
As3d	41.5	41.5	1.89	5514	2920
As4p	9.1	9.1	0.13	225	1784







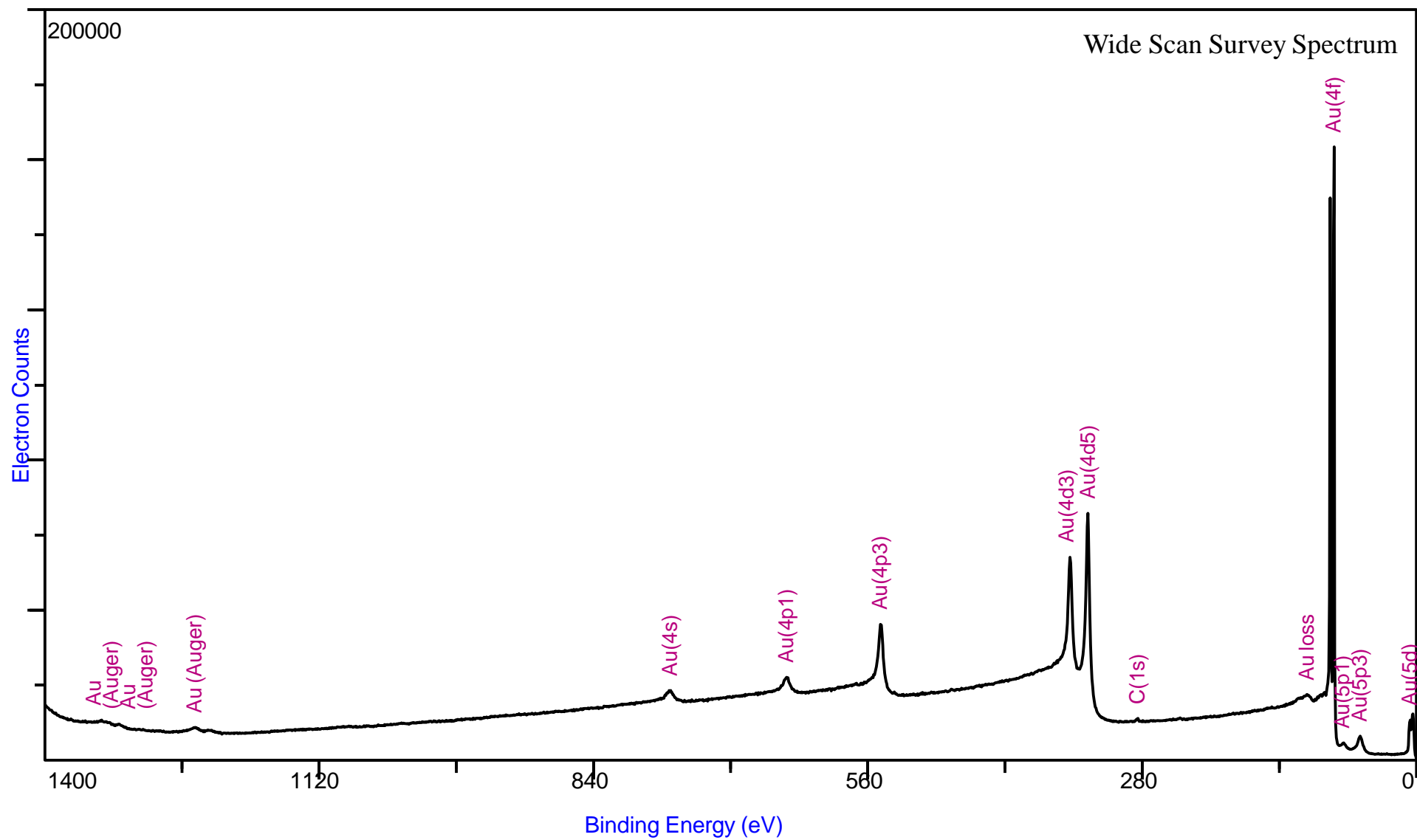
Detailed Surface Composition Table

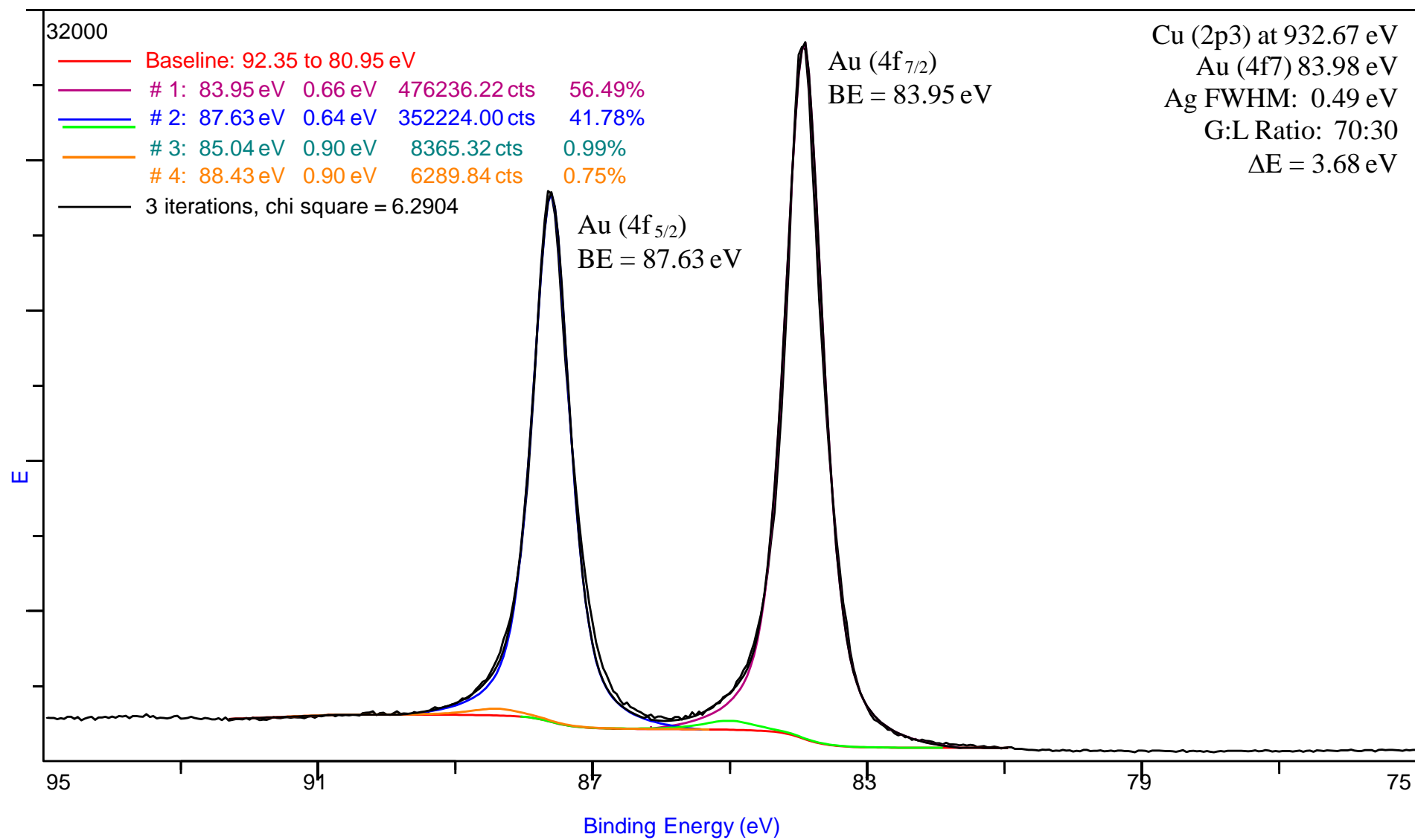
Description: Gold (Au) 90 deg TOA [Aurum = Au]

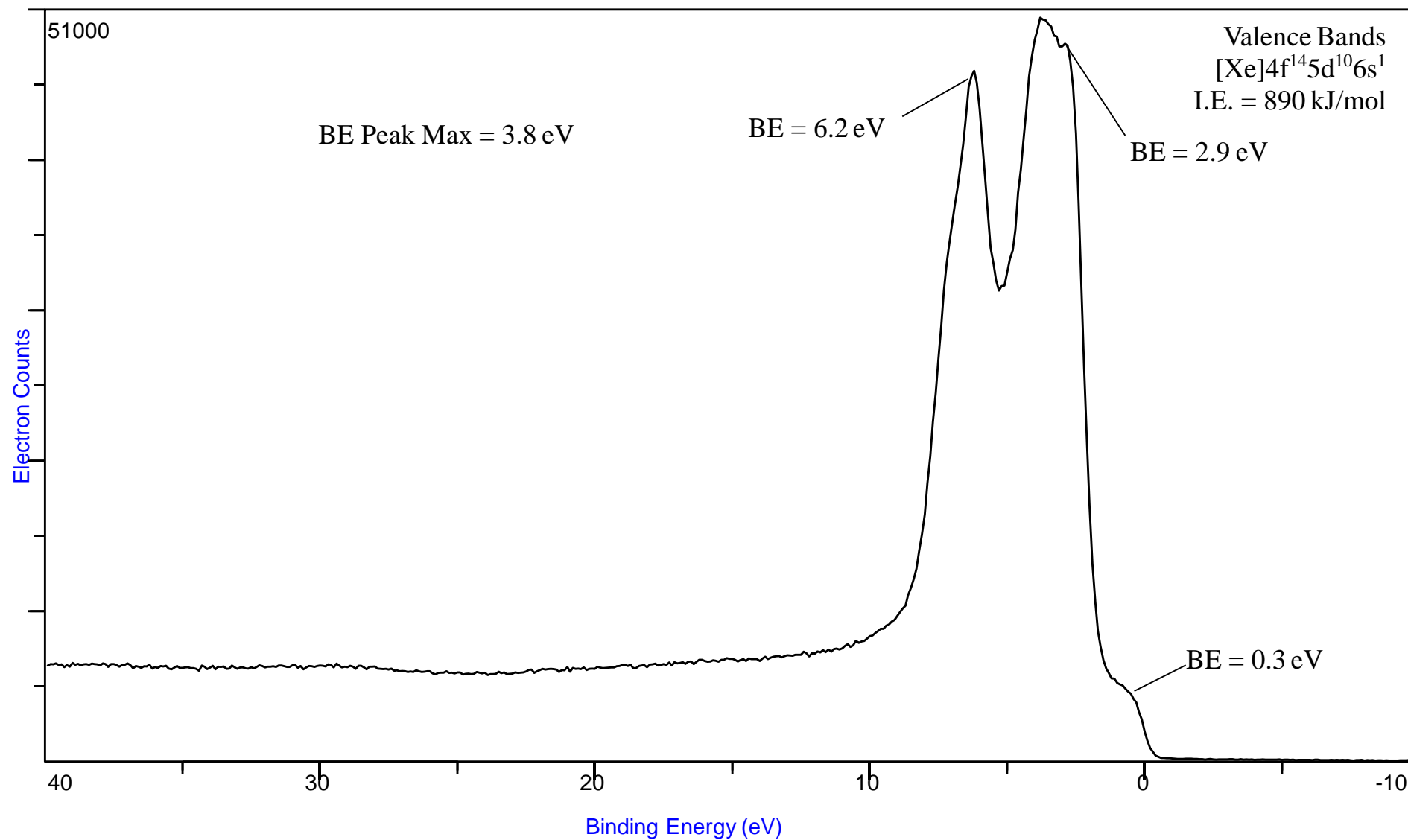
Sum of 15 repetitive etch/scans

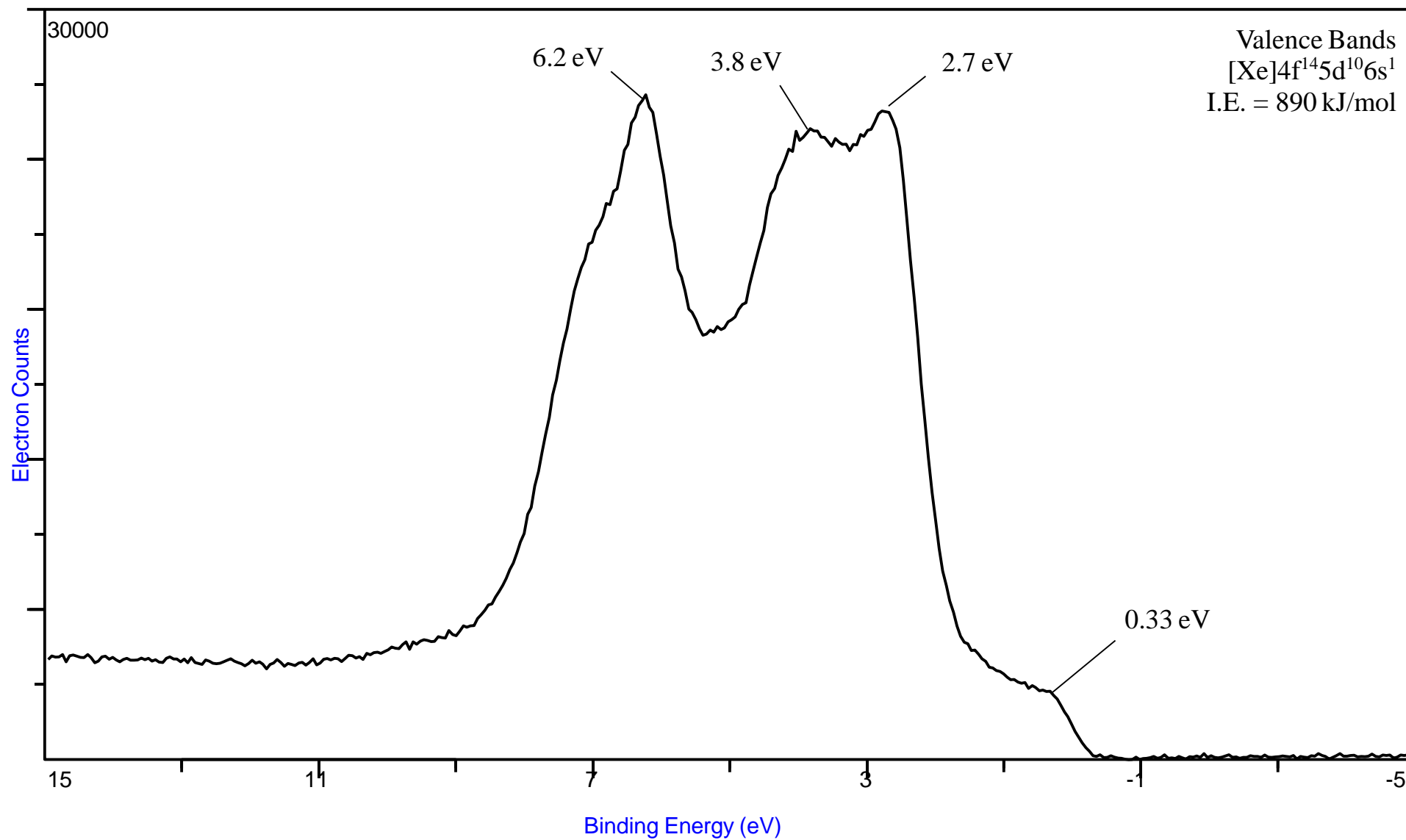
Date: Fri Feb 25 1994

<u>Signal</u>	<u>Corrected</u> <u>BE</u>	<u>Exper.</u> <u>BE</u>	<u>Sens</u> <u>Factor</u>	<u>Norm</u> <u>Area</u>	<u>Relative</u> <u>Area</u>
Au4s	761.2	761.2	1.74	9904	5706
Au4p1	642.4	642.4	1.99	14742	7393
Au4p3	546.3	546.3	5.61	51765	9231
Au4d3	353.0	353.0	7.97	76555	9610
Au4d5	335.0	335.0	11.64	103982	8933
Au4f	83.6	83.6	17.66	208355	11797
Au5p1	74.0	74.0	0.48	1956	4090
Au5p3	56.8	56.8	1.14	11411	10020
Au5d	5.8	5.8	1.89	24461	12977







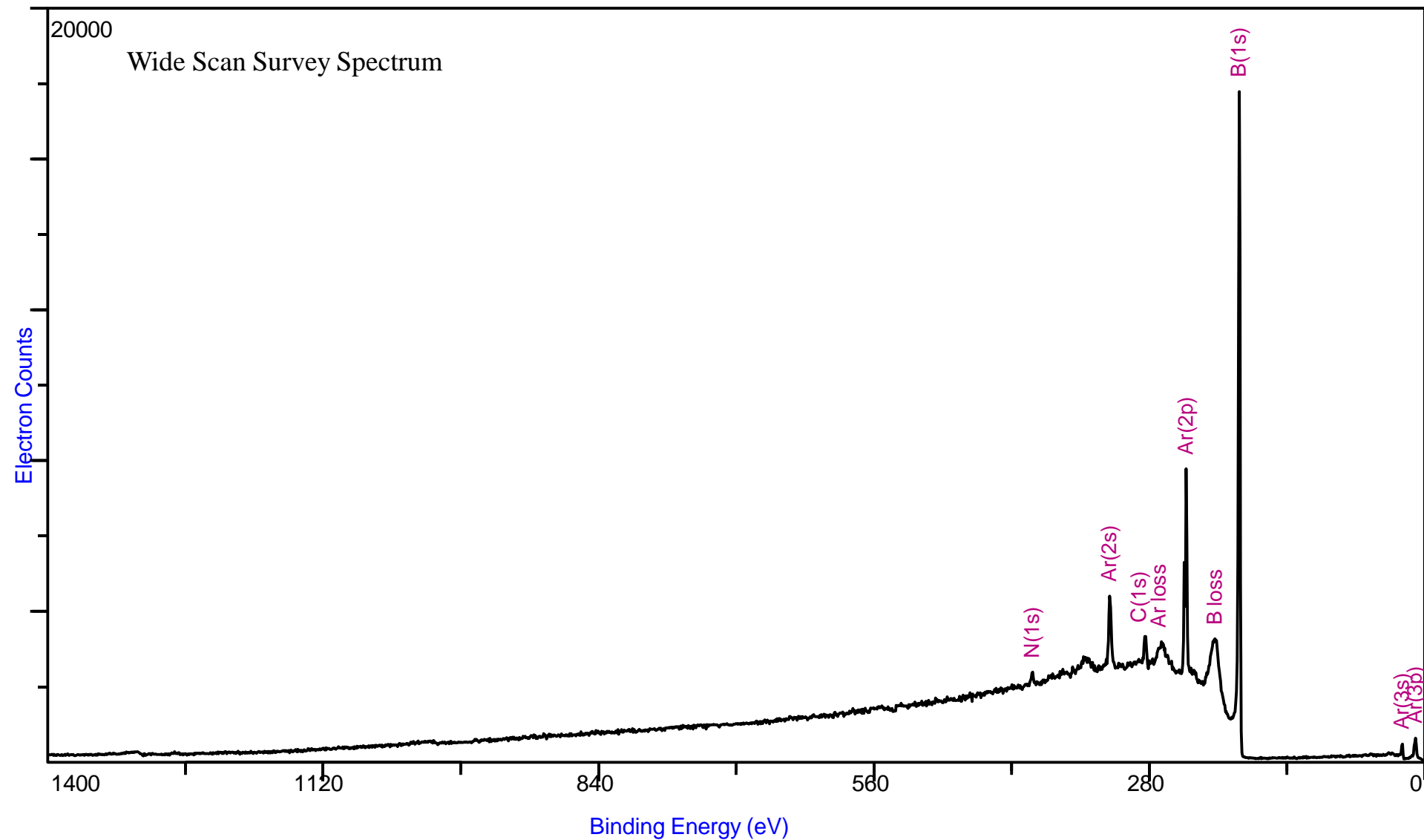


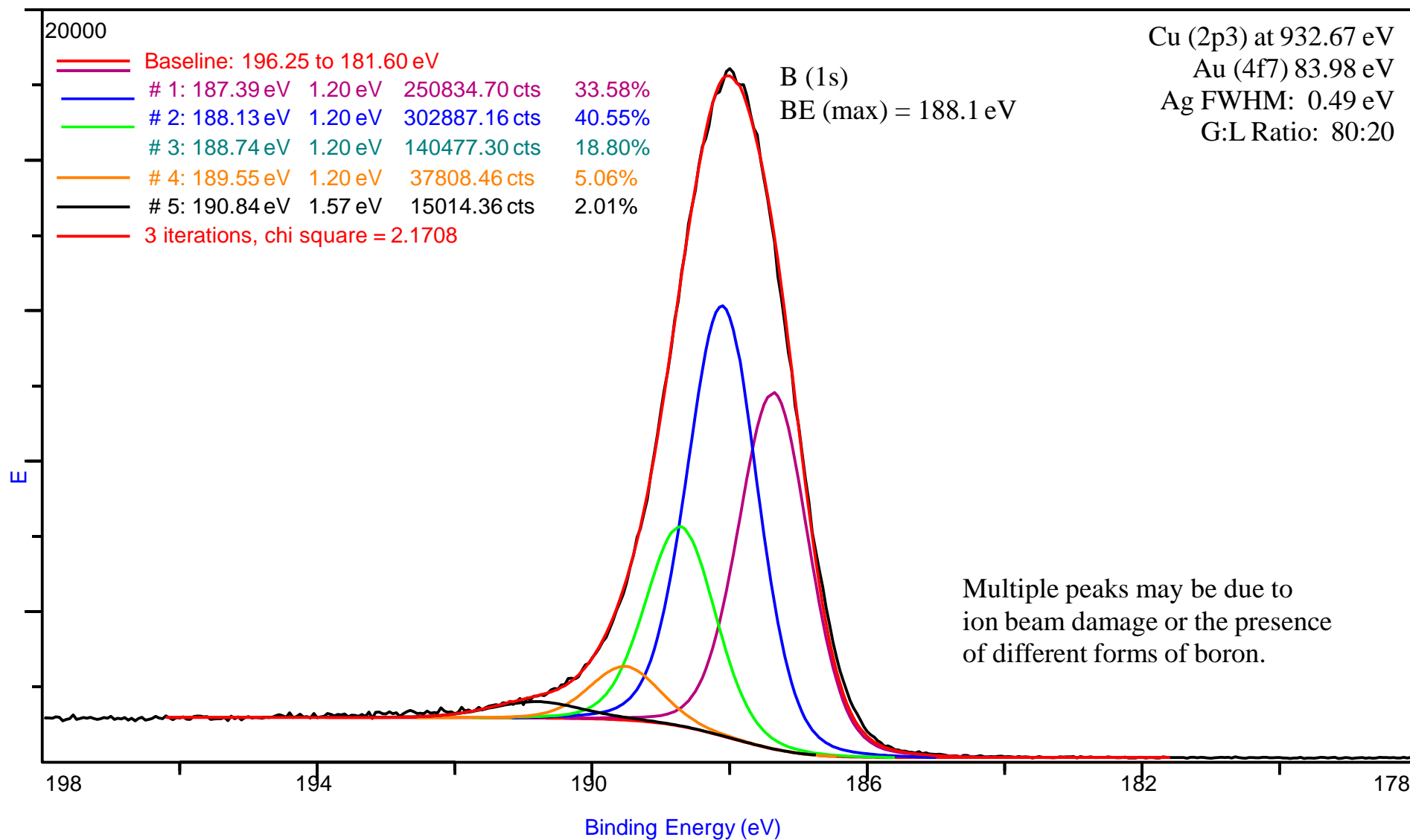
Detailed Surface Composition Table

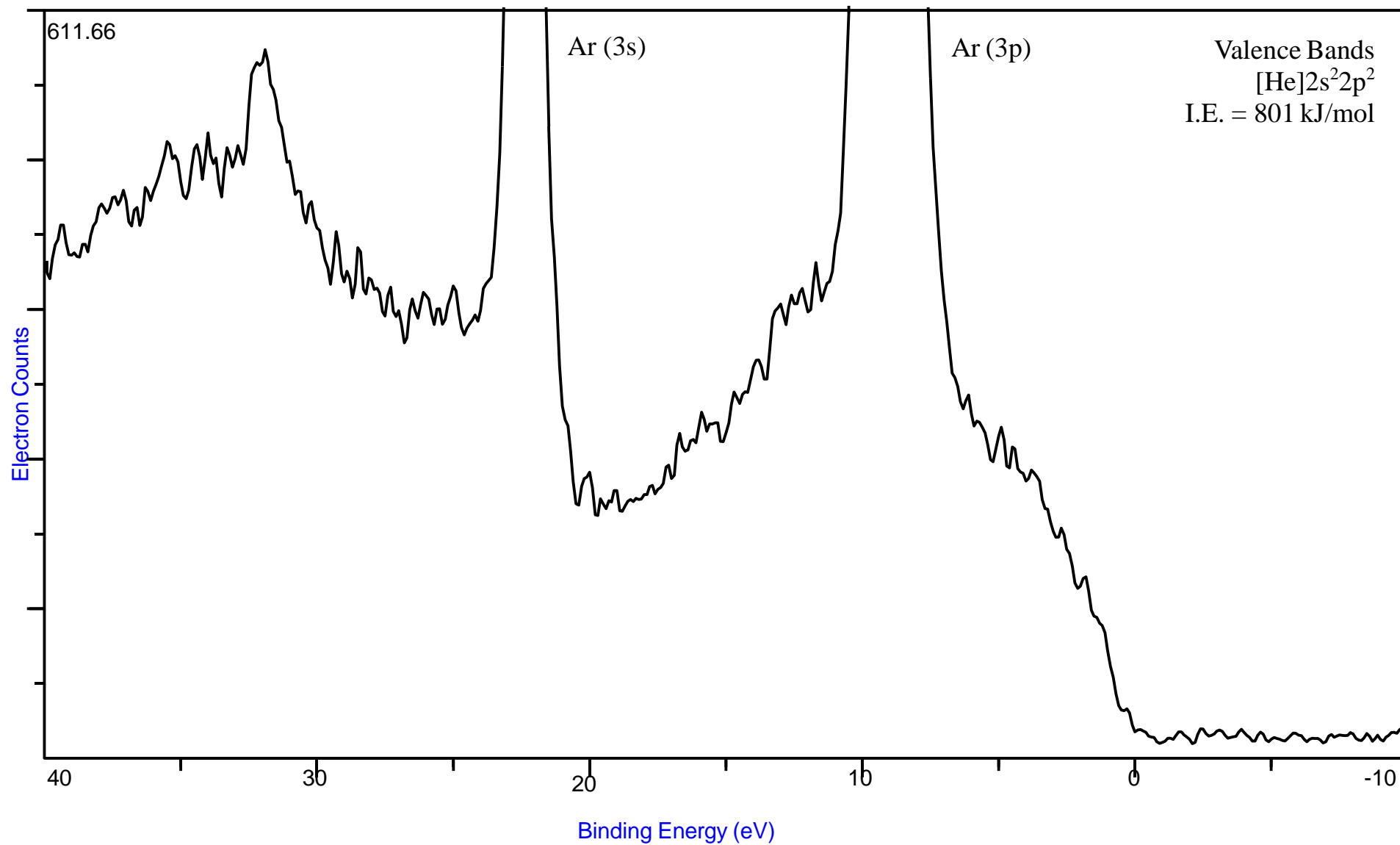
Description: Boron (B): Ion etched clean, 90 TOA

Date: Thu Feb 24 1994

<u>Signal</u>	<u>Corrected</u> <u>BE</u>	<u>Exper.</u> <u>BE</u>	<u>Sens</u> <u>Factor</u>	<u>Norm</u> <u>Area</u>	<u>Relative</u> <u>Area</u>
N 1s	398.2	398.2	1.76	583	331
Ar2s	319.4	319.4	1.96	4312	2202
C 1s	283.4	283.4	1.00	1302	1302
Ar loss	266.9	266.9	0.00	1506	0
Ar2p	241.6	241.6	3.06	8690	2839
B loss	212.6	212.6	0.00	12364	0
B 1s	187.7	187.7	0.49	27345	55744
Ar3s	22.0	22.0	0.24	476	2016
Ar3p	8.5	8.5	0.25	1338	5305





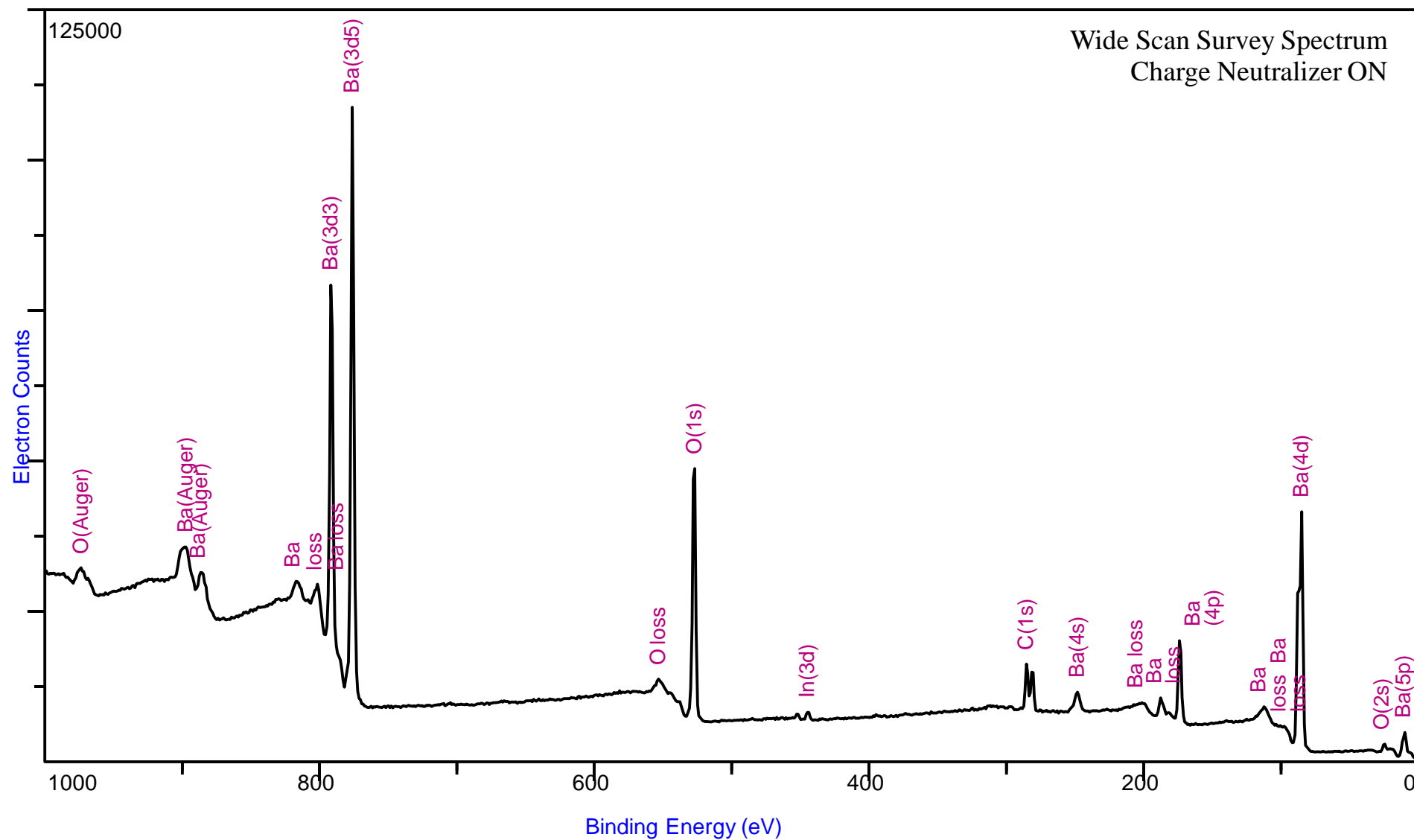


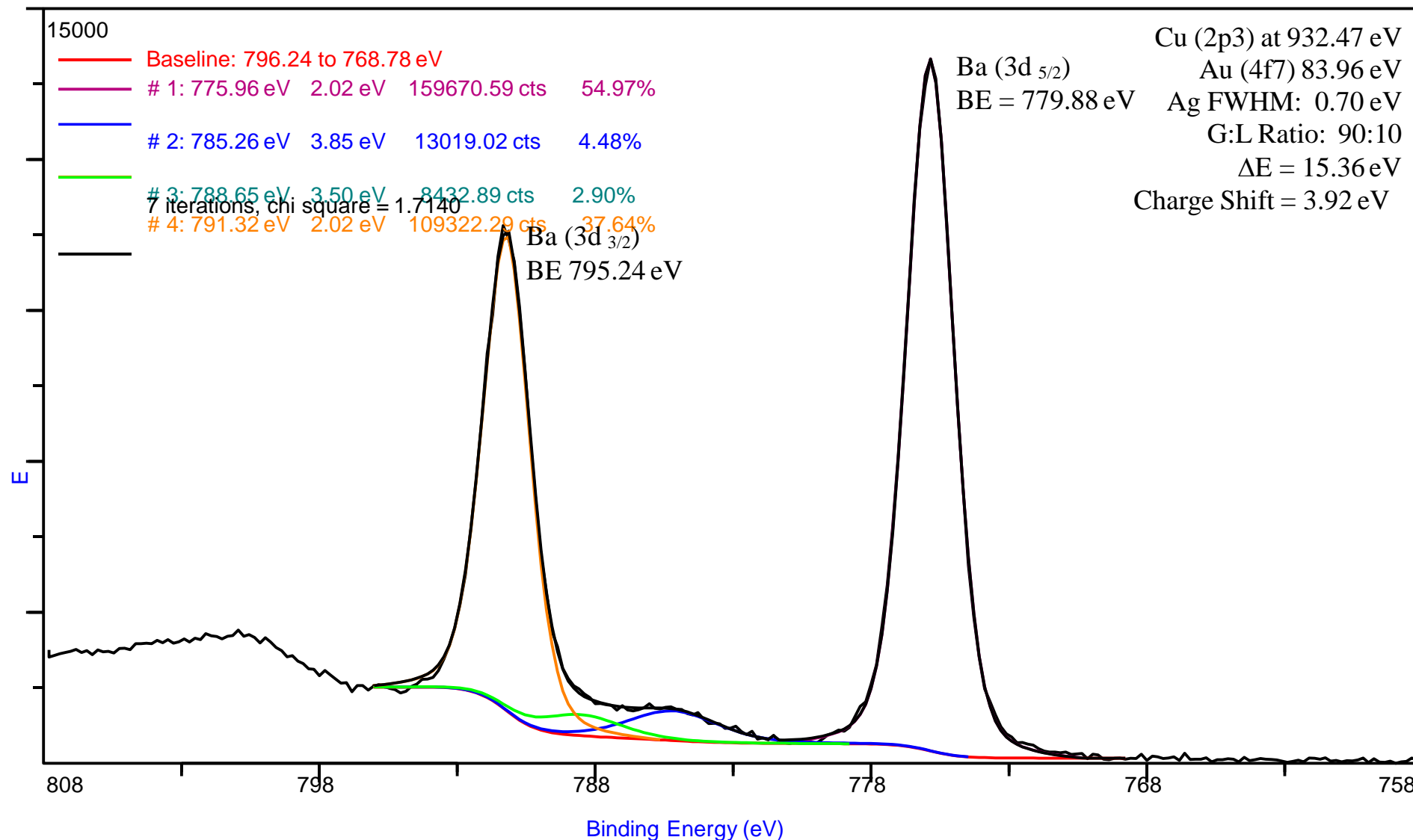
Detailed Surface Composition Table

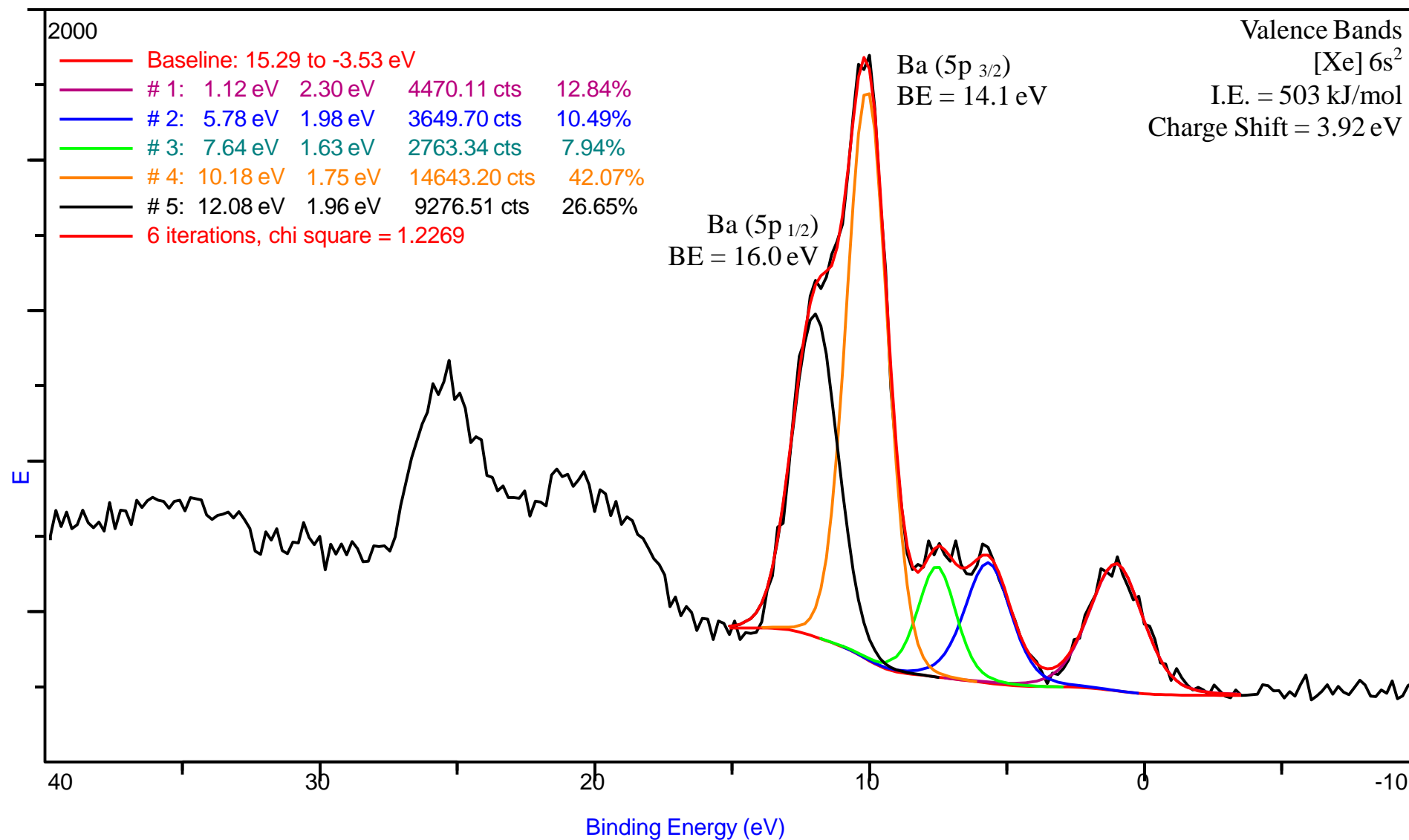
Description: BARIUM (Ba) CARBONATE (90 DEG TOA, Ion Etched Briefly at 4 KeV)

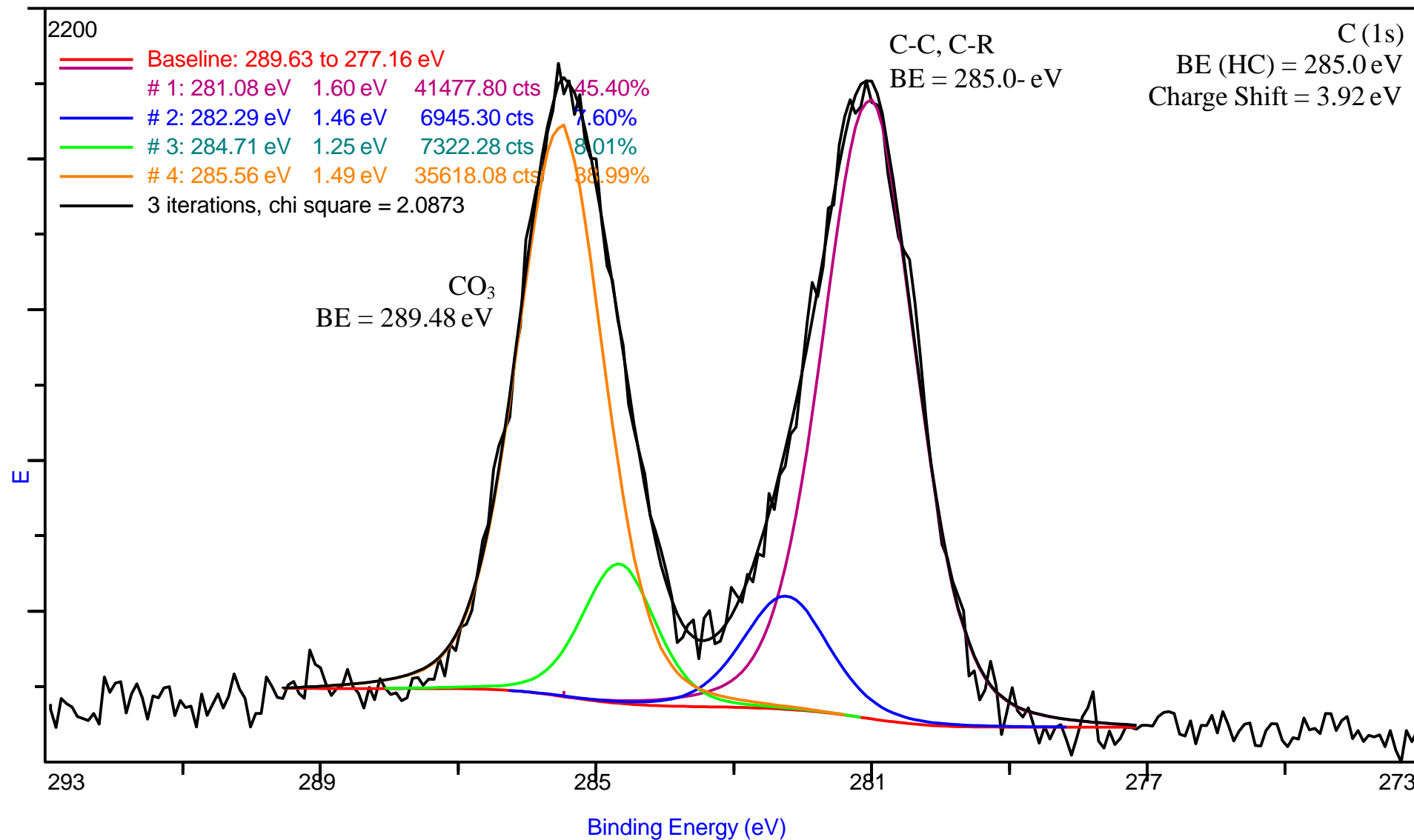
Date: Fri Jul 10 1987

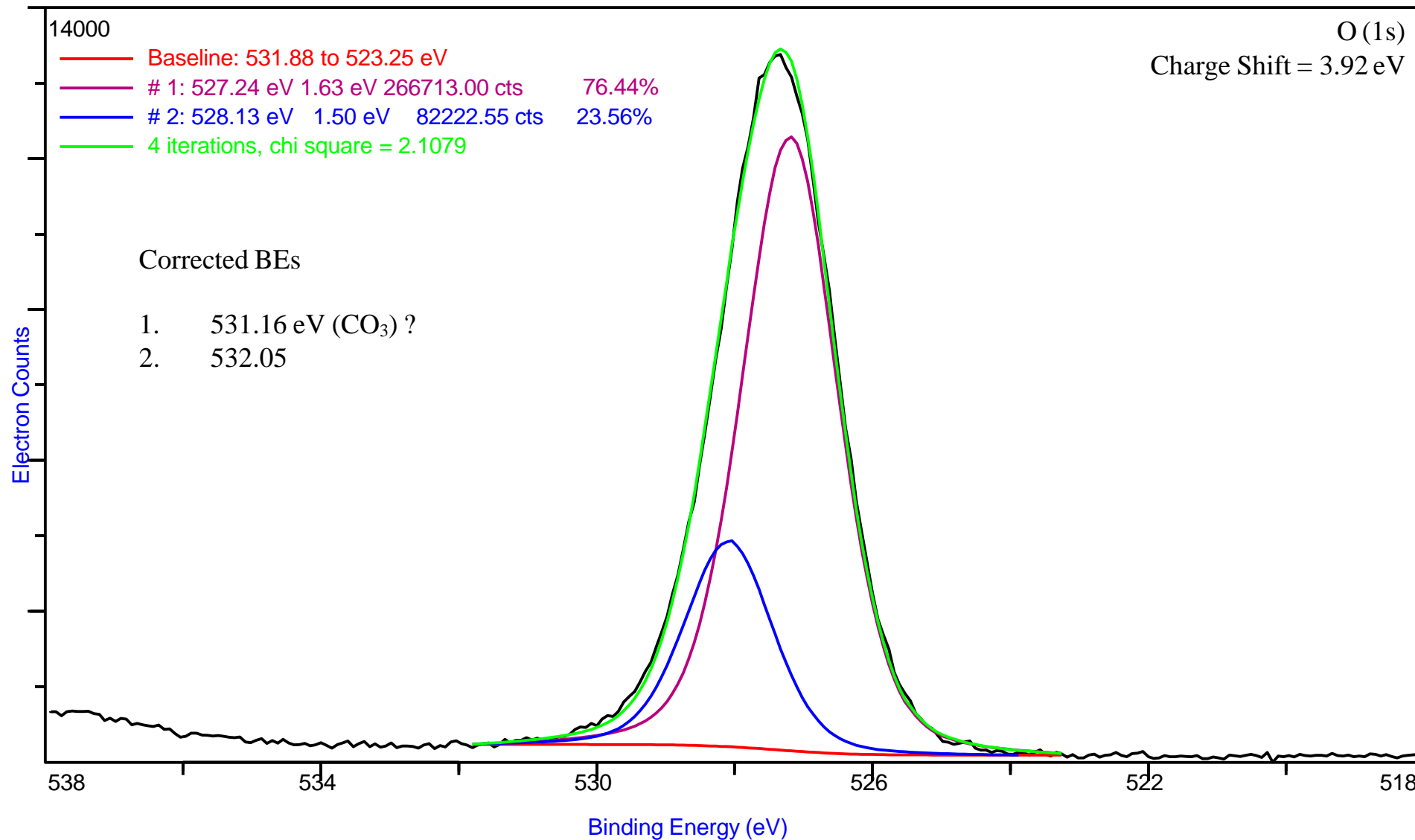
Signal	Corrected BE	Exper. BE	Sens Factor	Norm Area	Relative Area	Atom %
O Auger	974.3	973.8	0.00	22438	0	
BaAuger	898.2	897.7	0.00	48775	0	
BaAuger	886.5	886.0	0.00	18189	0	
Ba loss	817.1	816.6	0.10	18322	182905	
Ba loss	801.8	801.3	0.00	23120	0	
Ba3d3	791.8	791.3	9.29	154697	16650	
* Ba3d5	776.4	775.9	13.75	217657	15828	17.19
O loss	553.2	552.7	0.00	47393	0	
* O 1s	527.3	526.8	2.24	99098	44309	48.11
* C 1s	285.0	284.5	1.00	31967	31963	34.71
Ba4s	248.1	247.6	1.17	13225	11285	
Ba loss	201.1	200.6	6.08	9596	1578	
Ba loss	187.3	186.8	8.86	11455	1292	
Ba (4p)	173.4	172.9	0.23	30989	134568	
Ba loss	111.9	111.4	0.23	22578	98009	
Ba loss	97.5	97.0	0.00	3773	0	
Ba4d	84.7	84.2	7.05	125295	17764	
O 2s	24.3	23.8	0.18	8226	46424	
Ba5p	9.5	9.0	0.77	12728	16503	









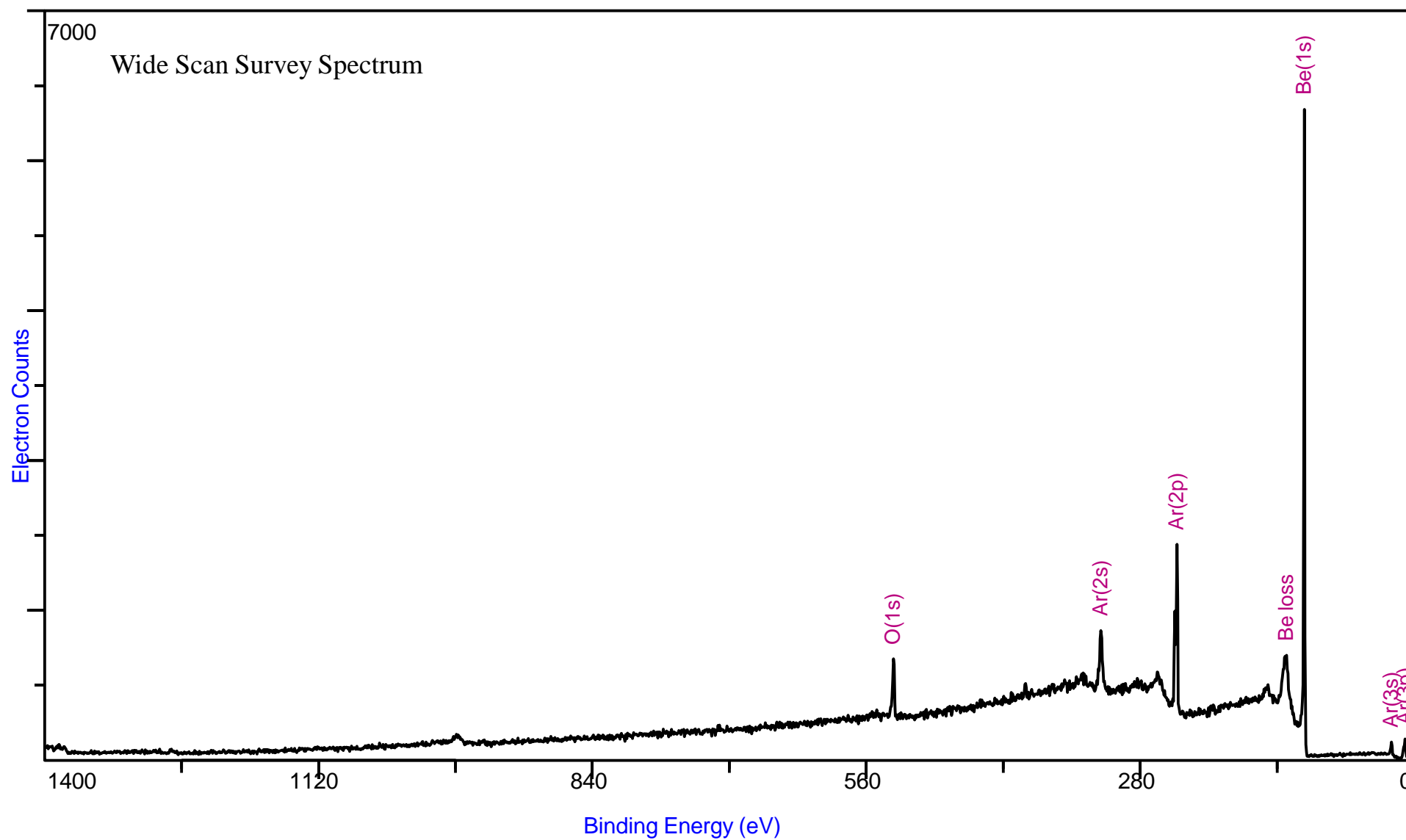


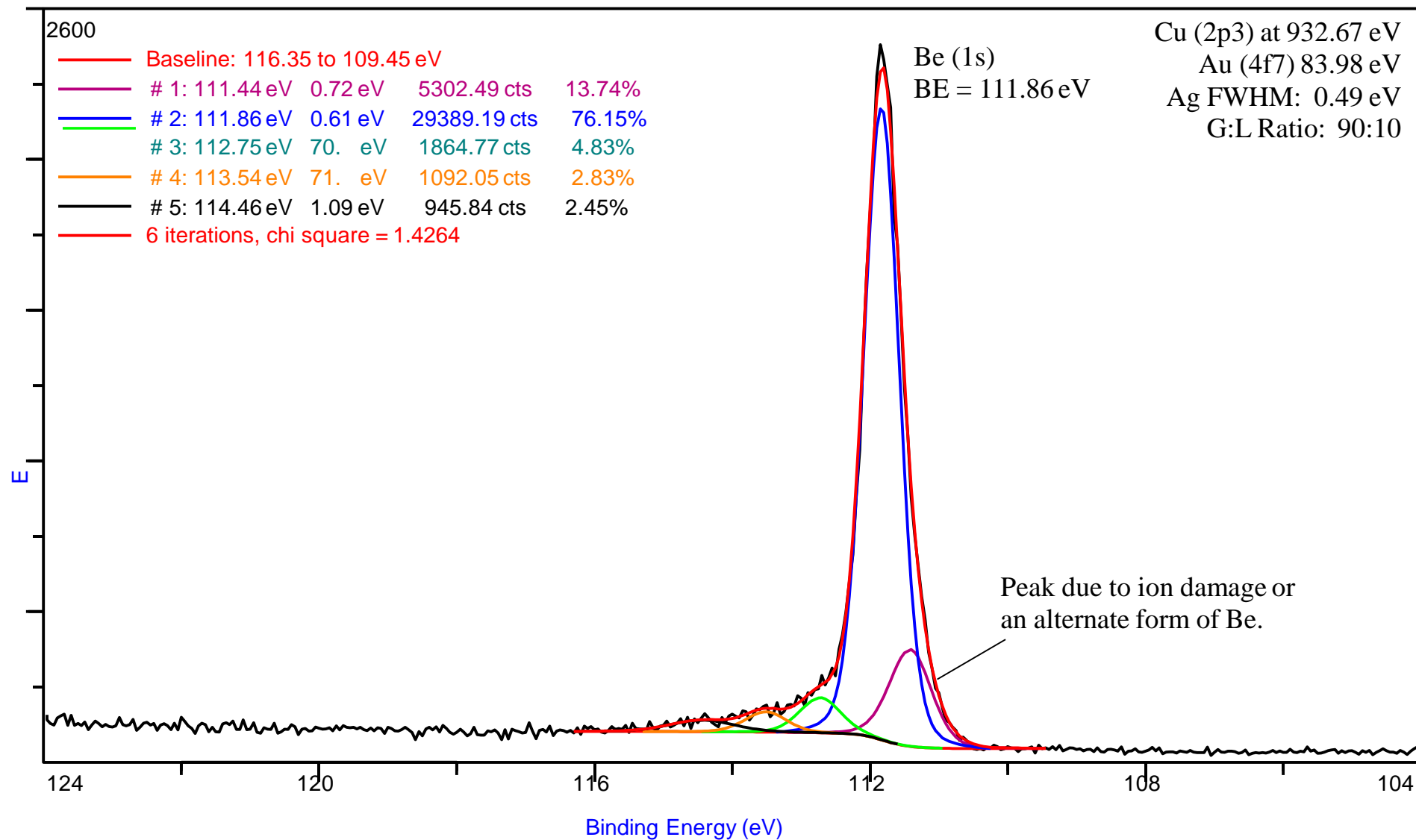
Detailed Surface Composition Table

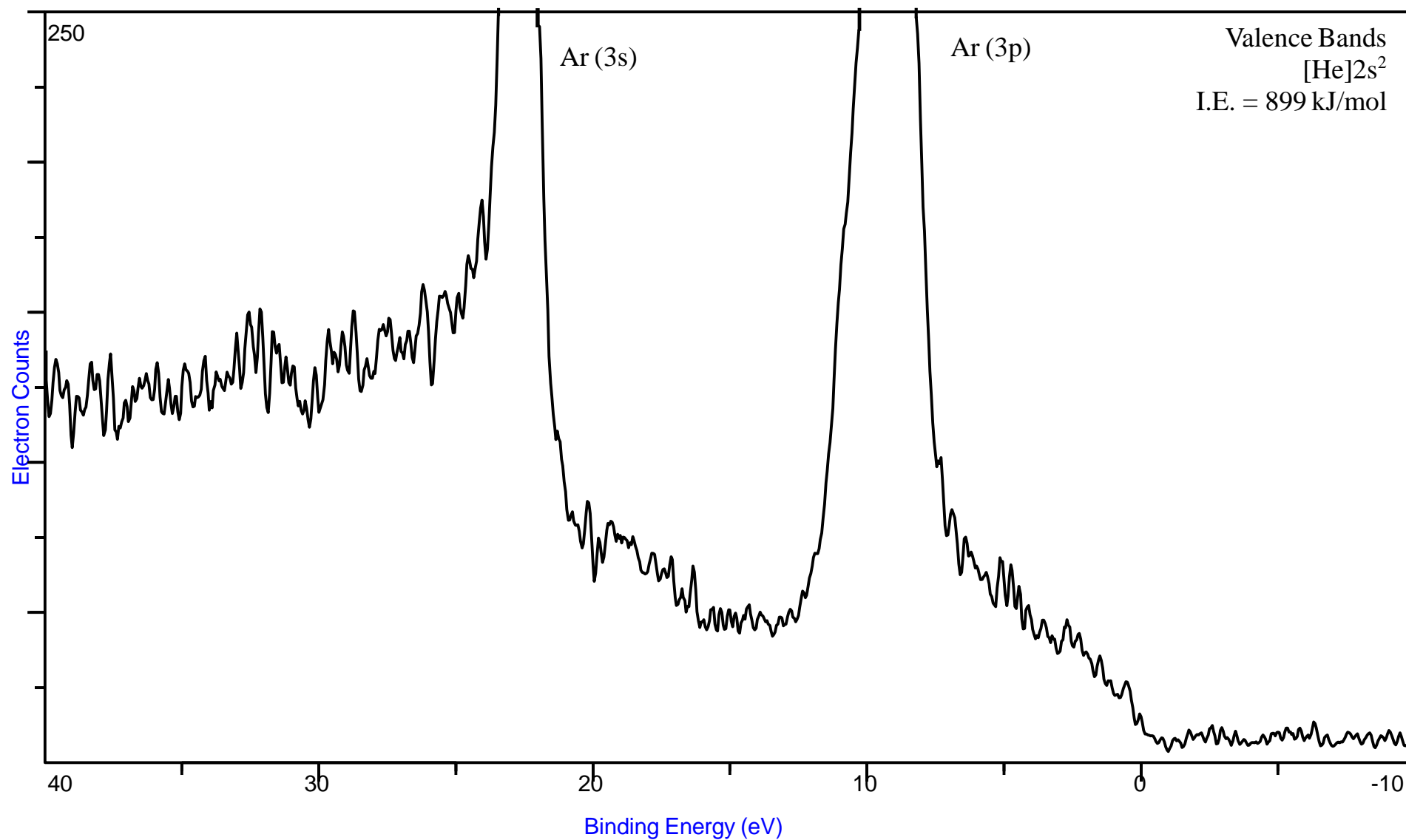
Description: Beryllium (Be)

Date: Mon Mar 7 1994

<u>Signal</u>	<u>Corrected</u> <u>BE</u>	<u>Exper.</u> <u>BE</u>	<u>Sens</u> <u>Factor</u>	<u>Norm</u> <u>Area</u>	<u>Relative</u> <u>Area</u>
O 1s	531.6	531.6	2.80	1375	491
Ar2s	319.5	319.5	1.96	2222	1135
Ar2p	241.7	241.7	3.06	4162	1360
Be loss	129.9	129.9	0.00	3989	0
Be1s	111.5	111.5	0.20	8003	39951
Ar3s	22.3	22.3	0.24	303	1283
Ar3p	8.5	8.5	0.25	460	1824





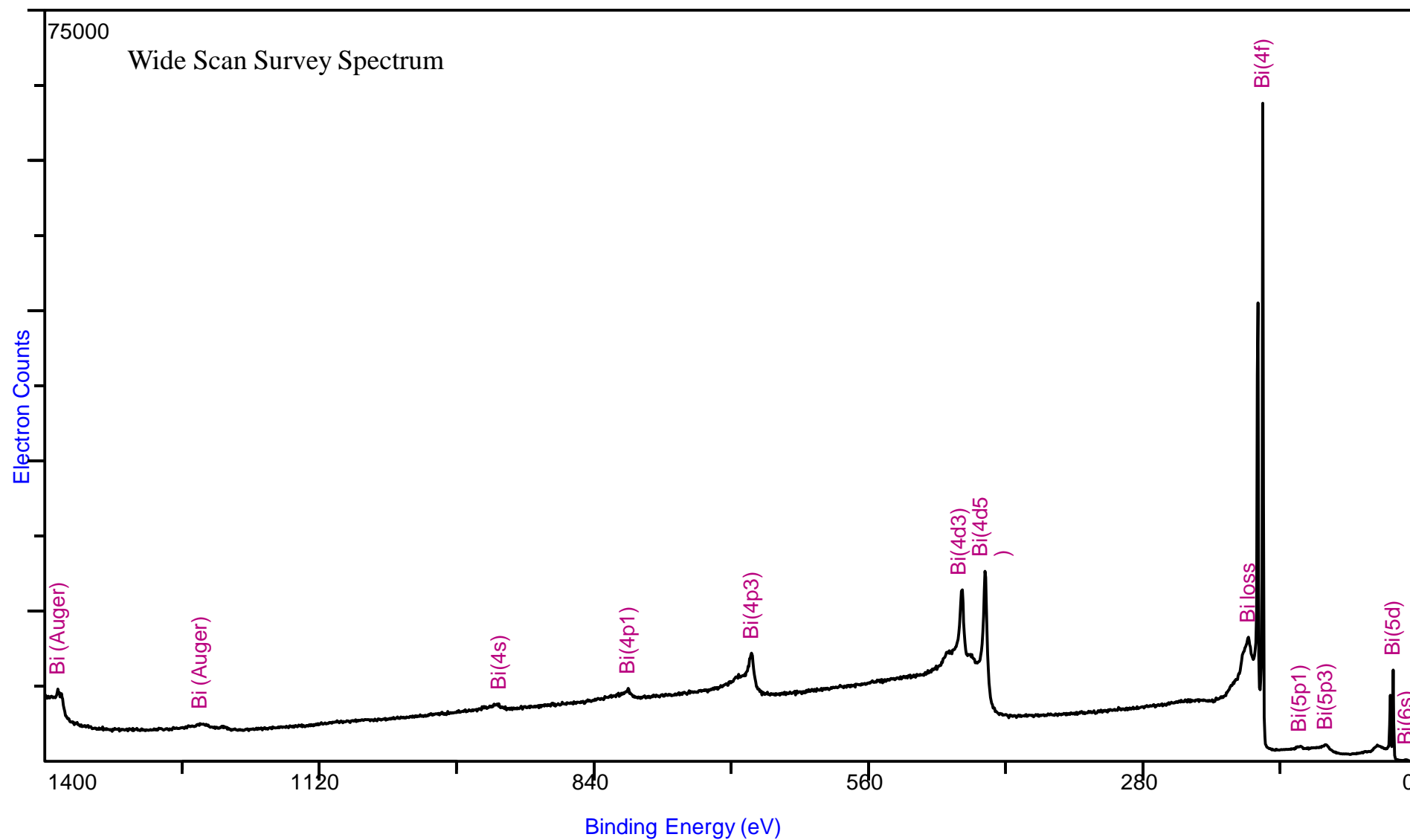


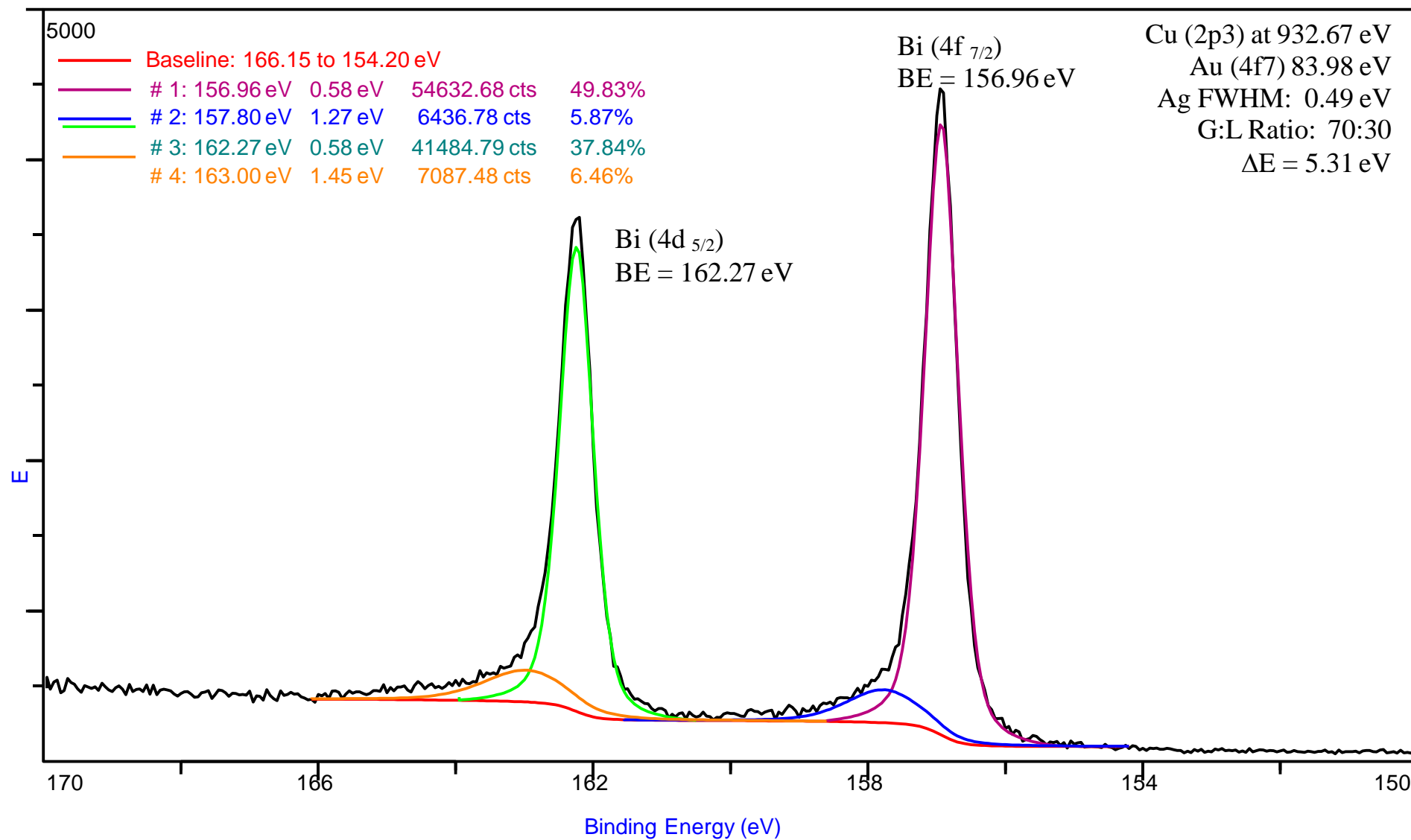
Detailed Surface Composition Table

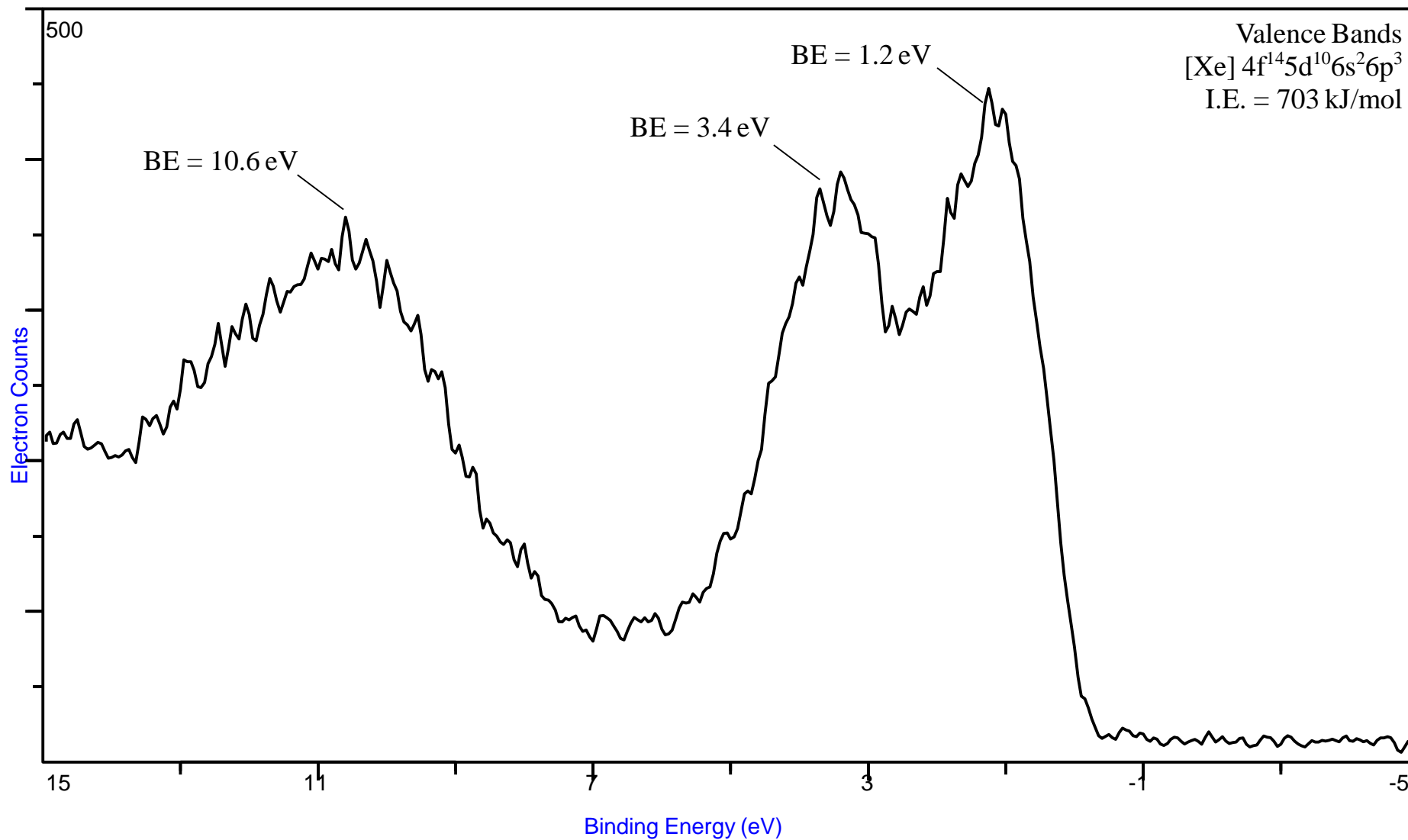
Description: Bismuth (Bi)

Date: Mon Mar 7 1994

<u>Signal</u>	<u>Corrected</u> <u>BE</u>	<u>Exper.</u> <u>BE</u>	<u>Sens</u> <u>Factor</u>	<u>Norm</u> <u>Area</u>	<u>Relative</u> <u>Area</u>
Bi4s	936.6	936.6	1.68	3856	2300
Bi4p1	805.0	805.0	1.87	3434	1832
Bi4p3	678.7	678.7	5.99	10932	1827
Bi4d3	463.9	463.9	8.85	15819	1788
Bi4d5	440.3	440.3	13.07	28588	2187
Bi loss	171.8	171.8	0.00	11212	0
Bi4f	156.8	156.8	25.34	67957	2682
Bi5p1	118.2	118.2	0.56	706	1260
Bi5p3	92.8	92.8	1.45	1655	1140
Bi5d	23.8	23.8	3.12	9837	3153
Bi6s	10.5	10.5	0.09	174	1988







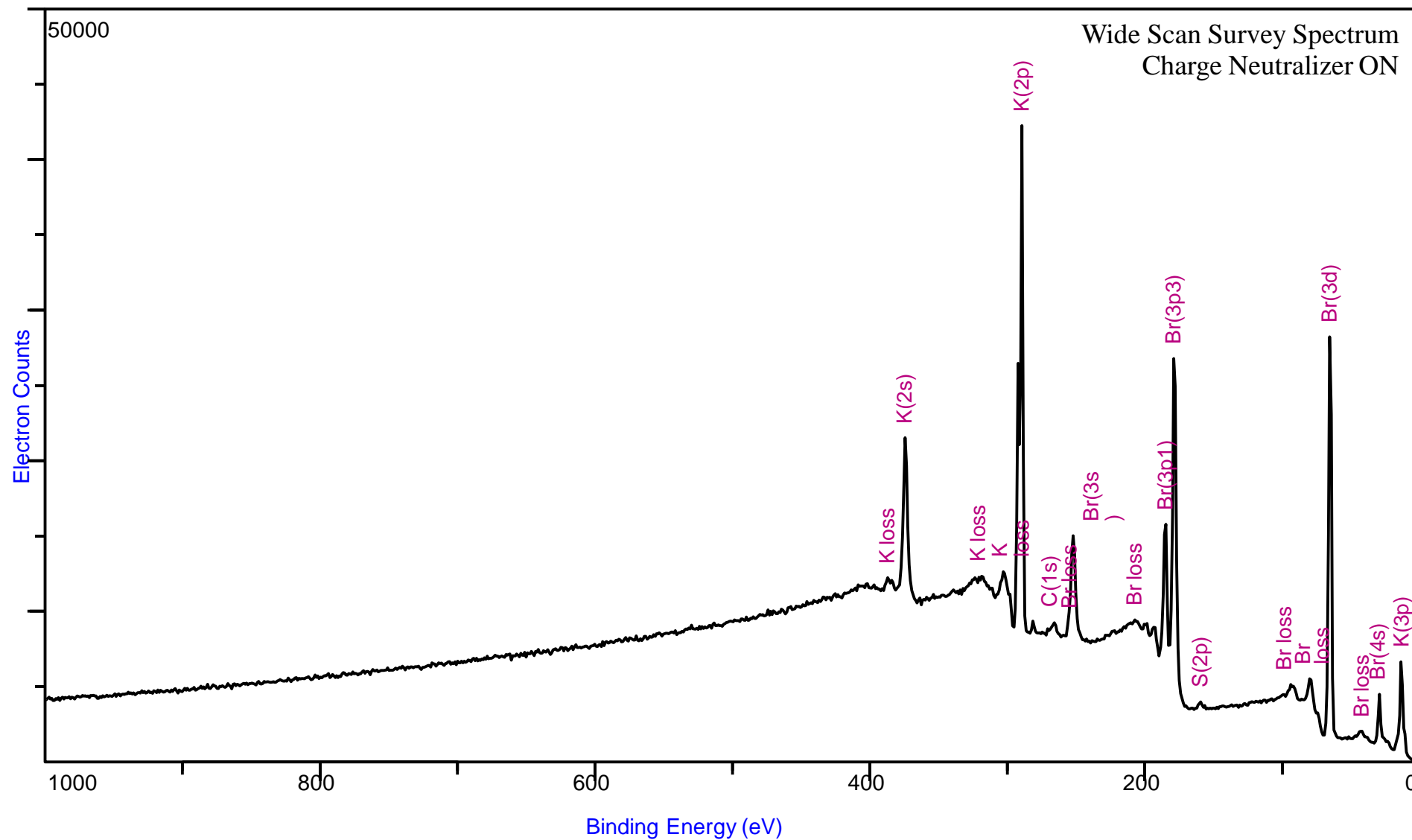
Detailed Surface Composition Table

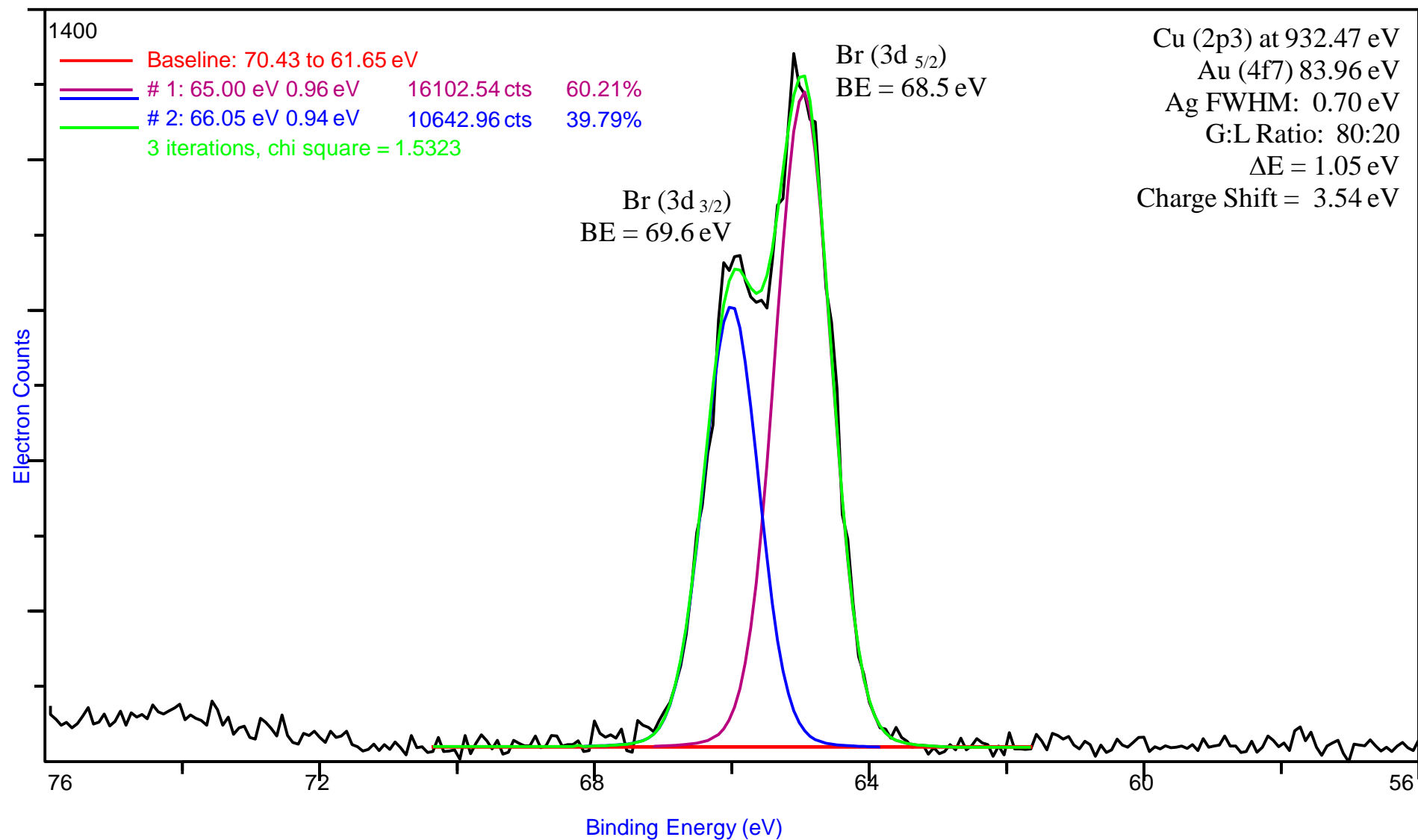
Description: POTASSIUM BROMIDE (KBr) CRYSTAL (17 HR IN VACUUM)

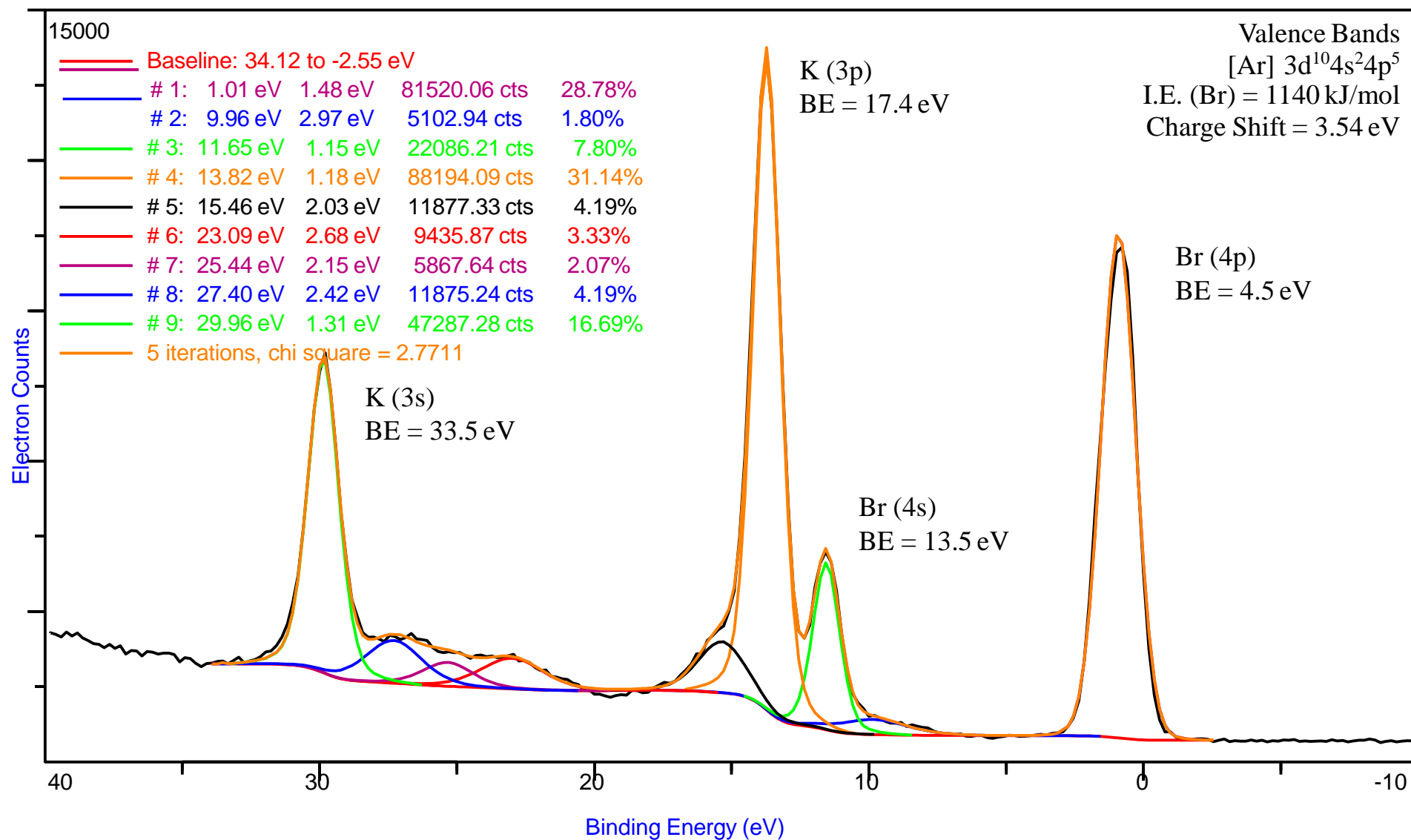
[\(Ref 6\)](#)

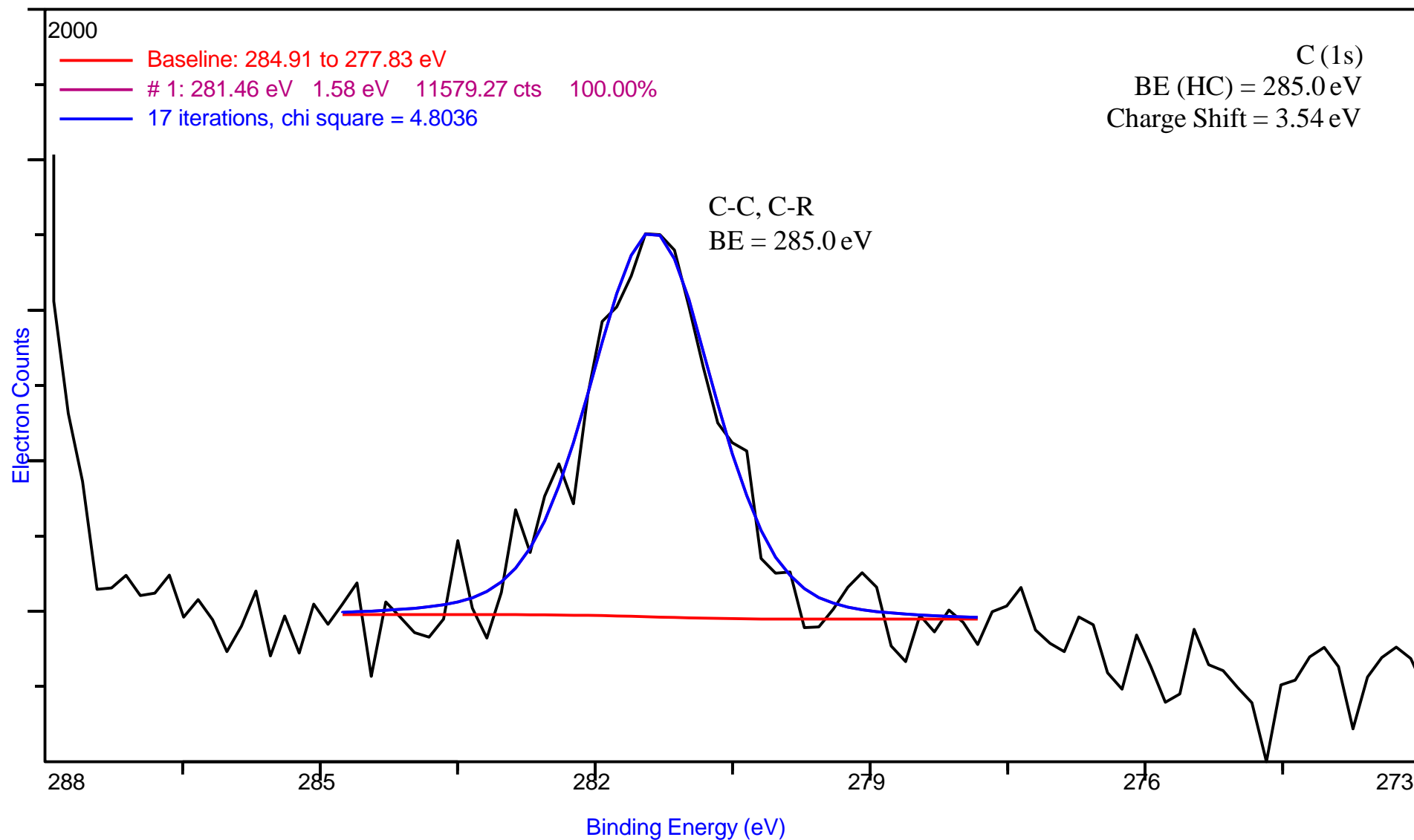
Date: Mon Dec 15 1986

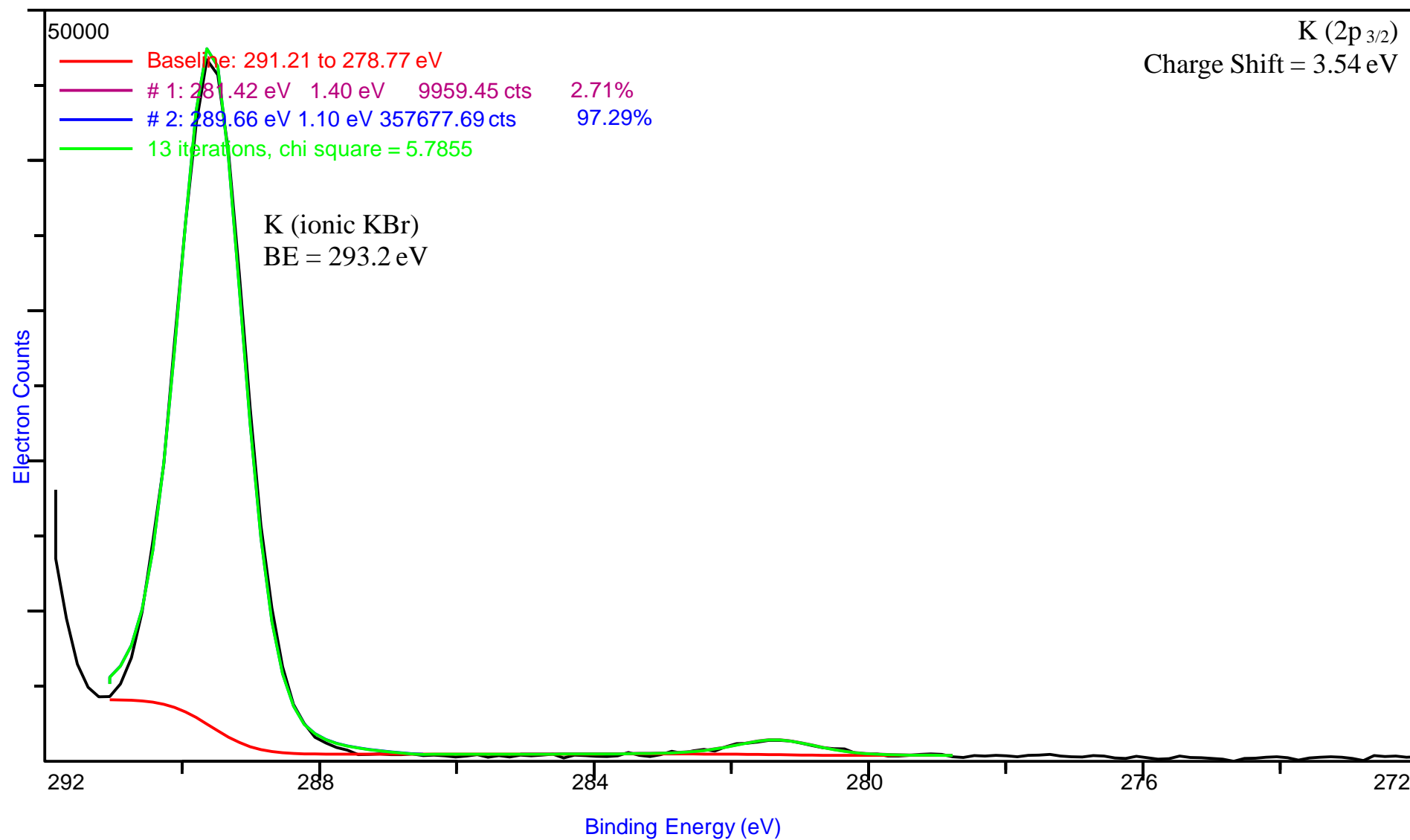
<u>Signal</u>	<u>Corrected</u> <u>BE</u>	<u>Exper.</u> <u>BE</u>	<u>Sens</u> <u>Factor</u>	<u>Norm</u> <u>Area</u>	<u>Relative</u> <u>Area</u>	<u>Atom</u> %
K loss	389.8	386.3	0.00	10051	0	
* K 2s	377.2	373.7	2.07	100049	48382	48.34
K loss	321.2	317.7	0.00	40521	0	
K loss	305.5	302.0	0.00	39599	0	
K 2p	292.2	288.7	3.95	242072	61227	
Br loss	268.7	265.2	0.00	9204	0	
Br3s	255.0	251.5	1.58	72740	46016	
Br loss	209.9	206.4	0.00	17984	0	
Br3p1	187.8	184.3	1.89	35873	18945	
Br3p3	181.2	177.7	3.67	140025	38194	
S 2p	162.2	158.7	1.89	4014	2124	
Br loss	96.3	92.8	0.00	16072	0	
Br loss	82.4	78.9	0.00	39435	0	
* Br3d	67.9	64.4	3.48	169762	48779	48.74
Br loss	45.0	41.5	0.00	12360	0	
Br4s	32.0	28.5	0.23	24934	106317	
K 3p	16.0	12.5	0.46	45428	98510	
* C 1s	285.0	281.5	1.00	2936	2927	2.92









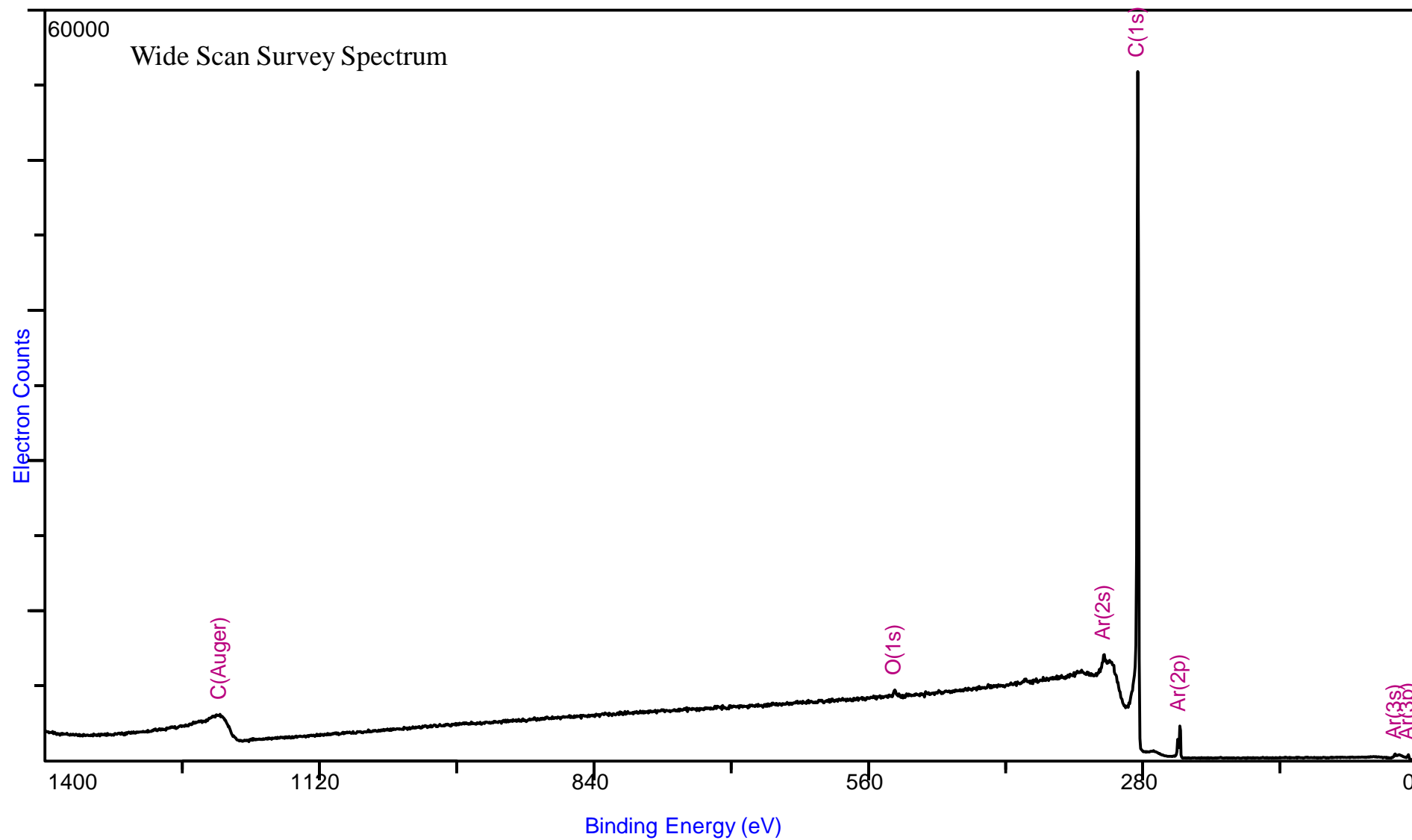


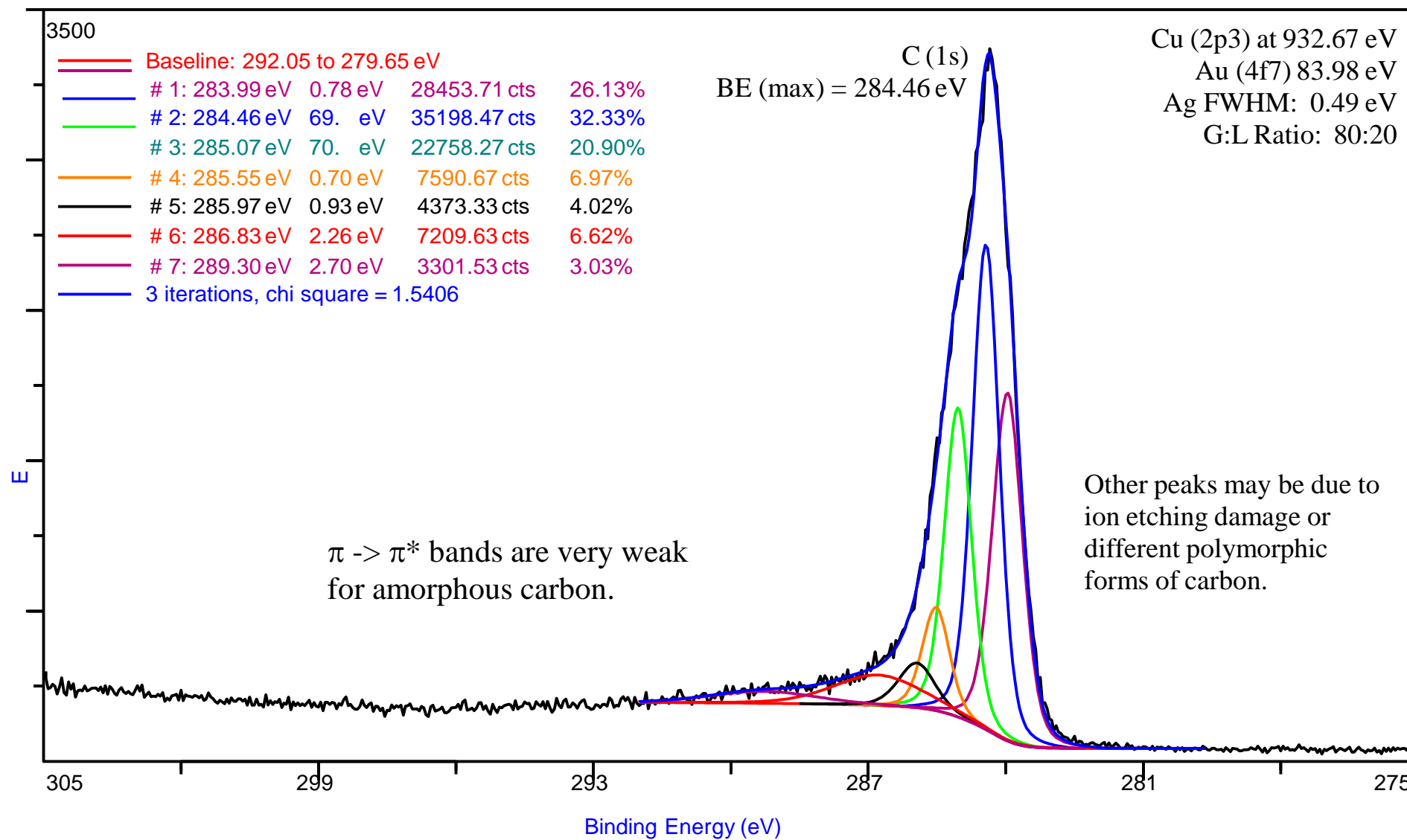
Detailed Surface Composition Table

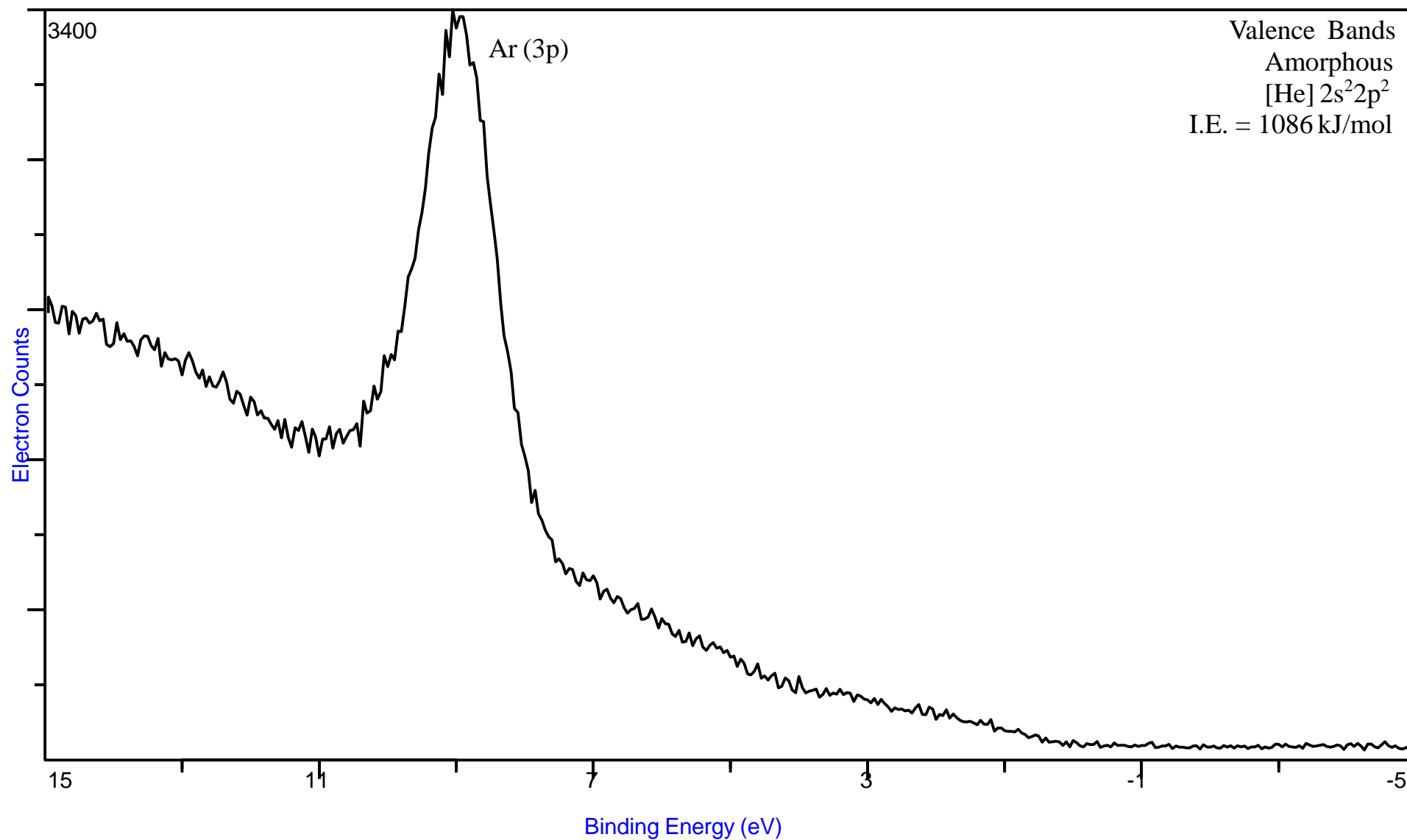
Description: Carbon (C) [amorphous]

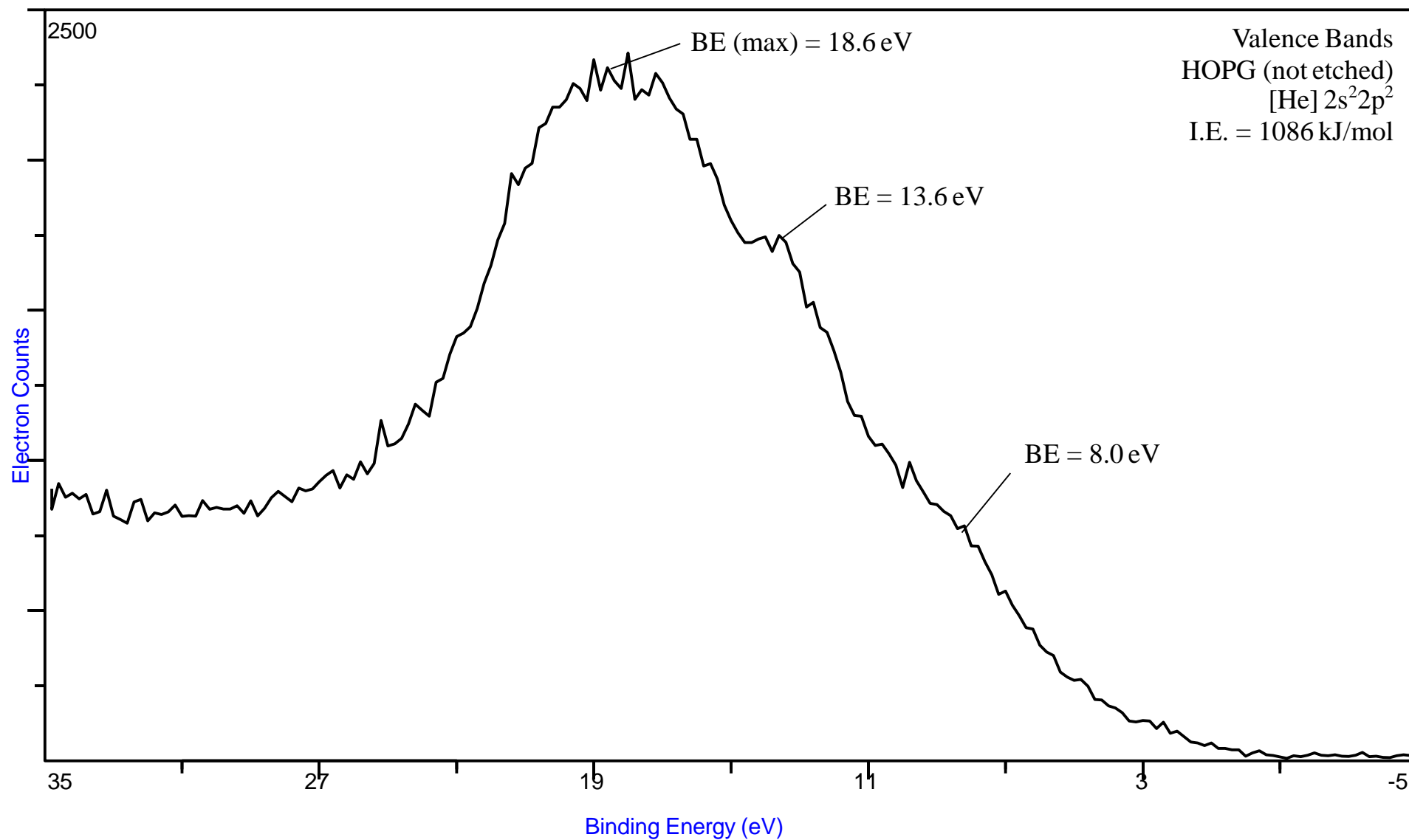
Date: Sun Mar 13 1994

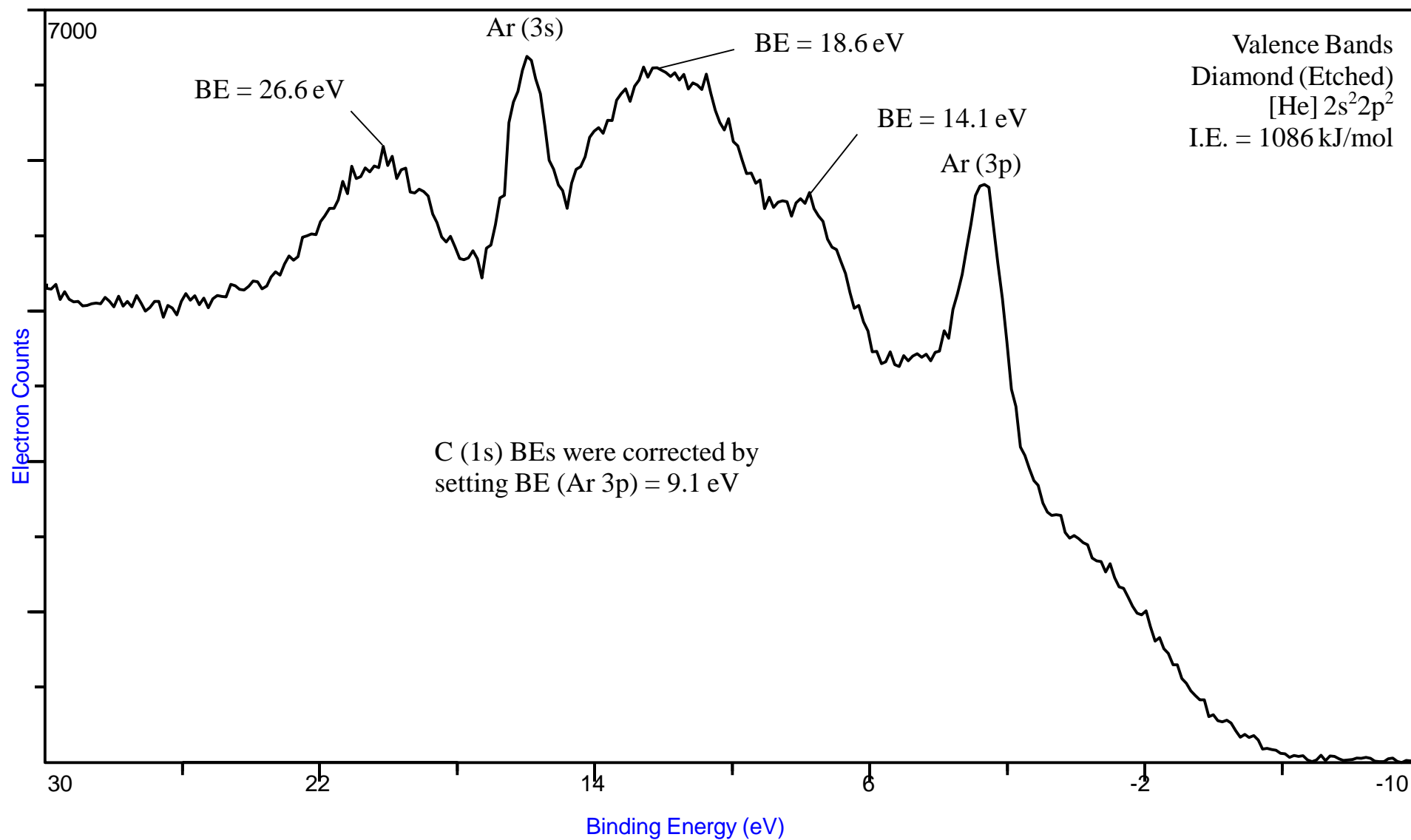
<u>Signal</u>	<u>Corrected</u> <u>BE</u>	<u>Exper.</u> <u>BE</u>	<u>Sens</u> <u>Factor</u>	<u>Norm</u> <u>Area</u>	<u>Relative</u> <u>Area</u>
C Auger	1221.4	1221.4	0.00	11013	0
O 1s	532.6	532.6	2.80	422	151
Ar2s	319.1	319.1	1.96	1178	601
C 1s	284.4	284.4	1.00	32524	32523
Ar2p	241.5	241.5	3.06	1650	539
Ar3s	21.9	21.9	0.24	514	2177
Ar3p	8.5	8.5	0.25	101	400











BE Lookup Table for Signals from Elements and Common Chemical Species

1-82 eV

1.0 Bi 6p1	3.9 Pt 5d	10.0 P 3p	18.0 At 6s	24.0 Kr 4s	34.0 K 3s	44.0 Ra 6s	52.0 Tm 5s	65.7 V 3s
1.0 Ce 4f	4.0 Ir 5d	10.0 Ti 4s	18.0 Ce 5p	24.0 Sn 4d	35.0 Re 5p3	44.0 U 6s	52.3 Yb 5s	66.0 Ni 3p
1.0 Co 3d	4.0 Pm 4f	10.0 V 4s	18.0 Pr 5p	25.0 Th 6p1	35.2 Mo 4p	44.4 Y 4s	52.6 Fe 3p	66.0 Pt 5p1
1.0 Cr 3d	4.5 Ag 4d	10.0 Zr 5s	18.1 Hf Ntv Ox	26.0 Bi 5d3	35.2 W Na2WO4	1. Ta 5p1	53.0 Sn loss	67.8 Ta 5s
1.0 Fe 3d	4.8 Dy 5d	10.5 Bi 6s	18.2 C 2s	26.0 He 1s	35.3 Y loss	2. As 2O3	53.4 Os 4f5	68.0 Ra 5d
1.0 Ga 4p	5.0 B 2p	10.7 Cd 4d5	18.4 Sr 4p	26.0 Rn 6s	35.8 W O3	45.5 As Ntv Ox	54.0 Os 5p1	68.0 Tc 4s
1.0 Hf 5d	5.0 Br 4p	11.0 Kr 4p	18.7 Ga 3d5	26.1 Lu 5p	36.0 Ce 5s	45.7 Ge loss	54.2 Se CdSe	68.5 Br 3d5
1.0 In 5p	5.0 Ca 3d	11.0 Rn 6p	18.8 Ga 3d	26.8 Ta 2O5	36.0 Gd 5s	46.0 Re 5p1	54.5 Se GeSe	68.5 Br KBr
1.0 Na 3s	5.0 Er 4f	1. Sc 4s	18.9 Ga 3d3	26.8 Zr 4p	36.6 Sr 4s	46.3 Ga loss	54.9 Se 3d5	68.8 Cd 4p
1.0 Os 5d	5.0 Po 6p	2. Cs 5p3	19.0 Eu 5p	27.0 Br 4s	36.7 V 3p	46.8 Re 2O7	54.9 Li 1s	69.0 Br 3d
1.0 Pb 6p	5.3 Se 4p	11.6 Cd 4d3	19.0 Nd 5p	28.2 Sc 3p	37.0 W 5p3	46.8 W 5p1	54.9 Li OH	69.5 Br 3d3
1.0 Sn 5p	5.5 Cl 3p	12.0 Cs 5p	19.0 Pb 5d5	28.6 In loss	37.5 Hf 5p1	47.0 Mn 3p	54.9 Se 3d	70.0 Re loss
1.2 Yb 4f7	5.8 Au 5d	12.0 Po 6s	19.0 Ra 6p	28.8 Rb 4s	38.0 Pm 5s	47.0 Rh 4p	55.2 Se GeSe2	71.0 Pt 4f7
1.4 Pd 4d	6.0 Ta 5d	12.0 Te 5s	19.0 Sm 5p	29.0 Dy 5p1	38.0 Pr 5s	47.9 Ru 4p	55.3 Li CO3	71.8 Mg loss
1.4 Rh 4d	6.0 Y 4d	12.0 Tl 5d5	19.1 Ga Sb fract	29.0 Er 5p	38.3 Sn loss	48.0 Dy 5s	55.6 Nb 4s	72.6 Pt 4f
2.0 Cd 5p	6.2 Hg 5d	12.6 Cs 5p1	19.4 Ga AlAs etch	29.0 Lu 5p	39.0 Eu 5s	48.0 Rn 5d	55.7 Se 3d3	72.7 Al 2p3
2.0 Mg 3s	6.9 Eu 4f	13.0 Tl 5d	19.5 N 2s	29.1 Ge 3d5	39.0 Nd 5s	48.0 Sb loss	56.8 Au 5p3	72.9 Al 2p
2.0 Mo 4d	7.0 O 2p	13.2 Rb 4p	19.7 Ga P fract	29.2 F 2s	39.0 Tc 4p	48.5 I 4d	56.8 Lu 5s	73.1 Tl 5p3
2.0 Nb 4d	7.0 Sm 4f	13.2 Rb 4p	19.7 Ga As fract	29.4 Ge 3d	39.5 Tm 5p	49.5 Ho 5s	57.4 Er 5s	73.2 Al 2p1
2.0 Nd 4f	7.0 Sn 5s	14.0 Ne 2p	20.0 U 6p	29.5 Ho 5p1	40.0 At 5d	5. Mg CO3	58.0 Ag 4p	73.8 Al N
2.0 Ni 3d	1. Xe 5p	14.0 Sc 3d	20.2 Zn loss	29.7 Ge 3d3	40.0 Ba 5s	6. Mg (OH)2	58.0 Fr 5d	74.0 Au 5p1
2.0 Pr 4f	2. Lu 4f7	14.2 Hf 4f7	20.5 Gd 5p	30.2 Ge Se	40.0 In loss	6. Mg 2p3	58.0 Hg 5p3	74.2 Cr 3s
2.0 Sb 5p	7.1 Tb 4f	15.0 Fr 6p	20.7 Ga 2O3	30.3 Na 2p	40.0 Tb 5s	7. Mg O	58.1 W loss	74.3 Al 2O3
2.0 Sc 4p	7. Gd 4f	15.0 H 1s	21.0 Pb 5d3	30.9 Nb 4p	40.1 Te 4d	8. Mg 2p	58.2 Ti 3s	74.3 Al 2O3-nH2O
2.0 Tc 4d	8. Dy 4f	15.0 Hf 4f	21.6 Ta 4f7	30.9 Pb loss	40.2 Re 4f7	9. Mg 2p1	58.3 Te loss	74.4 Pt 4f5
2.0 Ti 3d	8.0 At 6p	15.0 Rb 4p1	21.8 Tb 5p	31.0 Hf 5p3	41.0 Ne 2s	50.0 Mg CO3	58.6 Ag 4p	74.4 Al (OH)3
2.0 V 3d	8.0 S 3p	15.0 Tl 5d3	22.0 Dy 5p3	31.0 Po 5d	41.0 Sm 5s	50.0 Sr loss	58.9 Y loss	74.9 Cu 3p
2.0 Yb 4f	8.3 Ho 4f	15.7 Cl 3s	22.0 Pm 5p	31.3 W 4f7	41.2 Re 4f	3. Zr 4s	59.0 Co 3p	74.9 Se loss
2.0 Zr 4d	3. Lu 5d	15.9 Hf 4f5	22.3 Ar 3s	31.5 Ge Se2	41.4 Re Ntv Ox	4. Mg NtvOx1	59.2 As loss	75.0 Cs 4d5
5. Yb 4f5	4. Lu 2O3	15.9 I 5s	22.7 Ta 4f	31.7 Sb 4d	41.5 As 3d5	50.7 Os 4f7	60.8 Ir 4f7	75.1 Pt O2-nH2O
6. Te 5p	5. Tm 4f7	16.0 K 3p	23.0 Cs 5s	32.1 Ga loss	41.8 As 3d	50.7 Pd 4p	61.0 Mg loss	75.1 W 5s
2.8 Cu 3d	6. Lu 4f5	16.0 P 3s	23.1 O 2s	32.3 W 4f	42.0 As S	50.7 Sc 3s	62.0 Ir 4f	75.5 Al Ntv Ox
2.8 Mn 3d	8.9 Ar 3p	16.0 S 3s	23.3 Ho 5p3	32.4 Ti 3p	42.0 Th 6s	50.9 Mg reoxid	62.0 Ir O2	76.0 Cs 4d
2.8 Re 5d	9.0 F 2p	16.9 In 4d	23.3 Y 4p	32.6 Ta 5p3	42.1 Ca 3s	51.0 Ir 5p3	62.0 Ir 5p1	77.8 Ni loss
2.8 Si 3p	9.0 Ru 4d	17.0 La 5p	23.4 Ta S2	33.0 La 5s	42.1 Cr 3p	51.0 Mg NtvOx2	62.0 Mo 4s	78.3 In 4p
2.8 W 5d	9.0 Sb 5s	17.0 Th 6p3	23.5 Ca 3p	33.2 Ge O2	42.2 As 3d3	4. Os 4f	62.0 Xe 4d	79.0 Cs 4d3
3.0 Ge 4p	1. Si 3s	1. Xe 5s	23.5 Yb 5p	33.4 Lu 5p	42.7 Re 4f5	5. Pt 5p3	62.3 Hf 5s	80.0 Ru 4s
3.0 I 5p	2. As 4p	2. Hf O2	23.8 Bi 5d	33.5 W 4f5	42.7 Ta loss	51.5 Mg reoxid	62.7 Ir Ntv Ox	80.7 Rh 4s
3.0 Pb 6s	9.7 Zn 3d	17.7 Pb 5d	24.0 Ta 4f5	33.8 Ge Ntv Ox	43.0 As 2S3	51.7 Re loss	63.3 Na 2s	81.0 Hg 5p1
3.2 Bi 6p3	10.0 Ba 5p	17.9 Ga InAs (ar)	24.0 Bi 5d5	34.0 Fr 6s	44.0 Os 5p3	51.9 Mg NtvOx3	63.8 Ir 4f5	81.8 Re 5s

BE Lookup Table for Signals from Elements and Common Chemical Species

82-275 eV

82.0 Br	loss	8. Si	Almand.	119.4 Ga	loss	137.8 Pb	2O3	158.9 Y	2(CO3)3	1. Ge	3s	204.1 Nb	NbO	235.3 Mg	Auger
82.0 Mn	3s	9. Hg	4f	119.4 Tl	CO3	137.8 Se	Auger	159.2 Bi	Ntv Ox	2. Zr	3d3	205.0 Nb	3d3	237.0 Pm	4p3
82.7 Pb	5p3	102.0 Pt	5s	120.0 Hg	5s	138.3 Pb	4f	159.6 Ho	4d5	3. Br	3p3	205.1 S	loss	237.6 Ta	4d3
84.0 Au	4f7	102.0 Si	3N4	120.0 Tl	4f	138.5 Ge	loss	160.0 Bi	5s	182.0 Br	3p	205.8 Lu	4d3	237.9 Rb	3p3
84.0 Ba	4d3	102.6 Si	O	1. Pm	4d	138.8 Pb	Ntv Ox	161.2 S	PbS	1. Fr	5p1	206.1 Nb	NbO2	238.0 Cs	4s
84.7 Ba	4d	102.9 Zn	loss	2. I	4p	139.0 Pb	CO3	161.3 Ho	2O3	2. Yb	4d5	207.0 Ce	4p3	238.0 Rn	4f
85.0 Au	4f	103.0 Ga	3p	3. Ge	3p3	139.0 Xe	4p	161.5 S	CuS, TaS2	182.4 Zr	O2	207.0 Xe	4s	238.9 Mo	loss
85.0 Th	5d5	103.0 Ga	3p3	4. Tl	4f5	139.5 Zn	3s	161.7 Se	3p3	182.8 Er	Auger	207.3 P	loss	241.8 Ar	2p3
86.0 Ba	4d5	103.0 Pt	loss	122.4 Cu	3s	140.0 Fr	5p3	161.9 S	HgS	183.7 Si	loss	207.4 Nb	Nb2O5	242.0 Ar	2p
86.9 Kr	3d5	103.0 Si	O2	122.4 In	4s	140.3 Gd	4d5	162.2 S	MoS2	184.0 Po	4f	207.4 Nb	Ntv Ox	243.1 W	4d5
87.2 Kr	3d	103.0 U	5d3	127.0 Rn	5p3	140.7 As	3p3	162.3 Bi	4f5	184.9 Yb	2O3	208.0 Kr	3p3	243.9 Ar	2p1
87.7 Au	4f5	103.5 Si	O2-nH2O	2. Eu	4d5	141.2 Gd	2O3	162.4 S	Na2S2O3	185.3 S	loss	210.0 At	4f	245.0 Nd	4p1
1. Al	loss	103.7 Al	loss	3. Tl	loss	141.7 Pb	4f5	162.6 S	FeS2	185.5 I	4s	210.8 Hf	4d5	248.0 Ba	4s
2. Au	2O3	103.9 Hg	4f5	128.6 P	InP etch	142.0 As	3p	163.9 S	2p3	8. Br	3p1	210.9 Dy	Auger	248.0 Rb	3p1
3. Kr	3d3	104.0 La	4d	129.0 Ge	3p1	145.9 Tb	4d5	164.0 Rn	5p1	9. B	CrB	213.0 B	loss	249.6 S	loss
2. Pd	4s	104.0 Po	5p3	129.0 P	InP etch	146.0 Sr	loss	164.0 S	2p	188.0 B	1s	213.0 La	4p1	250.0 Sm	4p3
3. Zn	3p	106.3 Pb	5p1	129.0 Sm	4d	147.0 As	3p1	164.0 Sr	loss	1. B	MoB, LaB6	214.0 Rn	5s	253.0 Mo	loss
1. Os	5s	107.0 Ga	3p1	129.3 P	GaP etch	148.0 At	5p1	165.1 S	2p1	2. B	WB	217.5 Cl	loss	253.0 Tc	3d
2. Mg	2s	108.0 Au	5s	130.0 Be	loss	148.0 Pb	5s	166.6 S	Na2SO3	3. B	Ni3B	218.0 Pr	4p3	253.0 Tc	3d5
90.6 Sn	4p	109.7 Rb	3d5	1. Ho	Auger	148.5 Tb	F3	167.3 Er	4d5	188.9 B	Ntv Ox	220.5 Se	Auger	254.0 Ra	5s
91.0 Fe	3s	109.7 Rb	OAc	2. P	2p3	148.8 Al	loss	167.3 Se	3p1	189.0 P	2s	221.3 Hf	4d3	255.0 Br	3s
92.8 Bi	5p3	109.9 Cd	4s	130.6 P	2p	149.8 Pb	loss	167.6 Si	loss	189.2 Tm	Auger	223.0 Ce	4p1	255.0 Eu	4p3
93.0 Th	5d3	110.0 Ce	4d	131.4 P	2p1	149.9 P	loss	168.5 Er	2O3	8. B	N	225.7 As	3s	255.0 Pm	4p1
94.0 U	5d5	110.0 Rb	3d	132.0 Po	5p1	149.9 Tb	3O7	168.5 S	Na2SO4	9. Yb	4d3	226.1 Ta	4d5	255.1 Se	Auger
94.6 Tl	5p1	5. Ni	3s	132.7 Ga	loss	150.5 Si	2s	168.5 S	Na2S2O3	194.0 B	2O3	228.0 Mo	3d5	255.6 W	4d3
95.2 Ir	5s	6. Mg	loss	133.4 Al	loss	152.0 Zn	loss	168.6 P	loss	195.0 At	5s	228.0 Nd	4p3	257.0 Tc	3d3
96.0 Br	loss	111.2 Rb	3d3	6. Si	loss	152.3 Dy	4d5	168.8 Y	loss	195.0 U	5p3	229.0 S	2s	260.0 Re	4d5
97.0 Ag	4s	111.8 Be	1s	7. Sr	3d5	152.9 Sb	4s	169.1 Te	4s	1. Lu	4d5	229.4 Mo	O2 (?)	260.0 U	5p1
98.7 Er	Auger	112.6 Te	4p	133.7 Sr	CO3	153.0 Ra	5p3	169.3 Er	4d3	2. Zr	loss	229.5 Mo	3d	261.0 As	Auger
99.8 Si	2p3	113.6 Be	O	134.0 Sr	3d	155.8 Y	3d5	173.0 Ba	4p	197.0 La	4p3	229.7 Mo	S2	261.5 Tb	Auger
8. Mg	loss	114.7 Be	Ntv Ox	134.9 Sm	2O3	156.1 Dy	2O3	173.3 Ga	loss	197.5 Ge	Auger	229.9 Se	3s	264.3 Rb	loss
9. Hg	4f7	115.0 At	5p3	5. Sr	3d3	156.6 Y	2O3	175.4 Tm	4d	198.4 Se	Auger	230.0 As	Auger	267.5 S	loss
1. Si	2p	115.0 Pr	4d	6. Eu	2O3	157.0 Bi	4f7	175.9 Tb	loss	198.7 Cl	2p	231.1 Mo	3d3	267.7 W	loss
2. Si	O	115.5 Se	Auger	136.8 Pb	O2	157.0 Bi	4f	176.3 Tm	2O3	198.9 Cl	2p3	232.6 Mo	Ntv Ox	268.0 Fr	4f
100.4 Si	2p1	116.2 Si	loss	8. Rb	loss	157.0 Bi	loss	177.0 Po	5s	198.9 Cl	MCl	232.9 Tb	Auger	268.4 Sr	3p3
100.4 Si	C	117.7 Tl	4f7	9. Pb	4f7	157.0 Y	3d	177.0 Th	5p3	199.8 Cl	C-Cl	233.0 Kr	3p1	270.0 Cl	2s
6. Sb	4p	117.9 Al	2s	1. Tl	5s	157.9 Y	3d3	178.7 Se	Auger	200.0 Ra	5p1	233.1 Mo	O3	271.3 Gd	4p3
7. Hg	O	118.0 Nd	4d	2. Sn	4s	158.5 Cs	4p3	178.7 Zr	3d5	200.5 Cl	2p1	234.0 Fr	5s	273.5 Re	4d3
100.9 Co	3s	118.2 Bi	5p1	5. Pb	O	158.8 Bi	2O3	179.9 Zr	3d	201.4 Nb	3d	234.0 Pr	4p1	274.5 Er	Auger
100.9 Hg	S	118.2 Tl	2O3	6. Pb	3O4	158.9 Ga	3s	180.9 Cs	4p1	202.3 Nb	3d5	234.0 Th	5p1	275.0 La	4s

BE Lookup Table for Signals from Elements and Common Chemical Species

278-609 eV

278.7	Sr	3p1	301.6	Mg	Auger	340.3	Pd	3d3	382.0	U	4f	412.7	Lu	4p1	460.2	Gd	Auger	515.0	Eu	Auger	560.0	Pd	3p1
279.0	Os	4d5	305.0	Pr	4s	341.4	Ge	Auger	384.9	Tl	4d5	420.4	Ta	loss	462.5	Ta	4p1	515.6	V	2p	560.9	Ti	2s
280.1	Ru	3d5	305.5	K	loss	342.0	Th	4f5	386.0	Tm	4p1	421.6	Mo	loss	463.1	In	loss	515.9	V	2O3	562.8	Ta	4s
281.0	Ru	Ntv Ox	307.2	Rh	3d5	343.0	Ho	4p1	388.0	U	4f5	423.3	W	4p3	464.0	Bi	4d3	517.1	V	2O5	565.0	Na	Auger
281.1	Ru	O2	308.5	Rh	Ntv Ox	343.0	Zr	3p1	388.3	Se	Auger	424.5	N	loss	466.1	Ru	3p3	517.3	V	O2	567.0	Rn	4d3
282.2	Ru	3d	308.9	Rh	2O3	346.5	Pd	loss	389.8	K	loss	425.0	As	Auger	466.8	Nb	3s	518.5	Re	4p1	568.1	Cu	Auger
282.6	C	VC	308.9	Sr	loss	346.6	Ca	2p	390.3	Yb	4p1	425.0	Tc	3p3	468.0	As	Auger	519.0	As	Auger	570.9	Ga	Auger
282.9	C	NbC	309.4	Rh	3d	347.1	Ca	O	391.7	Ga	Auger	425.5	Pb	loss	468.5	Tm	4s	519.6	Pt	4p3	572.5	Te	CdTe
283.0	C	TaC	310.4	Ge	Auger	347.2	Mg	Auger	391.7	Mg	Auger	429.6	Zr	3s	471.0	Os	4p3	519.7	V	2p1	572.9	Te	3d5
283.0	Sm	4p1	311.0	Tb	4p1	347.8	Ca	UHV Ox	393.8	Mo	3p3	433.0	Ge	Auger	471.5	Zn	Auger	521.3	Rh	3p1	573.0	Zn	Auger
284.0	Tb	Auger	311.1	Y	3p1	349.0	Sm	4s	393.8	Y	3s	434.3	Pb	4d3	473.0	Po	4d5	524.0	Na	Auger	573.6	Ag	3p3
284.2	Ru	3d3	311.9	Ir	4d3	353.0	Au	4d3	395.6	Tb	4s	436.0	Ho	4s	474.0	Se	Auger	524.8	Ge	Auger	574.1	Cr	B
284.5	C	HOPG	311.9	Rh	3d3	357.2	Sr	3s	397.0	N	CrN	437.3	Hf	4p1	474.7	In	loss	528.2	Sb	3d5	574.3	Cr	2p3
284.5	Se	Auger	312.5	Mg	Auger	357.9	Ge	Auger	397.1	N	AlN	437.8	Ca	2s	480.8	Yb	4s	529.4	O	Ag2O, NiO	575.0	Cr	2p
285.0	C	1s	313.0	C	loss	357.9	Mg	Auger	397.3	N	TiN	440.0	Bi	4d5	484.9	Sn	3d5	529.6	Sb	2O3	575.5	Cr	Ntv Ox
285.4	C	C-OR	314.5	Pt	4d5	358.3	Hg	4d5	397.6	N	Si3N4	443.6	Ge	Auger	486.3	Sn	O	529.8	O	MgO	575.6	Cr	2O3
286.0	Cl	loss	315.1	Se	Auger	358.6	Se	Auger	398.4	N	1s	443.8	In	3d5	486.4	Ga	Auger	530.5	O	NaOH	576.5	Te	O2
286.0	Tb	4p3	315.2	Ho	4p3	359.0	As	Auger	398.4	N	BN	444.3	In	2O3	487.3	Sn	O2	531.1	O	Al2O3	576.6	Cr	Ntv Ox
287.0	C	C-Cl	319.5	Ar	2s	359.2	Lu	4p3	398.4	Sc	2p3	444.4	In	Ntv Ox	488.4	Ru	3p1	531.1	Sb	2O5	577.0	Fr	4d5
287.8	C	C=O, C-F	320.0	Nd	4s	359.3	Zr	loss	399.8	Se	Auger	444.8	In	P fract	488.8	Ho	Auger	531.8	O	1s LiOH	577.0	Te	3d
288.9	C	COOR	320.8	Er	4p3	360.8	Nb	3p3	399.9	Tm	Auger	444.9	In	GaAs	490.5	W	4p1	532.3	Pd	3p3	577.2	Hg	4p3
289.0	Eu	4p1	321.2	K	loss	363.0	Eu	4s	400.6	Ta	4p3	445.0	Tc	3p1	493.3	Sn	3d3	532.5	Ga	Auger	577.7	Cr	Ntv Ox
289.0	Kr	3s	321.8	Rb	3s	363.6	Ga	Auger	401.0	Sc	2p	445.2	In	Ntv OH	494.6	Zn	Auger	532.5	O	B2O3, SiO2	578.2	Ir	4p1
289.4	C	MCO3	322.0	U	5s	363.7	Dy	Auger	401.9	Sc	2O3	445.9	In	Ntv CO3	494.8	Ir	4p3	532.6	Sb	3d	579.5	Cr	O3
290.0	Ce	4s	323.6	Mg	Auger	366.0	Er	4p1	402.2	N	H4	446.4	Re	4p3	496.3	Rh	3p3	532.9	O	HgO	579.8	Ge	Auger
290.6	Gd	4p1	326.8	Ge	Auger	366.8	Ag	2S	403.2	Sc	2p1	446.9	Pb	loss	497.1	Se	Auger	533.0	At	4d3	580.0	Cr	KCrO4
290.8	C	C-CO3, CF2	329.4	Zr	3p3	367.7	Ag	O	404.1	Cd	O	447.3	Ga	Auger	497.2	Sn	3d	533.8	Hf	4s	581.8	Zn	Auger
291.7	C	pi->pi*	331.0	Pm	4s	368.2	Ag	Ag, Ag2O	405.0	Cd	3d5	448.0	In	3d	497.4	Na	Auger	536.4	Na	Auger	583.3	Te	3d3
292.7	C	CF3	331.2	Pt	4d3	368.5	Mg	Auger	405.1	Cd	Te	450.3	Er	4s	498.0	Sc	2s	537.6	Sb	3d3	583.5	Cr	2p1
292.9	K	2p3 KX	332.0	Dy	4p1	370.0	Eu	Auger	405.4	Cd	Se, CO3	451.4	In	3d3	499.0	Sn	loss	541.0	Rn	4d5	586.2	Er	Auger
293.0	Os	4d3	332.3	Tm	4p3	371.0	Ag	3d	405.5	Tl	4d3	453.0	Se	Auger	500.0	Po	4d3	544.0	Tc	3s	586.9	Tm	Auger
294.0	Th	5s	333.0	Th	4f7	371.0	As	Auger	406.7	Cd	(OH)2	453.9	Ti	2p3	503.8	Ga	Auger	544.2	Sb	loss	588.9	Ga	Auger
295.0	K	2p	333.1	Mg	Auger	374.2	Ag	3d3	407.2	N	O3	454.3	Na	Auger	505.0	Mo	3s	546.3	Au	4p3	591.0	Ru	3s
295.6	Dy	4p3	334.0	Au	4d5	376.0	Gd	4s	408.0	Cd	3d	455.1	Ti	O	507.0	At	4d5	548.0	Os	4p1	593.6	W	4s
295.7	K	2p1	335.0	Pd	3d5	376.2	Nb	3p1	411.0	Tb	Auger	456.0	Ti	2p	507.5	Sn	loss	548.1	Cu	Auger	600.0	Gd	Auger
296.2	Ir	4d5	335.4	Pd	Ntv Ox	377.2	K	2s	411.3	Mo	3p1	457.4	Ti	2O3	507.9	Lu	4s	552.4	Na	Auger	600.7	Te	loss
296.2	Se	Auger	337.0	Pd	O	377.3	U	4f7	411.7	Cd	3d3	458.0	As	Auger	512.1	V	2p3	553.2	O	loss	603.0	Fr	4d3
299.0	Ra	4f	337.5	Pd	3d	377.8	Hg	4d3	412.0	Pb	4d5	458.2	Ti	CaTiO3	513.2	Na	Auger	553.3	Sb	loss	603.0	Ra	4d5
299.2	Y	3p3	339.0	As	Auger	379.5	Hf	4p3	412.3	Ge	Auger	458.7	Ti	O2	513.5	Ga	Auger	557.1	Tb	Auger	604.0	Ag	3p1
300.6	Sr	loss	339.8	Yb	4p3	381.0	Mg	Auger	412.6	Dy	4s	460.0	Ti	2p1	513.9	Dy	Auger	558.5	Zn	Auger	609.1	Pt	4p1

BE Lookup Table for Signals from Elements and Common Chemical Species

609-1395 eV

609.6	Tl	4p3	675.0	Xe	3d	724.0	Pt	4s	819.7	Te	3p3	915.9	Cr	Auger	999.0	O	Auger	1107.0	N	Auger	1243.8	Pd	Auger
617.0	Cd	3p3	676.0	Th	4d5	724.8	Cs	3d5	826.0	In	3s	918.6	Cs	Auger	1003.0	Nd	3d3	1108.0	Sm	3d3	1245.9	Tl	Auger
619.0	I	3d	676.7	In	loss	724.8	Cs	Cl	830.5	Co	Auger	925.3	Co	2s	1003.6	Cr	Auger	1109.8	Cd	Auger	1249.0	Ge	2p1
619.2	I	3d5	677.9	Tm	Auger	724.9	Cs	2O:SiO2	833.0	Ce	Auger	929.0	Rn	4p1	1004.8	Te	3s	1112.9	Sb	Auger	1250.8	Pt	Auger
619.2	I	KI	679.0	Bi	4p3	736.0	U	4d5	833.0	F	Auger	930.9	I	3p1	1008.7	Ni	2s	1116.6	Ga	2p3	1259.8	Ru	a
623.2	Ni	Auger	680.2	Hg	4p1	740.0	At	4p3	835.2	La	2O3	7.	Cu	Cl	1013.0	O	Auger	1117.7	Sc	Auger	1264.2	Mo	Auger
625.2	Re	4s	682.0	Sm	Auger	740.0	Cs	3d3	836.0	La	3d5	8.	Pr	3d5	1014.7	V	Auger	1126.0	Eu	3d5	1265.0	Rh	Auger
626.1	Ho	Auger	682.4	Xe	3d3	748.0	Ho	Auger	836.5	Te	loss	932.0	Cs	Auger	1020.3	Te	Auger	1128.0	La	3p3	1265.8	Ge	loss
626.4	V	2s	685.1	F	CaF2	749.0	Cs	loss	837.2	La	B6	3.	Cu	S	1021.7	Zn	O	1128.9	Ag	Auger	1272.0	Ce	3p1
627.8	Rh	3s	685.7	F	1s	756.2	Sn	3p1	837.9	Co	Auger	4.	Cu	2O	1021.8	Zn	2p3	1129.0	Sn	Auger	1272.0	U	4p1
628.2	Cu	Auger	685.7	F	LiF	758.0	Nd	Auger	841.1	Gd	Auger	932.6	Cu	2p3	1022.3	Zn	S	1131.8	Te	Auger	1275.7	Tb	3d3
629.4	Ga	Auger	688.9	F	CF2	761.1	Pb	4p1	844.2	Cs	Auger	932.9	Cu	2O	1022.5	Sb	Auger	1135.0	Ag	Auger	1296.2	Dy	3d5
630.6	I	3d3	690.9	Ir	4s	761.2	Au	4s	846.0	Fe	Auger	933.9	Cu	O	1027.0	Pm	3d5	1137.0	Ba	3p1	1298.6	Mo	Auger
634.5	Er	Auger	695.7	Cr	2s	761.8	Cs	loss	846.7	Tl	4s	934.0	Xe	3p3	1027.2	Cr	Auger	1141.0	Xe	3s	1303.3	Mg	1s
635.0	Cu	Auger	697.4	Co	Auger	763.4	Gd	Auger	851.0	Po	4p1	934.6	Cu	(OH)2	1031.0	Zn	loss	1143.4	Ga	2p1	1304.0	Cl	Auger
636.0	Ra	4d3	700.3	Tb	Auger	766.4	Sb	3p3	851.6	Mn	Auger	936.6	Bi	4s	1031.9	Sb	Auger	1148.9	Sc	Auger	1307.0	Hf	Auger
638.7	Mn	2p3	702.0	Ne	Auger	768.0	Rn	4p3	852.6	Ni	2p3	940.7	Cu	CT	1034.9	Ti	Auger	1151.0	In	Auger	1315.3	Mg	loss
4.	Ni	Auger	703.1	In	3p1	768.6	Mn	2s	852.9	Ni	B	942.2	Cu	CT	1042.0	At	4s	1153.0	Fr	4s	1316.1	Pt	Auger
5.	Ga	Auger	703.5	F	loss	770.2	Sn	loss	853.0	La	3d3	943.8	Cu	CT	1043.0	U	4p3	1155.0	Eu	3d3	1318.0	Ta	Auger
640.9	Mn	Mn3O4	705.0	Po	4p3	772.8	Cd	3s	853.8	Ni	O	1.	Sb	3s	1044.8	Zn	2p1	1159.4	Pd	Auger	1319.0	Nb	Auger
641.0	Mn	MnO	705.2	Ni	Auger	777.7	Ni	Auger	854.3	Ni	NtvOx	2.	Mn	Auger	1049.6	Sn	Auger	1170.0	Th	4p1	1321.6	Lu	Auger
641.0	Mn	Mn2O3	706.7	Fe	2p3	778.3	Co	2p3	855.4	Ni	(OH)2	945.5	Sb	Auger	1052.0	Pm	3d3	1184.0	Ce	3p3	1322.3	Re	Auger
641.6	Mn	MnO2	707.2	Fe	S2	779.0	U	4d3	859.0	F	Auger	952.2	Cu	2p1	1055.3	V	Auger	1185.5	Rh	Auger	1323.9	As	2p3
642.4	Au	4p1	707.5	Ga	Auger	779.2	Co	O	863.0	Ne	1s	952.2	Pr	3d3	1055.5	Zn	loss	1186.8	Gd	2O3	1324.5	Mo	Auger
5.	I	loss	709.8	Fe	O	779.5	Co	3O4	869.9	Ni	2p1	952.5	Cs	Auger	1058.0	Ra	4p1	1186.9	Gd	3d5	1326.3	Mg	loss
6.	Pb	4p3	710.4	Fe	2O3-g	780.0	Ba	3d5	870.5	Cs	Auger	959.5	Cr	Auger	1058.0	Sn	Auger	1190.0	Ag	Auger	1334.0	Pt	Auger
645.0	Mn	2p	710.5	Fe	3O4	780.0	Ba	CO3, OAc	870.7	Te	3p1	959.9	Te	Auger	1063.0	Ba	3p3	1194.0	Ca	Auger	1335.1	Dy	3d3
647.5	Cu	Auger	710.8	Fe	2O3-a	780.6	Co	(OH)2	875.0	I	3p3	965.0	Th	4p3	1067.7	Ti	Auger	1196.4	Zn	2s	1337.7	Zr	Auger
649.7	Mn	2p1	711.5	Fe	OOH	780.9	Co	NtvOx	878.1	F	Auger	969.3	Te	Auger	1071.8	Na	2O-SiO2	1208.0	Ra	4s	1352.9	Ho	3d5
651.0	Cd	3p1	711.6	F	loss	782.2	Sb	loss	879.0	Ra	4p3	970.4	I	Auger	1071.9	Na	OH	1213.0	Pd	Auger	1358.7	Er	3d5
652.2	Zn	Auger	712.2	Ni	Auger	784.0	Fe	Auger	882.0	Ce	O2	976.8	V	Auger	1072.0	I	3s	1217.0	Cs	3s	1359.5	As	2p1
655.0	Eu	Auger	713.0	Co	Auger	793.7	Co	2p1	884.0	Ce	3d5	979.7	O	Auger	1072.0	Na	1s	1217.0	Ge	2p3	1363.6	Yb	Auger
655.7	Ga	Auger	713.0	Th	4d3	795.2	Ba	3d3	885.2	Sn	3s	980.0	Fr	4p1	1072.0	Na	Cl	1217.0	Ru	Auger	1365.5	Mo	Auger
657.2	I	loss	714.1	In	loss	797.0	Pr	Auger	886.0	At	4p1	981.0	Nd	3d5	1076.4	In	Auger	1219.6	Gd	3d3	1367.1	Tm	Auger
658.0	Os	4s	714.6	Sn	3p3	802.0	Ba	loss	886.5	Ba	Auger	981.8	I	Auger	1081.0	Sm	3d5	1221.4	C	Auger	1368.2	Zr	Auger
659.4	Zn	Auger	715.1	Er	Auger	803.6	Hg	4s	888.0	Fe	Auger	994.6	Te	Auger	1084.0	In	Auger	1225.0	Ag	Auger	1373.3	Tb	3p3
2.	In	3p3	719.5	Cu	Auger	805.0	Bi	4p1	888.4	Te	loss	995.0	Po	4s	1092.5	Te	Auger	1234.7	Rh	Auger	1378.9	Gd	3p3
3.	Ho	Auger	719.6	Ag	3s	808.9	Tb	Auger	891.7	Pb	4s	995.0	Sb	Auger	1097.0	Rn	4s	1234.8	Ge	loss	1390.9	Pb	Auger
669.7	Xe	3d5	719.9	Fe	2p1	810.0	Fr	4p3	898.0	Ba	Auger	996.0	Xe	3p1	1097.2	Cu	2s	1235.0	K	Auger	1392.6	Zr	Auger
671.5	Pd	3s	721.5	Tl	4p1	812.6	Sb	3p1	900.3	Mn	Auger	997.3	Cr	Auger	1102.8	Ti	Auger	1242.0	Pr	3p3	1393.3	Ho	3d3
						817.0	Ba	loss	902.0	Ce	3d3	998.0	Cs	3p3	1103.1	Cd	Auger	1242.1	Tb	3d5	1395.0	Si	Auger

